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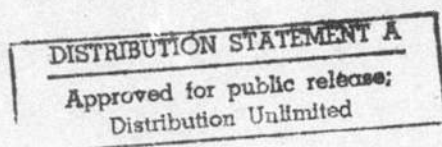
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Technical Reliability Studies
EOS/ESD TECHNOLOGY
ABSTRACTS

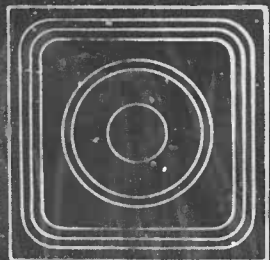


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Summer 1982

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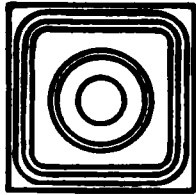
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A DoD Information Analysis Center

Technical Reliability Studies

EOS/ESD TECHNOLOGY ABSTRACTS

Summer 1982

Prepared by:

William K. Denson

John P. Farrell

IIT Research Institute

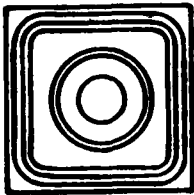
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20. ABSTRACT (Continue on reverse side if necessary and identify by block number) The EOS/ESD Technology Abstracts is a bibliography of approximately 400 papers, reports and articles related to the subject of electrical overstress/electrostatic discharge. The intent of this bibliography is to make more accessible the present information on the subject of EOS/ESD, such as design, failure analysis, protective measures and techniques, and training programs. The cut-off date for inclusion of material was March, 1982. The 400 abstracts represent a 50% increase in content over TRS-3.			

PREFACE

The purpose of this bibliography is to make more accessible present information on Electrical Overstress and Electrostatic Discharge. Duplication of previous studies can be avoided by the increased information retrieval capability provided by this bibliography. This bibliography contains approximately 400 abstracts of papers and articles, representing 50% more than contained in its predecessor, TRS-3. March, 1982, was the cut-off date for inclusion of material.

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INTRODUCTION AND USER'S GUIDE

The EOS/ESD Technology Abstracts references literature pertinent to Electrical Overstress and Electrostatic Discharge damage or degradation of electronic devices. Aspects found herein encompass design, failure analysis, protective measures and techniques, and training programs. References are selected for citation from the Reliability Analysis Center document files. The portion presented here dates from acquisitions made during 1969 to May 1982. Documents are selected on the basis of informational currency and usefulness as well as availability to the engineering community.

ARRANGEMENTS

This publication is arranged in eight sections: alphabetical list of terms (subjects), (subject) index, author index, corporate index, keywords in title index, bibliographic citations, source index, technology abstracts, and standards. The five digit number associated with each document is the RAC document number and is used in this publication for cross-referencing purposes.

The **ALPHABETICAL LIST OF TERMS** is a list of terms without citations and serves as a look-up table for the "index" which it precedes. The terms are arranged alphabetically to permit easy scanning for selecting similar terms. Scanning of this list can have the following useful benefits: (1) the researcher can develop a search strategy by serendipitous association and (2) the likelihood of overlooking a highly relevant citation is minimized.

The **INDEX** is the alphabetical list of terms of Section 1 with citations. The citations include the document number and the title of the documents. Including the title is a convenience which provides a possibility for selecting the most appropriate citation and eliminating those not applicable without the necessity of looking up more information elsewhere.

The **AUTHOR INDEX** is an alphabetical list of all authors cited whether principal or secondary.

The **CORPORATE INDEX** is an alphabetical list of all corporations, companies, institutions and government agencies with whom the authors were affiliated at the time the papers were prepared. Citations in the index include document number and title.

The **KEYWORD IN TITLE INDEX** is an alphabetical list of selected keywords in the title of the documents. Citations include document number and title. This index can be used to locate documents for which the keyword is a principal topic.

The **BIBLIOGRAPHIC CITATIONS** list is a compilation of all the citations of documents given in this publication. The citations are given in decreasing order by document number.

The **SOURCE INDEX** is an alphabetical list of the sources where the documents may be obtained.

The **TECHNOLOGY ABSTRACTS** provide complete coverage of the citations. Abstracts are in ascending numeric order.

The **STANDARDS** provide a list of government and industry standards.

IMPLEMENTATION

These indexes were composed and printed out on RADC's Honeywell 6180 computer using the General Comprehensive Operating Systems (GCOS). Programs for data input and the output reports were developed by RAC software engineers. The final manuscript was printed on an Anderson-Jacobson (Model AJ832) terminal.

SEARCH EXAMPLE

The following example illustrates the use of Section 1 and 2:

Suppose we are interested in studying the input protection on CMOS devices. The possible terms for finding applicable citations, we decide, would be "CMOS," "Input" and "Protection." Scanning Section I for these terms, we find by serendipitous association the following terms listed:

CMOS B Series Versus A Series Input Protection
CMOS Devices
CMOS Protection Levels
Input Protection
Protection Networks
Protection Techniques

When the terms are looked up in the index (Section 2), the following sixteen citations are accepted for study:

10395	14983
12309	15780
13309	15781
13310	15936
13672	16067
13717	16067
13720	16696
14075	17163

HOW TO OBTAIN DOCUMENTS IN THIS BIBLIOGRAPHY

Each reference listed herein contains complete bibliographic information including the personal and corporate author with location. Where the document is available from one of the government document distribution centers, see information shown below. Other documents can be obtained from the original source (i.e., author, journal, society, etc.). Documents other than those published by RAC cannot be obtained from RAC.

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(DTIC)
Cameron Station
Alexandria, Virginia 22314
(202)694-7633

SECTION 1
ALPHABETICAL LISTING OF INDEX TERMS

ALPHABETICAL LISTING OF INDEX TERMS

ACCELERATED STRESS TESTING
 AIR IONIZING GRIDS
 AIR-IONIZER(ENER-JET)
 AL-SIO2-SI CAPACITORS
 ANNEALING
 ANTISTATIC AGENTS
 ANTISTATIC AGENTS, LUBRICANT AND BEARING DAMAGE
 ANTISTATIC CONTAINERS
 ANTISTATIC EQUIPMENT
 ANTISTATIC FOOTWEAR
 ANTISTATIC GARMENTS
 ANTISTATIC LAMINATION(RCAS 3600)
 ANTISTATIC MATERIALS
 ANTISTATIC MICROFOAM
 ANTISTATIC NYLON(RCAS 2400)
 ARC GAPS
 ARC POTENTIALS
 ATOMIZER
 AUTOMATIC MACHINES
 AVALANCHE INJECTION
 BAGS
 BIMOS
 BIPOLAR IC
 BIPOLAR MICROCIRCUITS
 BIPOLAR SEMICONDUCTORS
 BIPOLAR TRANSISTORS
 CABLE TRANSIENTS
 CAPACITOR DAMAGE
 CARBON BLOCK
 CARPETING, STATIC GENERATOR
 CASE HISTORIES
 CHARGING MECHANISMS
 CLEAN ROOMS
 CLEANING SOLVENTS
 CLOUD PHYSICS THEORY
 CMOS 1K RAM (6518)
 CMOS AND GATE (4081B)
 CMOS B SERIES VERSUS A SERIES INPUT PROTECTION
 CMOS DESIGN PRECAUTIONS
 CMOS DEVICES
 CMOS FLIP-FLOP (4013A)
 CMOS (CD4001A)
 CMOS NAND GATE (4011A)
 CMOS NAND GATE (4011)
 CMOS NOR GATE
 CMOS NOR GATE (4001)
 CMOS NOR GATE (4002)
 CMOS NOR GATE (TP4000)
 CMOS OPERATION
 CMOS PROTECTION LEVELS
 CMOS RELIABILITY
 CMOS SHIFT REGISTER (4015A)
 CMOS SHIFT REGISTER (4021A/B)
 COMPUTER ANALYSIS
 COMPUTER DATA LINES
 COMPUTER FACILITIES
 COMPUTER SIMULATION
 COMPUTER SYSTEMS
 CONDUCTILE
 CONDUCTIVE ADHESIVE
 CONDUCTIVE CARBON BLACKS
 CONDUCTIVE COATINGS
 CONDUCTIVE CONTAINERS
 CONDUCTIVE CUSHIONS
 CONDUCTIVE FILAMENTS
 CONDUCTIVE FLOORS
 CONDUCTIVE MATERIALS
 CONDUCTIVE ORGANIC SURFACE COATINGS
 CONDUCTIVE SMOCKS
 CONDUCTIVE VINYL FLOORING
 CONDUCTIVITY
 CONTAINER MARKING
 CROWBARS
 CRYOGENIC COOLANTS, STATIC GENERATOR

ALPHABETICAL LISTING OF INDEX TERMS

DATA BASE
 DATA COMPARISON
 DC MODEL DEVELOPMENT
 DESIGN CONCEPTS
 DESIGN INDUCED MECHANISMS
 DETECTION TECHNIQUES
 DEVICE BURNOUT
 DEVICE DEGRADATION
 DEVICE GEOMETRY
 DEVICE RELIABILITY
 DIELECTRIC BREAKDOWN
 DIODE AND RESISTOR COMBINATIONS
 DIODE THRESHOLD LEVEL
 DIODE, PIN
 DIODE, SCHOTTKY BARRIER
 DIODE, SCHOTTKY (1N5711)
 DIP TUBES
 DISCHARGE WAVEFORMS
 DOPING
 DOWNY
 ECL OR/NOR GATE (10518)
 ELECTRIC DISCHARGE TRIMMING
 ELECTRIC SHOCK ELIMINATION
 ELECTRICAL NOISE
 ELECTRICALLY CONDUCTIVE PAINT
 ELECTROMAGNETIC EFFECTS
 ELECTRO-EXPLOSIVE DEVICE HAZARDS FROM ESD
 ELECTRO-EXPLOSIVE DEVICE PROTECTION AGAINST ESD
 ELECTRO-THERMOMIGRATION
 ELECTROSTATIC ANALYZERS
 ELECTROTHERMAL MODEL
 EMI SUSCEPTIBILITY
 EMI SYSTEM COMPATIBILITY
 EMI TESTING
 EMI/RFI SHIELDING
 EMP DAMAGE
 EMP DATA BASE
 EMP ENVIRONMENT
 EMP HARDENING
 EMP INDUCED DAMAGE
 EMP SUSCEPTIBILITY
 EMP TESTING
 EMP THEORETICAL MODELING
 EMP TO ESD CONVERSION
 EMP TRANSIENT SUPPRESSION
 EMP, HIGH ALTITUDE
 ENVIRONMENTAL FACTORS
 ENVIRONMENTAL STATIC
 EOS DAMAGE
 EOS FAILURES
 EOS MODELING
 EOS TEST PROGRAM
 EOS TESTING
 EPROM, 16K
 ESD CATEGORIES
 ESD CONSULTANTS
 ESD CONTROL
 ESD CURRENT PATH
 ESD DAMAGE
 ESD DAMAGE PREVENTION
 ESD DAMAGE THRESHOLD
 ESD DAMAGE, REDUCTION OF
 ESD ELIMINATION
 ESD EQUIPMENT MANUFACTURERS
 ESD FAILURE MODELS
 ESD FAILURES
 ESD FORUM
 ESD HANDBOOK
 ESD LIBRARY
 ESD MARKINGS ON HARDWARE
 ESD MATERIAL MANUFACTURERS
 ESD MATHEMATICAL MODELS
 ESD PACKAGING
 ESD POTENTIAL BLEED OFF

ALPHABETICAL LISTING OF INDEX TERMS

ESD REFERENCES
ESD SAFEGUARD, OVERKILL
ESD SENSITIVITY CLASSIFICATION
ESD SHOCKS
ESD SPECIFICATIONS
ESD STANDARDS
ESD STUDY
ESD SUSCEPTIBILITY
ESD SYMPOSIUM HIGHLIGHTS
ESD TESTING
FABRICATION CHARACTERISTICS
FAILURE ANALYSIS
FAILURE DISTRIBUTION
FAILURE LEVELS
FAILURE MECHANISMS
FAILURE MODES
FAILURE PREDICTION
FAILURE REPORT
FAILURE THRESHOLD
FIELD EFFECT TRANSISTORS (FET)
FIELD EFFECT TRANSISTORS, GAAS (GAAS FET)
FIELD EFFECT TRANSISTORS, METAL SEMICONDUCTOR (MESFET)
FIELD FORCE PROTECTION
FILTERS
FLOOR COVERINGS
FREON CANNED COOLANT, STATIC GENERATOR
FUSING VOLTAGES
GAS ARRESTERS
GATE DAMAGE
GATE DIELECTRIC DEFECTS
GEOSYNCHRONOUS ORBIT
GEOSYNCHRONOUS PLASMA
GLITCH DETECTOR
GROUNDING
GROUNDING DEVICES
GROUNDING, SINGLE-POINT
HANDLING
HARDNESS PROTECTION
HIGH FIELDS
HOSPITAL SYSTEMS
HUMAN BODY DISCHARGE
HUMAN BODY DISCHARGE, MEASURING
HUMAN BODY ESD DAMAGE
HUMAN BODY ESD MODEL
HUMAN BODY FACTORS
HUMIDITY EFFECTS
HYBRID ASSEMBLIES
HYBRID FACILITY
IIL DEVICES
IMPLEMENTATION SCHEMES
INDIVIDUAL PROTECTION
INPUT PROTECTION
INSTRUMENT BEARING PACKAGING
INSULATING MATERIALS
INTEGRATED CIRCUITS
INTERFACE CIRCUITRY SENSITIVITY ANALYSIS
INTERFERENCE TESTING
IONIZERS
J-FET
J-FET DEGRADATION
J-FET (2N4416)
J-FET (2N5524)
J-FET(2N4338)
JUNCTION BURNOUT
JUNCTION DEGRADATION
LAMINAR FLOW HOODS
LATCH-UP
LATENT FAILURE MECHANISMS
LEAD WIRE LENGTHS
LIGHTNING
LIGHTNING CAUSED FAILURES
LIGHTNING MODELING
LINE CONDITIONERS
LSI EVALUATION

ALPHABETICAL LISTING OF INDEX TERMS

LSTTL LOW POWER SCHOTTKY (54LS151)
 LSTTL LOW POWER SCHOTTKY (54LS153)
 LTTL (54L04)
 LTTL NAND GATE (54L10)
 MAINTENANCE, STATIC FREE
 MANUFACTURING ENVIRONMENT
 MELAMINE LAMINATE
 METAL FILM RESISTORS
 METAL OXIDE VARISTORS (MOV)
 MICROELECTRONICS, SCREENING OF
 MICROPROCESSOR
 MICROWAVE INTERFERENCE
 MICROWAVE RADIATION
 MIS DEVICES
 MNOS DEVICES
 MOS 16K MEMORY
 MOS 4K MEMORY
 MOS CIRCUIT DESIGN
 MOS DEVICES
 MOS I/O CIRCUITRY LIMITATIONS
 MOSFET DEVICES
 MOSFET (2N3631)
 MOSFET (3N128)
 MOSFET (3N157)
 MOSFET (3N170)
 MOSFET LOGIC CHIPS
 MULTIPLE PULSE TESTING
 NMOS 4K E2PROM (2401)
 NMOS DEVICES
 NMOS RAM
 NUCLEAR POWER PLANTS
 NUCLEAR RADIATION EFFECTS
 NUCLEAR STATIC ELIMINATORS
 OP AMP (344)
 OP AMP (741)
 OP AMP (HA2700)
 OP AMP (LM101)
 OVERSTRESS CONDITIONS
 OVERSTRESS FAILURES
 OVERSTRESS TOLERANCE
 OVERVOLTAGE CONDITIONS
 OXIDE DEFECTS
 PACKAGING MATERIALS
 PARASITIC SCR'S
 PASSIVE DEVICES
 PCB MANUFACTURING
 PHANTOM EMITTERS
 PHYSICAL ANALYSIS
 PINK POLY
 PLASMA ENVIRONMENT
 PLASMA ETCHING
 PLASTICS, STATIC GENERATOR
 PMOS DEVICES
 PMOS IC FAILURES
 PRECAUTIONARY MEASURES
 PRIMERS
 PROTECTION NETWORKS
 PROTECTION TECHNIQUES
 PROTECTIVE DIODES
 PROTECTIVE FILM
 PROTECTIVE HYBRID DEVICE
 PROTECTIVE REQUIREMENTS
 PULSE POWER-BURNOUT
 PULSE VOLTAGES
 PULSED OVERLOAD TOLERANCE
 PULSED POWER TESTING
 PULSER
 PULSES, HIGH AMPLITUDE CURRENT
 RADIOACTIVE PROTECTION
 RAM, MK4516
 RECTIFIER, FAST RECOVERY
 RESISTIVE PARTICLES
 RESISTIVE PASTES
 RESISTIVITY

ALPHABETICAL LISTING OF INDEX TERMS

RESISTIVITY, SHEET
 RESISTOR MATERIAL SENSITIVITY
 RESISTORS
 RF PROTECTION
 RF PULSE OVERSTRESS
 RF PULSE TESTING
 RF SHIELDED ENCLOSURES
 SCATHA SATELLITE INSTRUMENTATION
 SCHOTTKY (1N5711)
 SECOND BREAKDOWN
 SECONDARY EMISSION
 SEM APPLICATIONS
 SEMICONDUCTOR DEVICE STUDIES
 SEMICONDUCTOR DEVICES
 SHIELDING MATERIALS
 SHIPPING TUBES
 SHUNTING
 SHUNTING MATERIALS
 SILICA FABRIC
 SILICON DEVICES
 SILICON DIOXIDE DIELECTRIC STRENGTH
 SIMULATION
 SIMULATOR
 SINUSOIDAL STRESS
 SLIDE PRESENTATION
 SMALL SCALE JUNCTION IC'S
 SOLAR CELLS
 SOS DEVICES
 SOS DIODES
 SOS EDGE EFFECTS
 SOS RESISTORS
 SPACECRAFT
 SPACECRAFT CHARGING
 SPARK GAP ARC GENERATOR
 SPARK CAPS
 STATIC AWARENESS
 STATIC CHARGE
 STATIC CONTROL
 STATIC DEMONSTRATIONS
 STATIC EFFECTS
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 STATIC ELECTRICITY REFERENCES
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 STATIC HAZARDS IN PRODUCTION
 STATIC METERS
 STATIC ON PC BOARDS
 STATIC ON SPACECRAFT
 STATIC PHENOMENA
 STATIC PRECAUTIONS
 STATIC PROBLEMS
 STATIC PROTECTION
 STATIC SAFE WORK AREA
 STATIC SENSITIVE DEVICES
 STATIC WARNING DEVICES
 STATISTICAL ANALYSIS
 STEP STRESS TESTING
 STTL (54804)
 SUPERSAP2
 SURFACE ACOUSTIC WAVE (SAW) DEVICES
 SURFACE RESISTIVITY
 SURGE ARRESTERS
 SURGE SUPPRESSION
 TEMPERATURE EFFECTS
 TEMPEST
 TEST METHODS
 TESTING
 TESTING (CORROSION AND SOLDERABILITY)
 TEXTILE FIBERS
 THERMAL ANALYSIS
 THERMAL INSTABILITY
 THERMAL MODELS
 THERMAL SENSITIVITY
 THICK FILM INKS

ALPHABETICAL LISTING OF INDEX TERMS

THICK FILM MATERIALS
 THICK FILM RESISTORS
 THIN FILM RESISTORS
 THUNDERSTORM DATA
 TIME-RELATED ELECTRICAL IMPROVEMENT
 TOPICAL ANTISTATS
 TOPICAL ANTISTATS SPRAYING
 TRAINING PROGRAM
 TRANSFORMERS
 TRANSIENT DAMAGE
 TRANSIENT ENERGY
 TRANSIENT FAILURES
 TRANSIENT PULSES
 TRANSIENT SUPPRESSORS
 TRANSIENT VOLTAGE MEASUREMENT
 TRANSIENTS, SOURCES OF
 TRANSISTOR THRESHOLD LEVEL
 TRANSISTOR, DARLINGTON
 TRANSISTOR, LOW POWER (2N2222)
 TRANSISTOR, NPN
 TRANSISTOR, PARAMETER TRADE OFFS
 TRANSISTOR, PLANAR
 TRANSISTOR, POWER
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 TRANSISTOR, RF (2N5179)
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 TRANSISTOR, UHF
 TRIBOELECTRIC CHARGING
 TTL ADVANCED SCHOTTKY (74F04)
 TTL ADVANCED SCHOTTKY (74F175)
 TTL DEVICES
 TTL HEX-INVERTER
 TTL (5404)
 TTL NAND GATE (7400)
 TTL NAND GATE (74500, 74L500)
 TTL NAND GATE (9046)
 TTL SCHOTTKY (54157)
 VELOSTAT
 VLSI DEVICES
 VHOS GATE PROTECTION
 VOLTAGE EFFECTS
 VULNERABILITY, ELECTROMAGNETIC
 VULNERABILITY, RESISTORS
 VULNERABILITY, RF POWER
 VULNERABILITY, SEMICONDUCTORS
 VZAP DATA BASE
 WORK GROUP BEHAVIOR
 WORK STATIONS
 WORKBENCH MATERIALS
 WORKING ENVIRONMENT
 WORKSTATIONS
 WRIST STRAPS
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 ZENER DIODES
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04783

Smith, J.S. (U.S. Air Force, Rome Air Development Center, Griffiss AFB, NY).
PULSE POWER TESTING OF MICROCIRCUITS.
Rept. No. RAD-TR-71-59, October 1971, 50 pp.

Failure analysis of microcircuits subjected to high current transient pulses shows the principal cause of failure to be junction shorting. Thin film resistors are especially susceptible. Current and thermal profile analyses do predict the required energy to cause burnout. Metallization burnout is a function of current density for 200 nsec pulses but depends more on the thickness of the SiO₂ passivation at longer pulse widths.

04834

Lane, C.H. (U.S. Air Force, Rome Air Development Center, Griffiss AFB, NY).
ELECTRICAL OVERSTRESS FAILURES IN SILICON DEVICES.
Rept. No. RAD-TR-72-148, July 1972, 36 pp.

Experimental evidence is used to substantiate a proposed mechanism of overstress failures. The mechanism is considered to be a migration of liquid along a line determined by crystal and electric fields. Graphs are given showing the relationship between voltage and electrode spacing. Oxidation temperature is identified as a factor that affects sensitivity, higher temperature oxidation providing devices with higher resistance to surface zaps.

10000

Domingos, H. (Clarkson College of Technology, Potsdam, NY).
ELECTRO-THERMAL OVERSTRESS FAILURE IN MICROELECTRONICS.
Rept. No. RAD-TR-73-87, Contract No. F30602-72-C-0007, 182 pp.

Failure of microelectronic circuits caused by electrical overstress has been investigated theoretically and experimentally. Computer calculations on heat flow in silicon structures have pointed out the necessity of using temperature-dependent thermal constants for silicon. The effect of surface layers and power distribution on the peak temperature in silicon devices under transient conditions has been investigated.

Integrated circuits representing several fabrication technologies from several different manufacturers were pulsed to failure over pulse lengths from 100 nanoseconds to 10 milliseconds. The threshold power per unit area to produce permanent damage was found to vary by a factor of 20 among the parts tested. Peak temperatures to initiate current constriction were estimated to be 1000-1200°C.

10342

Van Beek, H.W. (Texas Instruments Inc., Houston, Texas).
MOS/LSI CIRCUIT DESIGN: DESIGNING-IN RELIABILITY.
IEEE - 10th Reliability Physics Symposium, 1972, pp. 36-41.

The solution to the need for extensive burn-in and temperature cycling calls for the circuit designer to "design-in" product reliability. By "designing-in reliability" is meant establishing reliability by design and fabrication with appropriate experimental monitoring. This is not a novel concept by any means but all too often it is forgotten when the topic of reliability is discussed. The application of this concept in MOS circuit design requires an understanding of the tools available to the designer and their relative importance and how they affect the MOS circuit design.

10379

Ebel, G.H., and H.A. Engelke (Singer-Kearfott Division, Wayne, NJ).
FAILURE ANALYSIS OF OXIDE DEFECTS.
IEEE - 11th Reliability Physics Symposium, Catalogue No. 73 CHO 755-9-PHY, 1973, pp. 108-116.

There have been many good papers presented on various failure analysis techniques for studying oxide defects. This paper will review some of these and will describe, in detail, the application of nematic liquid crystals to the problem of locating the failure sites in oxides.

10395

Linhom, L.W. (National Security Agency, Ft. George G. Meade, MD) and Plachy, R.F. (John Hopkins University, Silver Springs, MD).
ELECTROSTATIC GATE PROTECTION USING AN ARC GAP DEVICE.
IEEE - 11th Reliability Physics Symposium, 1973, pp. 198-202.

An ideal MOS protection device should respond to very fast and very slow rise time pulses and be able to short the input to ground before damage to the gate can occur. In general, all failures occur where the gate oxide overlaps the source or drain. The field plate protective diode by itself affords no protection to fast rise time pulses because of its connection in parallel with the input gate.

An arc gap is formed by locating the bonding pad 2.0 mils from a ground metallization ring encircling the chip. The ambient package atmosphere will support a low impedance gaseous discharge from pad to ground

ring. No other metallization should be located within 2 mils of the bonding pad, and the area should not be passivated from the ambient air.

10599

Tasca, D.M., J.C. Peden, and J.L. Andrews (General Electric).
THEORETICAL AND EXPERIMENTAL STUDIES OF SEMICONDUCTOR DEVICE DEGRADATION DUE TO HIGH POWER ELECTRICAL TRANSIENTS.
Rept. No., 73SD4289, Contract No. DAAG39-72C-0066, December 1973.

The principal areas of investigation were the detailed characterization of the degradation and failure mechanisms in selected discrete, bipolar, unipolar and integrated circuit devices. A major area of interest was to show experimentally the utility of square wave pulsed-power damage testing in the prediction of semiconductor device response for complex power waveforms typical of electromagnetic pulse (EMP) induced transients.

The experimental program consisted of a variety of electrical damage experiments on the following device types: 1N4148 diodes, 2N918 transistors, SN5405 microcircuits, MEM806A MOSFET's and RD211 microcircuits. The pulse widths ranged from three nanoseconds to thirty microseconds.

The theoretical modeling included considerable effort in further refinement of the thermal damage models. The application of these thermal damage models derived from the square wave data was then extended to the prediction of damage to more complex waveforms. This was done through the application of Duhamel's Theorem of linear heat transfer by which one can predict the temperature rise in the body for a constant rate of heat production. Duhamel's Theorem was successfully applied for damage prediction of both unipolarity and bipolarity complex electrical waveforms based upon the knowledge obtained for damage under square wave (constant rate) pulsing.

10792

Kennan, W.F., and D.M. Smith (Texas Instruments Inc., Dallas, TX).
PULSE POWER STUDIES OF HARDENED MICROCIRCUITS
Rept. No. RADC-TR-73-367, Contract No. F30602-72-C-0077, December 1973, 77 pp.

The effects of large amplitude transient pulses on radiation tolerant integrated circuits was investigated. Two distinct burnout mechanisms were discovered to exist, diode failure and resistor burnout. Both mechanisms were investigated independently by test structures to measure the influence of processing variations on the failure levels.

10839

Viele, A.A. (IBM, Manassas, VA).
A FAILURE ANALYSIS TECHNIQUE FOR LOCATING THE FAIL SITE IN MOSFET (LSI) LOGIC CHIPS WITH SPUTTERED SILICON DIOXIDE PASSIVATION.
IEEE - 12th Reliability Physics Symposium, 1974, pp. 16-21.

Failure analysis of MOSFET chips with sputtered SiO₂ passivation must be precluded by the removal of the passivation layer to allow probe contact. The electrical integrity of the chip must be maintained to locate the fail site by signal tracing. Mechanical removal of the SiO₂ passivation has a greater success. The chip is removed from the C-DIP by melting the eutectic or by polishing away the backside ceramic. Chips are removed from ceramic controlled-collapse connection (C-4) packages by etching the solder pads in a 5:1 solution of acetic acid/hydrogen peroxide, then rinsed in DI water, or as recommended mechanically by cutting the C4 pads on all sides of the chip. Parallel polishing in a syntron vibromat using a slurry of aluminum oxide powder (.05 micron) and DI water down to the aluminum surface removes the SiO₂. Even polishing can be facilitated by coating areas of excess polishing with fingernail polish. Electrical analysis isolates the failed circuits and signal analysis characterizes the failure mechanism. Physical analysis confirms the damage location.

10841

Gajda, J.J. (IBM System Products Division East Fishkill Facility, Hopewell Junction, NY).
TECHNIQUES IN FAILURE ANALYSIS OF MOS DEVICES
IEEE - 12th Reliability Physics Symposium, 1974, pp. 30-37.

Failure analysis of gate oxides of MOSFET devices is discussed using a copper decoration and plating technique. Static discharge failures can be readily identified while subtle gate failure (submicron) from leakage and stress testing shorts require copper decoration to identify the physical appearance of the defect site. Solutions of NH₄F (40%, 4 parts) HF (48%, 1 part) and glycerine (2 parts) are used to remove glass passivation layers; also HNO₃ (70%, 1 part) HF (48%, 5 parts) and glycerine (10 parts). Lands are opened using capacitive discharge. Aluminum is etched away using a standard H₂PO₄ - HNO₃ - CH₃COOH-H₂O solution. Poly-silicon gates are removed using an etch of 20 parts HNO₃ and 1 part HF. A displacement solution of 2% CuSO₄ and 28% HF with a high intensity lamp locates conductive paths through the gate oxide and where gate silicon is exposed. Regions of defects are analyzed using SEM analysis. To avoid etching any oxide a standard electroplating solution of

CuSO₄ and H₂SO₄ can be used. Pinholes in oxides, surface pits in gate region, Al₂O₃ formation in gates, single mounds and raised plateaus on oxide surface can be detected.

10843

Jones, W.K. (Charles Stark Draper Laboratory, Cambridge, MA).
PLASMA ETCHING AS APPLIED TO FAILURE ANALYSIS.
IEEE - 12th Reliability Physics Symposium, 1974, pp. 43-47.

Failure analysis is discussed using a carbon tetrafluoride plasma etch. The CF₄ is excited to plasma by RF energy in a vacuum of .7 torr. Helium is used to control the reaction as it is viewed through a sapphire viewer under a stereomicroscope @ 150x magnification. Prior to complete removal the subpassivation aluminum has a green yellow tint, while bonding pad metallization is metallic in appearance. Backgrinding and polishing with final plasma etch will reveal the underside of metallization.

Examples given of the use of optically controlled plasma etching are: (1) removal of passivation for SEM analysis; (2) backlapping of bipolar devices; (3) thin-section for TEM analysis of nichrome fuses.

10845

Speakman, T.S. (Western Electric Company, Inc. Reading, PA).
A MODEL FOR THE FAILURE OF BIPOLAR SILICON INTEGRATED CIRCUITS SUBJECTED TO ELECTROSTATIC DISCHARGE.
IEEE - 12th Reliability Physics Symposium, 1974, pp. 60-69.

A mathematical model to predict ESD voltage thresholds is presented. Device failure occurs as a result of emitter-base junction degradation caused by electrical overstress. The degradation is manifested as a lowered breakdown voltage or higher reverse leakage current. The charges may come from a human body or the device itself. The resulting current of discharge is an exponentially decaying pulse. The failure is deemed to have occurred when the local power density causes the temperature to melt the semiconductor. The threshold level is a function of the current path cross section area, not of the junction area. The total power dissipated is the expression $P = V_{bi} + R_{bi}^2$ (V_{bi} = junction drop and R_{bi} = junction resistance). The current path is from the edge of the emitter to the base contact. Its area is emitter length times base junction depth. The power density vs pulse length is plotted to show good correlation with the Wunsch-Bell plot.

10873

Freeman, E.R., and J.R. Beall (Martin Marietta Corp., Denver, CO).
CONTROL OF ELECTROSTATIC DISCHARGE DAMAGE TO SEMICONDUCTORS.
IEEE - 12th Reliability Physics Symposium, 1974, pp. 304-312.

A study was done on the failures of three devices. The first, a 2N3970 N-channel FET, suffered a degraded reverse breakdown when subjected to ESD pulses of 6000v. The second, a 2600 internally compensated amplifier, suffered a shorted MOS compensation capacitor when subjected to ESD pulses. The third example, a 54L04 hex inverter low power TTL circuit, experienced phase-splitter transistor failure mode subjected to ESD pulses of 2500 to 3000v. Facilities were examined and verified the presence of electro-static charges in excess of the levels necessary to produce failures in the laboratory.

10993

Himmel, R.P. (Hughes Aircraft, Culver City, CA).
THE EFFECT OF STATIC ELECTRICITY ON THICK FILM RESISTORS.
Insulation/Circuits, September 1972, pp. 41-44.

The effects of static electricity in the manufacturing process, packaging and use of thick film resistors is analyzed. Thick film resistors' sensitivities are related to resistivity which in turn is directly related to the materials used in manufacture. Isolated metal particles take part in the conduction process through the breakdown of dielectrics between particles. The clean room conditions of manufacturing often result in high static charge levels. Elimination of these charges may be facilitated by special precautions. The use of protective packaging materials is encouraged.

11207

Whelan, C.D. (RCA, Somerville, NJ).
RELIABILITY EVALUATION OF CMOS TECHNOLOGY IN COMPLEX INTEGRATED CIRCUITS.
Rept. No. RADC-TR-C-0282, March 1976, 210 pp.

The objective of this study was to investigate reliability of small and medium scale CMOS integrated circuits. Four manufacturers' type 4011A Quad 2-input NAND gates and three manufacturers' type 4015A dual four stage static shift registers were chosen as test vehicles. Only Manufacturer A's product was intended for MIL-M-38510 end use.

11295

Vandre, R.H. (Aerospace Corp., Technology Division, El Segundo, CA).
PULSE-POWER BURNOUT OF INTEGRATED CIRCUITS.
Rept. No. TR-0073 (3124)-1, SAMSO-TR-72-226,
Contract No. F04701-72-C-0073, August 15,
1972, 33 pp.

Results of pulsed power burnout testing of the Fairchild 9046 quad dual-input NAND gate and the Amelco 6041 three input NAND gate showed the circuits to be vulnerable to junction burnout for pulses of less than 100v and pulse widths on the order of 100 nsec. Calculations based on Wunsch-Bell junction burnout theory showed good agreement with experimental results. Sample calculations are given.

11436

Yang, D.Y., W.C. Johnson, and M.A. Lampert (Princeton University, Princeton, NJ).
A STUDY OF THE DIELECTRIC BREAKDOWN OF THERMALLY GROWN SILICON DIOXIDE BY THE SELF-QUENCHING TECHNIQUE.
IEEE - 13th Reliability Physics Symposium, 1975, pp. 10-14.

The dielectric breakdown of SiO₂ is studied using a thin metallization. The dielectric breakdown results in removal of metallization in the area of breakdown. Positive plate voltages resulted in anisotropic removal of metallization regardless of silicon dopant. Negative plate voltages result in irregular metallization removal. With positive field plate potentials and p-type substrate the anisotropic breakdown regions were square with smooth edges. The anisotropy is explained by hot electron conduction in the presence of a large radial electric field. Slow-high field instability also resulted in Al-SiO₂ structural breakdown enhanced at lowered temperatures. A steady state current was observed and attributed to the tunneling of electrons in the presence of field plate voltages well below the point of instability. The instability results when the production and trapping of holes dominates over recombination caused by electron tunneling from the silicon substrate into the conduction band of the oxide.

11494

Hampel, D. (RCA, Advanced Communications Laboratory, Somerville, NJ).
EMP HARDENED CMOS CIRCUITS.
Rept. No. HDL-TR-192-1, Code No. 691000.22.
63516, Contract No. DAAG39-73-C-0136, October 1973, 35 pp.

This paper shows how CMOS integrated circuits can be protected against electrical

transients originating from nuclear explosions, static discharge, etc. First, the causes of transient failures are determined and then analyzed. Next, a wide range of protection devices are designed and evaluated. Finally, complete transient hardened logic gates are fabricated and tested to prove the feasibility of EMP hardened CMOS circuits.

11704

Kirk, W.J., L.S. Carter, and M.L. Waddell (Bendix, Kansas City Division, Kansas City, MO).
CONTROL OF ELECTROSTATIC DAMAGE TO SOLID STATE DEVICES.
Contract No. AT(29-1)-613 USAEC, Rept. No. BDX-613-1080, March 1974.

The control and elimination of static discharge in the work area is discussed. The human body is represented in a capacitive discharge model. The degradation to a 2N4118A varies according to the resistance in series with the human discharge. A transient voltage detection system is used to monitor ESD. The peak voltages generated by operators occurred when an operator lifts her feet or increases the static charge by gliding in a roller chair. Conductive shoes on a conductive floor can limit static voltages to as low as 50 volts. Increased relative humidity above 45% can also reduce static levels. Spray cleaning increases the electrostatic potential. Wrist straps are shown to be impractical. Conductive floor, chair and shoes all help to reduce static voltages as do conductive packaging, table tops and grounded soldering tips.

11926-01

Hewitt, H.J., and R.A. Blore (U.S. Air Force, Rome Air Development Center, Griffiss AFB, NY) and J.J. Whalen (SUNY at Buffalo).
SUSCEPTIBILITY OF UHF RF TRANSISTORS TO HIGH POWER UHF SIGNALS - PART II.
Rept. No. RADC-TR-76-44, Contract No. F30602-75-C-0122, April 1976, 74 pp.

The electromagnetic vulnerability data needed to determine the effects of high power microwave signals on solid state components involves testing 2N5179 and 2N918 transistors using 240mhz RF single pulse signals. Physical analysis of the 2N5179 revealed emitter base shorting.

11980

Wunsch, D.C., and R.R. Bell (BDM Inc., El Paso, TX).
DETERMINATION OF THRESHOLD FAILURE LEVELS OF SEMICONDUCTOR DIODES AND TRANSISTORS DUE TO PULSE VOLTAGES.
IEEE-Trans. on Nuclear Science, NS-15, No. 6, December 1968, pp. 244-258.

Theoretical predictions of circuit failure in an Electromagnetic Pulse (EMP) environment require a knowledge of failure levels for each component of the circuit due to surge voltages or currents. For most circuits, the semiconductor devices are the weakest elements with respect to such failure. This paper presents the results of an extensive experimental program to determine pulse power failure levels of semiconductor junctions. Approximately 80 different types of silicon diodes and transistors were studied with variations in junction areas for 10^{-4} to 10^{-1} cm² and with widely varying function geometries. Power levels of up to two kilowatts, with time durations of 0.1 to 20 microseconds, were applied to semiconductor junctions in both forward and reverse polarity modes. A semi-empirical formula, based on experimental data and on a simple thermal failure model is given. From the formula one can make order-of-magnitude estimates of the failure level as a function of pulse length for many silicon diodes or transistors whose junction area is known.

12227

Himmel, R.P. (Hughes Aircraft Company, Culver City, CA).
HIGH VOLTAGE SENSITIVITY OF A NEW GENERATION OF THICK-FILM RESISTOR MATERIALS.
1975 International Microelectronic Symposium, pp. 273-278.

The results of a new study into the high voltage sensitivity of this "new" generation of resistor materials is reported here. In this study, thick-film resistive pastes from five manufacturers were printed, fired, and tested for sensitivity to electrostatic discharge. The results of the tests indicate significant change from the materials previously tested, with an order of magnitude reduction in resistor sensitivity in many cases.

12278

Biddle, J.G. (Hughes Aircraft Company).
DON'T GIVE ME ANY STATIC.
Internal Report, 1979, 40 pp.

Packaging and handling precautionary measures that should be with ESD devices from Receiving to Shipping are described. Anti-static equipment needed at the work station is also identified. Advantages and disadvantages of different materials and equipment are discussed as well as the results of an evaluation on ionizing air blowers.

12309

Trigonis, A.C. (Jet Propulsion Laboratory, Pasadena, CA).
ELECTROSTATIC DISCHARGE IN MICROCIRCUITS DETECTION AND PROTECTION TECHNIQUES.

IEEE Reliability and Maintainability Symposium, Contract No. NAS 7-100, January 18, 1976.

ESD failures are analyzed as to location and extent of damage using SLM and standard optical analysis. Circuit analysis and electrical probing locate the site of failure. An HA-2700 operational amplifier failed as a result of ESD punch-through causing a 400 ohm short across a MOS capacitor (another device had a 200 ohm short). The HA-2600 high impedance op amp exhibited a similar failure mode, also the HA2520 high slew rate op-amp. Bipolar microcircuits such as the LM723H exhibited electrical degradation of the input bipolar transistors as a characteristic ESD failure. No surface damage was observed by optical microscopy or SEM except in the induced current mode. Evidence of small microcracks occurred in the damaged junctions of the LM101H device. The electron beam induced current display revealed a leakage path at the crack. The failures were analyzed to be a result of ESD because of the high voltage, low energy nature of the damage.

12351

Dominick, F. (GHZ Devices, Inc., Chelmsford, MA).
HOW MUCH PULSED POWER CAN A PIN DIODE HANDLE?
Microwaves, Vol. 15, No. 2, February 1976, pp. 54-59.

A thermal analysis is necessary to determine the peak pulsed power that a PIN diode can safely switch. Thus the maximum power handling problem is thermal in nature involving heat flow analysis. For the noncontinuous or pulsed case the peak power also depends on pulse width (t_p) and pulse interval ($t_r = (\text{rep rate})^{-1}$). Thermal time constants play an important role in the eventual cooling of the device and initial meltdown. Temperature gradients and thermal resistance are functions of device geometry, doping and the material used in mounting the device.

12502

Keenan, W.F. (Texas Instruments Inc., Dallas, TX).
PULSED OVERLOAD TOLERANCE OF SI/CR, NI/CR AND MO/SI THIN FILM RESISTORS ON INTEGRATED CIRCUITS.
IEEE - Trans. on Reliability, Vol. R-25, No. 4, October 1976, pp. 248-255.

The maximum Fusing Voltage (FV) (for 0.1-10 microsecond pulses) of Mo/Si, Ni/Cr, and Si/Cr resistors formed on oxidized Si substrates has been experimentally shown to be essentially independent of the following parameters: 1) resistive film material, 2) passivation film material (but a crack-free film is important for Ni/Cr resistors) and 3)

the thickness of the oxide film between the resistor and silicon substrate (0.5-1.5 micrometer). The FV depends on the resistor geometry, substrate material, and post fabrication annealing of the resistors. The most commonly used resistor geometry is adequate for use on ICs. The most dramatic change in FV obtained in the study was for resistors formed on glass substrates. The FV was reduced by almost a factor of 2 for 0.1 microsecond pulses over that of resistors on Si substrates.

Post fabrication annealing resulted in marked increases in FV for each material for the 0.1 microsecond pulses but had diminishing effects for 1.0 and 10 microseconds. Annealing for times greater than 60 minutes or temperatures greater than 470° did not result in important further increases.

12666

Mykkanen, C.F. (Honeywell).
ESD (ELECTROSTATIC DISCHARGE) CONTROL UPDATE NO. 1.
Component Comments, Avionics and Defense Systems, Sept. 7, 1979, 33 pp.

This component comment addresses ESD protective work surfaces and floor surfaces. The advantages and disadvantages of pink poly and melamine work surfaces are discussed. Test results of charge dissipation is given on the two work surfaces. Various types of floor surfaces are described along with an assortment of floor polishers and cleaners.

12686

Walker, R.C., and H.C. Rickers (IIT Research Institute).
SEMICONDUCTOR ELECTROSTATIC DISCHARGE DAMAGE PROTECTION.
Society of Automotive Engineers, Contract No. AF 30602-76-C-0192, Rept. No. 770228, 1977, 12 pp.

ESD is generated upon the contact of two dissimilar materials. Contact then separation results in the retention of charges. The magnitude of the charges generated depends on the ranking of materials in the triboelectric series and the intimacy and duration of contact. Fast, repetitive contact increases charge accumulation. Electronic semiconductor devices are particularly susceptible to ESD because of the catastrophic damage which results upon contact. Metal gate MOS devices are unusually susceptible. As a result of this susceptibility input protection circuitry has been devised and is successful at low limits of ESD. Failure analysis should be used whenever ESD damage is suspected. Failure duplication caused by ESD overstress can be used to confirm ESD damage.

Precautionary measures to prevent ESD damage include the identification of electrostatic sources using a noncontacting electrostatic voltmeter. Grounding, humidity control, ionized air and protective clothing can all be used to eliminate the source of ESD.

12728

De La Moneda, F.H., D.E. Debar, K.P. Stuby, and C.L. Bertin (IBM, Manassas, VA).
HYBRID PROTECTIVE DEVICE FOR MOS-LSI CHIPS.
IEEE-Trans. on Parts, Hybrids, and Packaging, Vol. PHP-12, No. 3, September 1976, pp. 172-175 or ECC, 1976, pp. 103-108.

Several structures that can be used to protect MOS-LSI chips against electrostatic discharges (ESD) are examined experimentally to determine some of the possible specification tradeoffs that result in improved overall performance. It is shown that by using structures able to withstand larger energy discharges at the expense of their voltage-clamping characteristics, higher overvoltages can be handled. Additional protection is possible by incorporating a spark-gap device on the chip-carrying module. Conditions under which this hybrid combination is effective are examined.

13210

Li, S.P., E.T. Bates, and J. Maserjian (Jet Propulsion Laboratory, Pasadena, CA).
TIME-DEPENDENT MOS BREAKDOWN.
Solid-State Electronics, Vol. 19, No. 3-E, 1976, pp. 235-239.

A general model for time-dependent breakdown in metal-oxide-silicon (MOS) structures is developed and related to experimental measurements on samples deliberately contaminated with Na. A statistical method is used for measuring the breakdown probability as a function of log time and applied field. It is shown that three time regions of breakdown can be explained respectively in terms of silicon surface defects, ion emission from the metal interface, and lateral ion diffusion at the silicon interface.

13265

Jowett, C.E.
STATIC ELECTRIFICATION HAZARDS IN MICRO-ELECTRONICS PRODUCTION.
Microelectronics and Reliability, Vol. 13, No. 6, 1974, pp. 543-547.

Three criteria exist for the existence of an electrostatic hazard: (1) charging of material or nearby structures; (2) slow, small leakage of such charge; (3) ignition, explosion, or damage by ensuing sparks of material. Relative humidity and ionization of

the local atmosphere decrease the relaxation time for stored charge. Warning devices include goldleaf electroscopes, neon lamps, electro-static voltmeters, electrometers and field mills. The magnitude and polarity of the charge acquired by a powder or its container may depend on: (1) the moisture content of the atmosphere and the powder; (2) the particle size distribution; (3) the velocity with which the powder moves or impinges on surfaces; (4) the state of surfaces on which the particles impinge. Ignition of combustible gases requires a minimum spark energy and voltage.

13309

Gallace, L.J., and H.L. Pujol (RCA/Solid State Division, Somerville, NJ).
RELIABILITY CONSIDERATIONS FOR COS/MOS DEVICES.
Rept. No. ST-6418, 1975, 24 pp.

CMOS low power digital logic finds many applications because of its high volume manufacturing and inherent reliability. All CMOS devices are susceptible to ESD. About 50% of devices fail as a result of ESD damage, overstress or application problems. An input protection network has been devised to protect gate oxides against ESD up to 1000v. Zener diodes at the output pins can clamp the voltage to safe levels. Latchup can occur when operating above maximum ratings. Bias life tests are used to accelerate chip related mechanisms sensitive to time, temperature and voltage. Leakage mechanisms respond to bias life test. Operating life tests are switching in nature and relate to the quality of the chip process. Real time controls are accelerated tests designed by reliability and application engineers working cooperatively. CMOS devices of lower junction temperatures will provide lower failures than TTL. To detect ESD a curve tracer check is made in the area isolated by electrical test. Overstress failure is internally seen as a burned or open metallization path. Gate oxide shorts are the most common failures modes for MOS devices. They may occur in weak spots anywhere, though in a perfect MOS transistor they would occur at the four corners of the gate area. Moving ionic charges under the gate area can reduce or increase threshold voltages of ESD. Bias applied to the gate metal can cause shorts from source to drain by ionic redistribution. HTRB tests can be used to check for contamination.

13310

Gallace, L.J., H.L. Pujol, and G.L. Schnable (RCA/Solid State Division, Somerville, NJ).
CMOS RELIABILITY.
Rept. No. ST-6561, 1976, 17 pp.

This report, which presents new data on the reliability of CMOS integrated circuits, is divided into four major sections. The first section is a review of background information on MOS integrated circuit reliability, the second section presents new experimental results of comprehensive studies of the reliability of RCA CMOS (or COS/MOS) integrated circuitry, the third section is a discussion of application considerations and outlines RCA electrical specifications for COS/MOS integrated circuits, and the fourth section is a review of the effects of some of the trends occurring in the CMOS industry. Some generalizations and conclusions concerning CMOS reliability are included in the fourth section.

13319

Anon. (NASA, Langley Research Center, Hampton, VA).
ELECTROSTATIC-DISCHARGE DAMAGE TO SEMICONDUCTORS.
NASA Tech. Briefs, Rept. No. LAR-11739, Winter 1976, 29 pp.

Electrostatic discharge damage is responsible for a large number of failures in semiconductor devices. The devices examined, a J-FET, an internally-compensated op-amp and a TTL hex inverter, exhibited degradation in reverse breakdown voltage. The op-amp experienced latch-up at 80% of supply voltage. A hybrid circuit in the TTL hex inverter failed to respond to a digital command. All facilities where failures were being experienced had ESD levels in excess of those needed to produce failures. Semiconductors can be tested for ESD using a 150-200pfd capacitor and 1.5k to 2k ohm resistor model. ESD can be controlled by eliminating generators and relieving charges.

13387

Van Lint, V.A.J. (Mission Research Corp., La Jolla, CA).
MECHANISMS OF SEMICONDUCTOR JUNCTION BURNOUT.
Rept. No. MRC/SD-R-1, Contract No. DNA 001-76-C-0201, August 1976, 62 pp.

Mechanisms of semiconductor junction burnout are reviewed with particular emphasis on parameters controlling variation in energy to achieve second breakdown and device damage. Stabilizing effects promoting uniform current distribution and destabilizing effects promoting filamentary currents are identified. Those destabilizing factors involving thermal changes lead to thermal-mode second breakdown. They include resistivity peak and reverse saturation current. A nonthermal destabilizing effect at high injection conditions leads to current-mode second breakdown. The

dominant mode depends on device parameters and the current level. A minimum energy needed to achieve damage can be estimated for each destabilizing mechanism from mechanisms knowledge.

13430

Nakamura, T., H. Kunita, and H. Ihara (Nippon Electric Co., Ltd., Japan).
ELECTROSTATIC DISCHARGE EFFECTS ON MOS MEMORY ICs.
NEC Research and Development, No. 58, UDC 621.3.049.77: 537.24, July 1980, pp. 15-24.

This paper presents the results of electrostatic discharge simulation tests for MOS memory ICs and describes the analysis of an electrostatic discharge using a simple model. Also, experimental results are described for an MOS memory card and comparison of its electrostatic withstand voltages made with a single MOS memory IC. According to the results, the MOS memory IC damage mode mainly involves destruction of the input protection circuit itself, rather than gate-oxide destruction in MOS transistors. The MOS memory card is sufficiently more resistant to electrostatic discharge than a single MOS memory IC. However, several kinds of devices which are loaded on the card could possibly cause problems.

13455

Porter, D.C., R.D. Price, and L.K. Brooks (Boeing Co., Seattle, WA).
EVALUATION OF PLASTIC LSI CIRCUITS.
Rept. No. D180-22945-1, Contract No. DAAH01-76-C-0455, 56 pp.

Failure analysis was performed on custom P-MOS LSI devices from field removals in a commercial telephone switching application. ESD was found to be one of the causes of failure.

ESD damage levels were investigated simulating human body RC using a 100 picofarad capacitor.

13585

Pancholy, R.K., and T.J. Okl (Rockwell International Corp., Anaheim, CA).
SOS GATE PROTECTION.
Rept. No. RADC-TR-77-134, Contract No. F19628-76-C-0192, April 1977, 68 pp.

This report describes work performed from June 1, 1976 to September 30, 1977 to investigate device design and fabrication methods for CMOS/SOS gate protection devices and circuits to be used with a radiation hardened SOS technology.

13672

Dunn, R., and H.Y. Ho (Xerox, El Segundo, CA).
INPUT PROTECTION NETWORKS ON MOS DEVICES.
Rept. No. CPT-77-6811, Components and Packaging Tech. A2-29/Ext. 1730-3303, December 15, 1977, 33 pp.

The ESD failure levels for MOS devices of various manufacturers are discussed. A failure incidence of 1% on the factory floor occurs with MOS devices having an input protection capability of 500-800v. MOS devices with protection of 1000-2000v had no failures. With multiple sources, vendors of devices with 1000-2000v are preferred. Humans are the primary source of ESD. Partially degraded networks will often continue to deteriorate and become hard failures. Overall test procedures verify the worst stress mode of charge, isolate particularly susceptible inputs and extend data base to several date codes and package types.

13717

Pancholy, R.K. (Rockwell International, Anaheim, CA).
GATE PROTECTION FOR CMOS/SOS.
IEEE - 15th Reliability Physics Symposium, Catalogue No. 77CH1195-7PHY, April 1977, pp. 132-137.

Pulse-power burn-out test results on SOS resistors, high voltage diodes, and thermally grown gate oxides are described. For SOS diffused resistors, the failure power per unit area ranged from 4×10^6 to 3.7×10^5 watts/cm² for pulse widths of 100 nanoseconds to 10 microseconds. The failure mechanism is heat-induced resistivity variation resulting in formation of low resistivity hot spots or filaments. High voltage diode and resistor combinations extended the failure voltages to 325 volts for 100 nanoseconds pulses.

13718

Minear, R.L., and G.A. Dodson (Bell Telephone Laboratories, Reading, PA).
EFFECTS OF ELECTROSTATIC DISCHARGE ON LINEAR BIPOLAR INTEGRATED CIRCUITS.
IEEE - 15th Reliability Physics Symposium, Catalogue No. 77CH1195-7PHY, 1977, pp. 138-143.

Electrostatic Discharge (ESD) can easily damage bipolar integrated circuits. "Second breakdown" of NPN transistor emitter-base junctions is a common failure mode. No external emitter connection is needed for this to occur. ESD current paths, physics of ESD failure, and design concepts for improved ESD resistance are discussed.

13719

Hickernell, F.S. (Motorola, Scottsdale, AZ).
DC VOLTAGE EFFECTS ON SAW DEVICE INTERDIGITAL
ELECTRONICS.
IEEE - 15th Reliability Physics Symposium,
Catalogue No. 77CH1195-7PHY, 1977, pp. 144-
148.

The transducer electrodes of high frequency surface acoustic wave (SAW) devices can be damaged by dc voltage transients as low as 150 volts. Controlled dc pulsed voltage levels applied to SAW device aluminum interdigital electrodes on piezoelectric quartz and lithium niobate have served to define arc discharge and surface fracture conditions affecting device performance. It is recommended that high frequency SAW devices be handled as voltage sensitive parts.

13720

Gallace, L.J., and H.L. Pujol (RCA/Solid State Division, Somerville, NJ).
THE EVALUATION OF CMOS STATIC-CHARGE PROTECTION NETWORKS AND FAILURE MECHANISMS ASSOCIATED WITH OVERSTRESS CONDITIONS AS RELATED TO DEVICE LIFE.
IEEE - 15th Reliability Physics Symposium, Las Vegas, Nevada, ST-6638, April 1977, 30 pp.

All CMOS devices, which are composed of complementary insulated gate field effect transistors, IGFETS, are susceptible to damage by the discharge of electrostatic energy between any two pins. The gate oxide breakdown voltage of a CMOS device is typically 80v. Series resistors and zener diodes can clamp voltages to safe levels. Gate-oxide shorts are the most common failure mode for MOS devices. Theoretical rupture points would be located at any one or more of the four corners of the gate area. In practice, voltages may puncture a weak spot elsewhere. A circuit capacitance of 100 picofarads and series resistance of 560 ohms is used in equivalency to the human body discharge circuit. Life test showed that leakage level associated with the input protection diodes can degrade with operating life especially those prestressed to low level simulated ESD.

13757

Anon. (NASA, Lyndon B. Johnson Space Center, Houston, TX).
SAFE HANDLING PRACTICES FOR ELECTROSTATIC SENSITIVE DEVICES.
NASA Tech. Briefs, Vol. 2, No. 3, Rept. No. MSC-16642, Fall 1977, 19 pp.

The primary consideration for all electrostatic precautions is that they must be continuous. Static sensitive devices shall be

identified with tags and/or labels. Personnel must follow static precautions at a static free work station including grounding of all equipment and using uninsulated metal hand tools. Plain plastic trays shall not be used for unprotected devices. Shunting clips shall not be removed until the item is in a wired circuit or receptacle. Notes on design drawings will include static warnings. DC voltages will be applied before signal voltages when testing MOS and CMOS devices. Antistatic polyethylene shall have its properties protected from degradation by immersion in water.

13974

Antinone, R.J. (BDM Corp., Albuquerque, NM).
SPECIFICATIONS FOR MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE, VOL I.
Rept. No. RADC-TR-78-28, Contract No. F30602-76-C-0308, March 1978, 139 pp.

During a literature search and survey, two types of transients were identified as being important in microcircuit applications. These are electrostatic discharge transients resulting from handling and system transients generated within a system or within the environment in which it operates. It was found that the static discharge transient could be simulated by a decaying exponential pulse with a short circuit time constant of 150 nanoseconds, delivered through a source impedance of 1500 ohms. Provisions were made for varying the peak amplitude of the pulse, but a charging voltage of 1000 volts was found to provide the best screening.

Further, it was found that the system transients could be simulated by a decaying exponential pulse with a short circuit time constant of 10 microseconds, delivered from a 100 ohm source impedance. Provision was made for varying peak voltage. Different technologies require different charging levels, but a level of 50 volts was found to separate microcircuit types into sensitive and non-sensitive categories.

A pulser having the capability of delivering either the static discharge or system transient simulation pulse was fabricated. This pulser was used in subsequent procedure evaluation and sample qualification tests.

13980

Singletary, J.B., W.O. Collier, and J.A. Myers (BDM Inc., Albuquerque, NM).
SEMICONDUCTOR VULNERABILITY VOL. II.
Rept. No. AFWL-TR-73-119, Vol. II, Contract No. F29601-70-C-0019, July 1973, 144 pp.

This report presents, for a selected group of semiconductor devices, pulsed power

burnout data sufficient to establish failure threshold curves. The failure curves were obtained from the experimental failure data using previously developed device failure models. This work is an extension and experimental corroboration of estimated pulse power failure levels obtained from two simple failure models which make use of device handbook parameters.

13986

Wunsch, D.C., R.L. Cline, and G.R. Case (BDM Inc., Albuquerque, NM).
SEMICONDUCTOR VULNERABILITY.
Rept. No. AFWL-TR-73-119, Vol. 1, Contract Nos. F29602-69-C-0132 and F29601-70-C-0019, July 1973, 78 pp.

This report provides an electromagnetic pulse vulnerability listing for a number of selected semiconductor diodes and transistors. The power required to cause failure was determined based on models verified experimentally. For diodes it was found experimentally that the PN junction is more vulnerable in the reverse polarity mode. For transistors testing showed the base emitter junction, in general, to be most vulnerable.

14026

Alexander, D.R., J.B. Almassy, G.L. Brown, D.L. Durgin, C.R. Jenkins, R.N. Randall, A. Unwin, and J.J. Schawarz (Boeing Co., Seattle, WA and BDM Inc., Albuquerque, NM).
ELECTROMAGNETIC SUSCEPTIBILITY OF SEMICONDUCTOR COMPONENTS.
Rept. No. AFWL-TR-74-280, Contract No. F29601-74-C-0008, September 1975, 308 pp.

This report presents the results of a program to expand and interpret the data base for EMP susceptibility of semiconductor components. The primary objective was expansion of the data base. Secondary purpose was to gain improved understanding of failure modes. Failure testing was performed on over 60 integrated circuit and 83 discrete circuit types. Specific tasks addressed were (1) IC failure modes, (2) components, (3) bulk resistance in discretes.

14075

Hickernell, F.S., R.S. Klein (Motorola, Scottsdale, AZ) and M.R. Ware (U.S. Department of Defense, Fort George G. Meade, MD).
ARC GAP INPUT PROTECTION FOR CMOS/LSI CIRCUITRY.
Government Microcircuit Applications Conference, November 9-11, 1976, pp. 350-353.

Arc gaps have been used on MOS chips in conjunction with resistor, capacitor, and

diode networks to provide protection against potentially damaging fast rise-time, high voltage pulses. Such pulses can occur due to equipment transients or electrostatic discharges during handling. There is little information in the literature on the operation of aluminum planar arc gap structures fabricated under standard MOS design and processing rules. A two-phase study was conducted to investigate in greater detail the use of such arc gap structures. The first phase had two objectives. The first was to identify improved arc gap structures with low ignition voltages and fast turn-on times. The second objective was to gain a better overall understanding of arc gap operation. The second phase of the study consisted of taking the glassivated arc gap structure identified as optimal in the first phase and incorporating it on a CMOS LSI logic test chip. The objective was to reduce the chip's susceptibility to damage by fast rise-time, high-voltage pulses.

14077

Huntsman, J.R., D.M. Yenni, Jr., and G.E. Mueller (3M, Static Control Systems, St. Paul, MN).
FUNDAMENTAL REQUIREMENTS FOR STATIC PROTECTIVE CONTAINERS.
Nepcon/West Conference, 1980, 9 pp.

Static protective packaging materials must prevent damage to static-sensitive components from triboelectrically generated charges and also electrostatically shield them from the effects of charged objects.

Protection of static-sensitive components from the two types of static charges by using protective bags, tote boxes and dip tubes is discussed.

14082

Yenni, D.M., Jr., and J.R. Huntsman (3M, St. Paul, MN).
GUARDING ICS AGAINST STATIC DISCHARGE.
Electronics, Vol. 53, No. 16, J-SGAS (801.0)R1, July 17, 1980, pp. 115-121.

Major advances in processing are already resulting in very-large-scale MOS integrated circuits with increased packing density, higher operating speed, and lower operating power. However, the finer lines and thinner oxide layers of these new superchips will aggravate a problem that has plagued MOS manufacturers and users since the emergence of these devices: device failure from electrostatic damage.

Fortunately, effective methods and materials for handling and packaging static-sensitive devices have been developed. For MOS devices (whether individual parts or mounted on printed-circuit boards), transpor-

tation in bags, tote boxes, or storage tubes made of special metallized film laminates or carbon-loaded plastics serving as static-protective materials is required. The use of older, military-specified materials has resulted in device damage and failure.

14085

Hart, A.R., and R.P. McCluskey (U.S. Navy, Naval Electronics Laboratory Center, San Diego, CA).
RF PROTECTION PROVIDED BY PACKAGING MATERIALS.
Rept. No. NELC-TD-204, Sept. 27, 1972, 29 pp.

An investigation into the protection various aluminized packaging materials provide microelectronic devices in radar RF environments was conducted. It was determined that packaging shielding materials could protect microelectronic devices in RF environments.

The packaging materials used in the investigation are described along with their ability to protect devices from various RF sources.

14119

Ignaczak, L.R. (Lewis Research Center, Cleveland, OH).
PORTABLE SPARK-GAP ARC GENERATOR.
Nasa Tech Briefs, Rept. No. LEW-12886, Spring 1978, pp. 10-11.

A self contained spark-gap arc generator has been developed to simulate the electrical noise from the discharge of a static charge. The arc potentials are variable from 3 to 15kv with the energy per arc .01 to .25 joules or greater. Application has been found in testing spacecraft components. Spacecraft operating in synchronous altitudes have been surface charged to 11000 volts.

14173

Brown, W.D. (Sandia Laboratories, Albuquerque, NM).
SEMICONDUCTOR DEVICE DEGRADATION BY HIGH AMPLITUDE CURRENT PULSES.
IEEE - Trans. on Nuclear Science, Vol. NS-19, No. 6, December 1972, pp. 68-75.

If the short duration, high amplitude current pulses produced by gamma radiation in a nuclear environment flow through semiconductor devices permanent damage may result in the form of a low impedance shunt across the device junction. The current required to initiate damage in the forward direction is 5 to 15 times that necessary to initiate damage in the reverse direction. The emitter base junction is most vulnerable.

The area used to calculate power density is the active emitters sidewall area. Only a fraction of the sidewall area is involved for

deep junctions. The emitter periphery plays a most important role in determining the threshold level of a device. Deeper emitter diffusions produce more tolerant devices.

Annealing of devices at 300°C for times of 1/2 to 3 hours produced significant recovery for some devices.

14284

Porter, D.C. (Boeing Co., Seattle, WA) and M. Bahan (U.S. Army Missile Research and Development Command, Huntsville, AL).
FAILURE ANALYSIS OF PLASTIC ENCAPSULATED CUSTOM LSI CIRCUITS.
Symposium on Plastic Encapsulated/Polymer Sealed Semiconductor Devices for Army Equipment, May 10-11, 1978, pp. 42-53.

A plastic encapsulated 40 pin, 630 gate LSI PMOS circuit on a 30,000 square mil chip was introduced into commercial service in 1974. By 1977, 3.7×10^8 unit hours had been accumulated and a failure rate of 0.042%/1000 hours was demonstrated. Failure analysis was performed on 150 devices removed during the maintenance cycle with date codes spanning two years. One third were good units. Of the remaining, 55% were devices which had never worked properly and were sent to the field because they were not tested properly. Detailed autopsy efforts were completed on 70 units and no failures traceable to the packaging technique were encountered.

14646

Frankel, H.C. (U.S. Army Electronics Research and Development Command, Fort Monmouth, NJ).
THICK FILM RESISTOR ELECTROSTATIC VULNERABILITY TEST STUDY.
Rept. No. MFR-78-4, June 1978.

This report describes a Hybrid Microcircuit and Assembly Team (HM&A) investigation to develop the relative vulnerability of various thick film materials to degradation by ESD. Test specimens of alumina substrates with 31 resistors mounted were subjected to Corona, Tesla, and Polyurethane sheet tests. Measurements were made to determine the relative influence of device factors to vulnerability. Factors considered were materials, geometry, and location on substrate. Material effects were compared for observable differences to determine the most susceptible configurations.

14808

Costache, G., D. Goulette, and S. Xavier (Bell Northern Research).
ZEROING IN ON STATIC DISCHARGE.
Telesis, Vol. 5, No. 5, October 1977, pp. 148-153.

In the course of investigations over the past two years, the electromagnetic engineering department of Bell-Northern Research has reached a much better understanding of the static discharge process and how it affects equipment.

The Bell Northern research investigation explored the radiation aspect of the phenomenon in greater detail.

The electrostatic spark jumps right at the heart of the equipment and so is a sharp spike. The current and radiated field it creates, though extremely brief, can produce significant effects. They depend on the rate of change of voltage, not on the voltage directly.

Measurement probes had to be specially made to pick up the transient currents and radiated fields. As discharge current in a cabinet travels along its conducting frame it radiates energy. Other items such as cables add their own pattern. Both the electrical and magnetic components of these patterns were measured.

Radiation patterns can be contained using transient suppressing devices, shelf and rack grounding, and damage can be prevented by keeping sensitive circuit tracks away from structural or circuit members likely to carry large discharge currents.

14905

Dicken, H.K. (Integrated Circuit Engineering, Scottsdale, AZ).
INTEGRATED CIRCUIT FAILURE MODES.
Defense Microelectronics, EW/DE, October 1978, pp. 66-68.

The following are some of the stresses that will cause integrated circuit failures: radiation (alpha, beta, gamma), static electricity, vibration, power line transients, excessive hot or cold, temperature cycling, and moisture. Special conditions apply to each mode; an example is vibration. Bonding wires resonate at 30 to 50 KHz. The presence of such frequencies may cause this failure.

14960

Eichel, F.G. (Givaudan Corporation).
ELECTROSTATICS.
Chemical Engineering, March 13, 1967, pp. 153-167.

Generation of static electricity by movement of low conductivity fluids relative to each other causes the accumulation of hazardous electrical charges. This report discusses the origin and nature of electrostatic phenomena, gives methods for calculating their magnitude in practical engineering units and describes techniques for controlling and minimizing static electricity in process operations. Values for the

dielectric constants, specific conductivities, and minimum ignition energies of various materials are presented.

14961

Anderson, D.C. (Richmond-Division of Dixico Inc., Redlands, CA).
ELECTROSTATIC DAMAGE PREVENTION: AN OVERALL VIEW.
1978 American Defense Preparedness Association: Packaging, Handling, and Transportability Division, November 15, 1978, 17 pp.

For static protection techniques to be effective they must be applied at all times and places where electrostatic damage might occur. Simple demonstrations help to bring personnel to see the realities of static. Tape unrolled over an ash tray will pick up ashes, indicating a surface charge of 4000 volts. A neon bulb in a plastic bag will glow after being rubbed with a sweater (Anderson Effect). The point should be made that nonconductors generate charges, conductors pick them up and deliver.

14962

Kirk, W.J., L.S. Carter, and M.L. Waddell (Bendix Corp., Electronic Products Dept., Kansas City, MO).
ELIMINATE STATIC DAMAGE TO CIRCUITS.
Electronic Design, Vol. 27, No. 7, March 29, 1976, pp. 80-85.

Observed effects of ESD on JFETs included changes in the reverse breakdown voltages. The capacitance value of the discharge model influenced the voltage required to degrade the transistor. Repeated discharge pulses at voltages below the degradation level did not significantly degrade the device. Half of the JFETs showed a decrease in breakdown voltage with no significant change in the transconductance or pinch-off voltage.

Human operator-generated voltages were also measured. Peak generated voltages were observed at points where the feet of the subject partly or totally lost contact with ground plane. Conductive floors and spraying with low resistivity solvents helped to reduce environmental static.

14963

Petrick, J.T. (U.S. Navy, Naval Weapons Laboratory, Dahlgren, VA).
DISCHARGE OF AN ELECTROSTATICALLY CHARGED HUMAN.
Proceedings of the Sixth Symposium of Electro-explosive Devices, July 9-10, 1969, Franklin Institute Research Laboratories, Philadelphia, PA, 17 pp.

The results of tests outlined herein will provide valuable information that will enable valid electrostatic sensitivity tests for explosives and also aid in explaining the variation of human skin resistance with applied voltage and in determining the depth at which the charge having most effect resides. The results will also enable the analysis of possible bodily dangers involved in discharges of this nature and give considerable insight into the RF response of the human body.

14964

Amicone, R.G., C.T. Davey, and J.B. Campbell (Franklin Institute Research Laboratories, Philadelphia, PA).
ELECTROSTATIC HAZARD TO ELECTROEXPLOSIVE DEVICES FROM PERSONNEL-BORNE CHARGES.
APL-65-1, February 1965, 26 pp.

The occurrence of accidents involving electroexplosive devices (EED) has renewed interest in the static electric charge that can be accumulated and transferred by personnel. This monograph develops an electrical model to use in rough checks of EED sensitivity to personnel-borne charges: a series circuit of 500 pf capacitance and 5000 ohms resistance that can be charged to potentials up to 20 KV.

It is shown that very sensitive EED's can be fired with charges developed by personnel and it stresses caution with respect to so-called insensitive types which may be susceptible in the pin-to-case mode.

The study indicates that the hazard may be greater than anticipated and it is recommended that these limited studies be supplemented with additional investigations to furnish a firmer quantitative basis for action.

14965

Anderson, D.C. (Richmond-Division of Dixico Inc., Redlands, CA).
COMMON PLASTICS: MAJOR ENEMY OF STATIC-SENSITIVE ELECTRONICS.
Evaluation Engineering, Vol. 17, No. 2, March/April 1978, pp. 22-24.

In almost every case of electrostatic discharge damage encountered in the electronic industry, the source of the static is everyday plastic, including synthetic textiles, which are, after all, spun plastics. CMOS devices, precision resistors and countless similarly static-sensitive components are destroyed or damaged daily by this simple but misunderstood phenomenon. Even when static is recognized as the principal cause of damage, most companies fail to envision the simplicity of proper protection. They often waste money on expensive "overkill" techniques, or ignore the problem as being too expensive to correct.

14966

Anon.
HELPFUL TIPS ON COPING WITH STATIC ELECTRICITY.
Evaluation Engineering, Vol. 16, No. 4, July/August 1977, pp. 42-43.

Three devices examined illustrated ESD damage. An n-channel JFET exhibited a degradation in reverse breakdown voltage from 83v to 28v when subjected to a single discharge of 6000v. An internally compensated op-amp experienced output "latchup" to about 80 percent of supply voltage. The failure was traced to a shorted MOS compensation capacitor caused by a discharge of 1500 to 2000 volts. Finally a TTL hex inverter failed due to a beta reduction from 15 to 2. This failure was reproduced with charge of 1500 to 2000v.

14967

Anon.
COPING WITH STATIC ELECTRICITY - PART II HELPFUL IDEAS AND A DO-IT-YOURSELF SOLUTION.
Evaluation Engineering, Vol. 16, No. 5, September/October 1977, pp. 30-31.

Numerous down-to-earth tips were given including the following: conductive chairs and floors should be used as much as possible. Spray cleaning solutions have been prone to cause static. Trichloroethylene is a typical example of a cleaning solution that causes problems.

14968

Anon.
COPING WITH STATIC ELECTRICITY - PART III PRECAUTIONARY MEASURES.
Evaluation Engineering, Vol. 16, No. 6, November/December 1977, pp. 44-47.

Primary methods of coping with static electricity include using smocks made of conductive materials, controlling relative humidity, and ionized air precipitators.

Restricting personnel from wearing static charge generating clothing can result in political turmoil and regulations which would be impossible to enforce. Conductive smocks reduce such restrictions and need for enforcements.

Leakage rates for capacitive charged static voltages can be increased in a higher humidity environment; the optimum humidity range is 40-50%.

In situations where grounding and controlled relative humidity are impossible or impractical ionized air precipitators can be employed to reduce static discharge hazards.

14969

Anon.
COPING WITH STATIC ELECTRICITY - PART IV
DESIGN PRECAUTIONARY MEASURES.
Evaluation Engineering, Vol. 17, No. 1,
January/February 1978, pp. 56-62.

MOS input protection techniques are increasing diode size, using diodes of both polarities, adding series resistors and utilizing a distributed network effect.

Design precautions dictate avoiding crossunders beneath strips connected to external pins. Oxide thicknesses and the distances between contact edges and junctions should be carefully controlled. Transistors can be better protected by increasing the emitter perimeter adjacent to the base contact. Likewise "phantom emitters" incorporated by a second emitter diffusion shorted to the base contact add additional extrinsic base resistance ballast.

To avoid latchup in CMOS circuits, limit input current to 10 mA. For particularly sensitive CMOS devices, outputs should be isolated from cable lines via resistors and by clamping each line to VDD or VSS via high speed switching diodes.

In general all inputs and outside terminations must be protected via some circuit or device. All ESD sensitive items must be labeled as such and handled appropriately.

14970

Anon. (Storage Technology).
COPING WITH STATIC ELECTRICITY-PART V
STC'S NEW IC STATIC ELECTRICITY SPEC.
Evaluation Engineering, Vol. 17, No. 2,
March/April 1978, pp. 16-21.

STC has initiated a wafer level oxide test that must be performed before the unit is packaged. Intel has found that testing of MOS devices with overvoltage proved more effective in eliminating potential failures than normal 125°C 168 hours burn-in. This was true, as explained, because the dominant failure mode on MOS was and still may be poor oxides.

Anti-Static Air Cap designed to cushion as well as give anti-static protection to electronic components and materials has been introduced by Sealed Air Corporation. 3M has introduced a three layer film consisting of a conductive metallic outer layer, a middle layer of polyester film and a final inner layer of heat-sealable polyethylene film.

14971

Anon.
COPING WITH STATIC ELECTRICITY-PART VI STATIC AWARENESS IS KEY TO PROTECTION.
Evaluation Engineering, Vol. 17, No. 3,
May/June 1978, pp. 45-48.

The primary consideration for all electrostatic (static) precautions is that they must be continuous. Just as a precision clean part must have a maintain cleanliness requirement for all operations, a static sensitive item must have a 'maintain static free' requirement from the original component manufacturer through final production assembly.

In the vicinity of unprotected static sensitive devices avoid activities which tend to be friction producing, such as putting on or taking off smocks, wiping feet, rubbing hands, etc. Develop the habit of first touching the grounded bench top before handling static sensitive items. All equipment used at a static free work station shall be grounded, such as soldering irons and tips, lead forming tool, test fixtures and lights.

14972

Huntsman, J.R., and D.M. Yenni (3M, St Paul, MN).
COPING WITH STATIC ELECTRICITY-PART VII
A NEW TECHNOLOGY IN TRANSPARENT STATIC PROTECTIVE BAGS.
Evaluation Engineering, Vol. 17, No. 4,
July/August 1978, pp. 48-50.

Because of the intrinsic deficiency in antistatic polyethylene, Static Control Systems of 3M Company has developed a new packaging material to provide transparency and the shielding effectiveness more like that of a metallic conductor. It is unique in having very low surface resistivity (less than or equal to 10^4 ohm/sqcm) but very high volume resistivity (greater than or equal to 10^{15} ohm-cm). It is a multilaminate sheet of three electrically distinct layers.

The humidity-independent conductive outer layer has a metallic coating providing a faraday cage-like protective shielding. The center layer is polyester, which provides good mechanical strength and puncture resistance. The inner layer consists of antistatic polyethylene which is heat sealable.

An ESD pulse in an antistatic polyethylene bag lasts 60-70 milliseconds and has a peak of 3000 volts. The pulse in a static shielding bag lasts just several microseconds with a peak of 75 volts.

14973

Kroeger, J., and B. Threewitt (Signetics, Sunnyvale, CA).
HEED THE LIMITATIONS OF MOS I/O CIRCUITRY.
Electronic Design, No. 6, March 15, 1974, pp. 98-105.

Because of their high d.c. impedance, MOS inputs can be damaged by static charge accumulation.

Even with protection, problems can arise with MOS circuits. Soldering with an unisolated iron, wearing silk smocks and leaving pins unterminated increase the probability of discharge damage.

A noncatastrophic failure mode occurs when input pins are left open. For example control inputs such as recirculate for a shift register, that are left open may cause a device to be in the wrong operating mode if sufficient charge is accumulated to reach the input switching threshold voltage. The device would not necessarily be damaged but would appear to malfunction.

14974

Keers, J.J. (3M Company, St. Paul, MN).
NUCLEAR STATIC ELIMINATORS - THEIR DEVELOPMENT AND USES.
Research and Development, March 1966, pp. 26-29.

The radioactive static eliminator is a self powered ionizer of air molecules. The development of 3M brand radiating microspheres presents a convenient method of safely containing the isotopes. The microsphere is a ceramic bead in which the isotope can be absorbed, then permanently sealed. The size of these beads is very small, 20-80 microns in diameter.

The use of a radioactive neutralizer for a particular application depends on a number of considerations. Cost considerations are in favor of tinsel and wire brushes if a reduction of 30000 to 10000 volts is required. If a reduction of static charge from 5000 to 500 volts is required, then a radioactive system is a must.

14975

Erickson, D.
ANTISTATIC EQUIPMENT AND TECHNIQUES.
Electronic Packaging and Production, February 1979, pp. 74-96.

Static electricity, also referred to as ESD (electrostatic discharge), has its real danger arise from the illusive "docility" of its nature. Static problems are unusual in that it is often more difficult to identify the problem than to solve it. One of the best instruments for identifying the nature of ESD damage is the SEM (scanning electron microscope).

Planning for minimizing static charges involves taking a look at all poor conductors that move. In practice there are often too many nonconductive materials involved directly or indirectly to ban all. Antistatic soldering/desoldering equipment and device carriers are available from a number of

manufacturers. Conductive bags are often used for packaging protection. For the occasional requirement of antistatic coating, liquid immersion or sprays can be a practical answer. Conductive trays, containers and tote boxes help make static protection continuous. Complete static work stations are available also. Static clothing including smocks of various fiber construction and tools designed to reduce static damage are being offered in various styles. Portable work stations grounding kits complete the "arsenal".

14976

Huntsman, J.R. (3M, St. Paul, MN).
REDUCING ELECTROSTATIC DAMAGE USING PROTECTIVE MEASURES.
Electronic Packaging and Production, Vol. 18, No. 10, October 1978, 3 pp.

There is no way to totally eliminate static sensitivity; but, following common-sense antistatic procedures do a lot to protect your circuits, increase yields, improve MTBFs and lower costs. First, test all components and devices for static sensitivity. If vendors perform satisfactory testing and certification, only spot-checking is necessary. Second, specify static-shielding packaging on all static-sensitive devices coming from outside sources. Third, counsel assembly/manufacturing personnel regarding types of devices that will require special static protection. Fourth, give antistatic measures publicity; keep reminding everyone you know that static is a problem and encourage protective measures. The solution is largely one of attitudes and work habits.

14977

Kohlhaas, P. (3M Company, St. Paul, MN).
CONTROLLING POTENTIAL STATIC CHARGE PROBLEMS.
Electronic Packaging and Production, Vol. 17, No. 1, January, 1977, pp. 71-73.

While some skepticism existed one or two years ago as to whether static charge is responsible for high failure rates, it is now an accepted fact that some MOS devices can be destroyed by less than 100v of static charge.

You can ground conductive materials but you can not ground nonconductive materials. As a result anything less than a complete safeguard system is only partial protection. Clothing is not the only nonconductive material that is brought into the work station area. Items such as plain plastic tote boxes, plastic work-order sleeves or covers, candy wrappers, etc., all have the capability of blowing or degrading static sensitive electronic devices.

14978

Schreier, L.A. (Hughes Aircraft Company, Culver City, CA).
ELECTROSTATIC DAMAGE SUSCEPTIBILITY OF SEMICONDUCTOR DEVICES.
IEEE - 16th Reliability Physics Symposium, 1978, 7 pp.

Devices were chosen for ESD degradation threshold testing on the basis of high failure rates in manufacturing environments. Critical electrical parameters were measured before and after each simulated ESD. A change of more than 10 percent of the specification was considered a failure.

In addition, devices were pulsed at 75 percent of the ESD degradation threshold and then subjected to burn-in. In most cases, the critical parameter change was dramatic. Device sensitivity ranged from 100v for MOSFET to above 3KV for JFET.

The data gathered on burn-in of devices suggests that there is no long term first-order degradation mechanism if ESD levels are kept below the ESD degradation threshold.

14980

Mendelsohn, A.
TRANSIENT SUPPRESSORS.
Electronic Products, Vol. 21, No. 10, March 1979, pp. 31-40.

A transient is a brief voltage pulse or surge of current that can wreck havoc in milliseconds. It may cause slow degradation, erratic operation or catastrophic failure in semiconductors, insulation dielectrics and switch and relay contacts.

Combining or "staging" of protective devices can provide overall protection unattainable with one device alone.

Silicon avalanche diode suppressors can be efficient alternatives to bulky selenium stacks used to protect SCR's triacs and diodes in solid state power control technology. Exhibiting extremely fast turn-on times these devices are available in a dozen voltage breakdown ratings between 500 and 1600 volts.

Tin, zinc, or bismuth oxide voltage dependent resistors (VDRs), often referred to as MOVs (metal oxide varistors), offer a cost effective means of dealing with high, medium, and low level transients. MOVs change resistance nonlinearly in response to applied voltage. A gradual deterioration in characteristics occurs each time a MOV conducts.

Prior to making an ultimate judgment on any given type of suppressor, a final analysis must take into account all parameters and the end product protection level desired.

14981

Williams, J.H. (General Dynamics, Pomona, CA).
COPING WITH STATIC ELECTRICITY - PART VIII
ELECTROSTATIC DAMAGE TO SEMICONDUCTOR DEVICES: CAUSES AND CURES.
Evaluation Engineering, Vol. 17, No. 5, September/October 1978, pp. 46-50.

All components are static sensitive to some degree. The smaller the part, the less power it can dissipate and the more likely it is to be damaged by an electrostatic discharge.

Even now industry cannot agree on the most effective method to provide adequate protection. It frequently resorts to an expensive "overkill" practice or takes no action at all because it feels that the precautions are too expensive.

Industry experience with solid state devices has revealed numerous cases of actual or potential damage from static discharges. One of the more dramatic incidents occurred in 1964 when a polyethylene drape used as a dust cover for a Thor Delta third stage solid propelled rocket created an estimated 28000 volts as it was unrolled and accidentally ignited the rocket by inducing a charge on its igniter squib.

14982

Anon.
COPING WITH STATIC ELECTRICITY - PART IX METAL FILM RESISTORS CAN BE ZAPPED BY STATIC ELECTRICITY.
Evaluation Engineering, Vol. 17, No. 6, November/December 1978, pp. 36-38.

Some evaluation engineers are not aware that precision metal film resistors are subject to damage by static electricity, and they are shocked to discover the problem.

The zapping problem occurs during sampling where some resistors are pulled out of the lot for testing. The technician walks across the room, building up a static charge on his body. Upon touching the resistor, he zaps it and it is no longer a precision film resistor with a stability of .1%. Instead, it is now a film resistor with a .2-1% tolerance.

14983

Brown, R.T. (IPL Systems, Waltham, MA).
COPING WITH STATIC ELECTRICITY - PART X.
Evaluation Engineering, Vol. 18, No. 1, January/February, 1979, pp. 54-58.

Most MOS devices contain zener diode protection to ground or substrate. Zener diodes can bleed off excess static voltages, but there is normally no protection on output pins.

To say that some ICs are not susceptible to static discharge is unrealistic, for there is a potential that can damage any chip.

The characteristic of a static charge to spread itself thin (cover all conducting surfaces) makes it a problem. The solution then is to establish a chip or board ground and ground yourself to it before work starts.

Some of the body characteristics that influence voltage levels are the dielectric constants of the clothing worn and the skin moisture level of the body.

14984

Shelton, S. (Simco Company, Lansdale, PA).
COPING WITH STATIC ELECTRICITY, PART XI WHY
USE ANTISTATIC GARMENTS?
Evaluation Engineering, Vol. 18, No. 2,
March/April 1979, pp. 28-30.

Antistatic garments generally are somewhat conductive in nature and are normally worn over street clothing. In effect, they provide a type of "screen" to aid in reducing strong static fields which could induce damaging static charges on nearby electronic devices. The antistatic garment should cover all static generating clothing where possible and should at some point make contact with the person's body to provide a resistive path to ground.

A strong static field may be associated with charged clothing and radiates from it. This strong static field can induce an opposite charge on an isolated object within the field without any point or direct contact with the person's charged clothing. As long as this person remains in proximity to the object it will remain charged.

The individual being of different potential than the component causes a static discharge which may either degrade or destroy the sensitive device.

14985

Johnson, W.D. (Hughes Aircraft Company, Los Angeles, CA).
COPING WITH STATIC ELECTRICITY - PART XII
STATIC AWARENESS TRAINING FOR FACTORY
PERSONNEL.
Evaluation Engineering, Vol. 18, No. 3,
May/June 1979, pp. 68-72.

Product reliability and production costs are directly affected by static electricity. Static controls will improve product reliability and reduce production rework or scrap. "Static Safe" ESD protection must be maintained at all times. Personnel must maintain all static free requirements for sensitive devices from the original source of manufacture through all assembly operations to point of use.

All work stations must be essentially equipped with an anti-static conductive work surface, conductive wrist band and operator ground straps, "static safe" approved label, caution signs, caution labels, static free shop carriers and approved soldering irons. Conducting materials, handling containers and packaging supplies are also necessary.

14986

Klein, W.G. (United Technical Products, Westwood, MA).
STATIC ELECTRICITY: PROBLEMS AND SOLUTIONS IN
COMPUTER FACILITIES.
8 pp.

Although static problems are well-recognized, their causes are not widely understood. Floor coverings (particularly carpeting) and the relative humidity are known generally to play important roles.

The matter of degree of homogeneity of conductivity is very important as most practical permanent antistatic systems involve a two-phase approach in which a small amount of discrete conductive material is added to a textile system which is otherwise nonconductive. An example of this is the introduction of conductive filaments at a predetermined spacing throughout a carpet. It has been found experimentally that conductive elements with a resistivity on the order of 10^8 ohms/cm constitute good electrostatic conductors.

One frequently hears requirements for floor coverings having static property less than 1KV or even .5KV. It is the opinion of the author that, in the absence of a specified shoe, no floor covering material can under dry conditions permanently assure performance below the 2KV level.

14987

Yenni, D.M. (3M Company, St. Paul, MN).
BASIC ELECTRICAL CONSIDERATIONS IN THE DESIGN
OF A STATIC-SAFE WORK ENVIRONMENT.
Presented at Nepcon-West Conference, Anaheim,
CA, 1979.

Static damage of components is fast becoming one of the most significant problems plaguing the electronics industry. Technological advances in IC manufacture such as ion implantation, ion beam milling and electron beam direct current lithography all make possible devices with higher circuit densities, higher unit performance and quite often higher static susceptibility.

Fortunately, the problems associated with static charges in the electronics environment can be controlled. To accomplish this, programs must be instigated throughout the manufacturing cycle to increase static

awareness in all personnel who handle static sensitive devices. Once educated, personnel must be provided with the proper equipment to implement these techniques of static control. At the work bench this includes conductive table mats, conductive wrist straps, conductive floor mats and ionized air.

The purpose of this paper is to discuss the basic electrical requirements of the conductive components of this system in relation to the individual function each provides.

14988

Sinclair, R.E. (Lockheed Aircraft, Sunnyvale, CA).
SEMICONDUCTOR CIRCUIT FAILURE AND PROTECTION IMPLEMENTATION SCHEMES.
Nuclear EMP, Rept. No. PEM-21, 15 pp.

The transient pulse failure mechanism in semiconductor devices and thermal models for heat generation and transfer within the device are described. From these, formulas and criteria are developed to enable calculation of the critical energy for permanent damage. This is the applied pulse energy necessary for device failure. From these results, device protection criteria are developed. Protection resistor values can be calculated which permit protection of devices for specified critical energies and applied energy levels.

14989

Keller, J.K. (Lehigh University).
PROTECTION OF MOS INTEGRATED CIRCUITS FROM ELECTROSTATIC DISCHARGE.
Presented to the Graduate Committee of Lehigh University, 1976, 50 pp.

One of the primary purposes of this paper is to present a realistic model of the human body for static electric protection purposes. It is extremely important that the model be highly correlated to actual human characteristics. It is generally agreed that the best model for the human body is that of a charged capacitor, a series resistor and a relay type switch. Human body capacitance can be related to the subject's height and other physical parameters such as shoe thickness and area. Likewise human body resistance varies for different conditions (humidity, skin conditions, etc). Extensive study indicates that the human body "switch" bounces several times before making final contact. In simulated testing a high voltage relay was discovered to closely resemble the human discharge.

Protective input resistors, when fabricated from non-diffused material so that no parasitic diode results, are of little value. To be effective they must be combined with a device that will prevent the gate

voltages from reaching destructive levels. Fabrication of input protection diodes must be such that the reverse breakdown voltage of the diode is less than that of the gate oxide. Thick oxide, punch through, gated punch through and field plate diodes are all designed to do this. Spark gaps are also useful precautionary devices although certain precautions with nonconducting encapsulants must be taken.

The most versatile and effective network is a gated punch through device in combination with a spark gap which may extend the protective limit to five kilovolts.

14991

Singletary, J.B., and J.A. Hasdal (BDM, Albuquerque, NM).
METHODS, DEVICES, AND CIRCUITS FOR THE EMP HARDENING OF ARMY ELECTRONICS.
Rept. No. ECOM-6085-F, Contract No. DAAB-07-70-C-0085, DA Project No. 1H6 62705 A 440, Task 01 BDM/A 24-71-TR, June 1971, 55 pp.

Electric and magnetic pulse fields generated by nuclear weapon detonations can temporarily or permanently disable military electronic equipment. Communications/electronic systems are particularly vulnerable where the pulse energy may be coupled into antennas and cables and thereby affect highly sensitive circuitry.

In the higher range of voltage applications for protective devices the use of spark gaps immediately comes to mind. Tests conducted indicate that when response occurs on a test pulse rise the response is linear. At longer pulse duration when applied voltages still exceed d.c. sparkover voltages, longer response occurs. The minimum response time for a gap may be interpreted as the sum of the times required for formulation of avalanche discharge. As a protective device a spark gap is obviously better as its response time is decreased.

Opposed series diode protection indicates this configuration is restricted in its range of passed frequencies and are susceptible themselves to EMP damage. Opposed parallel diodes offer slightly better frequency response for those applications where low voltage operation is possible. Opposed parallel diode stacks offer higher voltage protection but frequency response is lowered and response time increased.

Various diode configurations indicate usefulness in the voltage range below 90 volts, the lower limit of spark gap protection.

Supplementary analysis relates the spark gap parameter impulse ratio as defined as the ratio of surge peak voltage to static breakdown voltage. Widely observed facts indicate that higher impulse ratios produce faster response times. Analysis of the kanal

equation points to the underlying factor for impulse ratios to be the ionization multiplication factor.

14992

Schade, O.H., Jr. (RCA Corporation).
ADVANCES IN BiMOS INTEGRATED CIRCUITS.
RCA Review, Vol. 39, No. 2, June 1978, pp. 250-277.

The transfer characteristics of BiMOS MOSFET's throughout the nanoampere to milliampere range are presented, and their use in current mirrors, amplifiers, oscillators, and timing circuits is discussed. Linear operation in the subthreshold region is shown to provide extended performance in micropower integrated circuits, with transconductance levels similar to those of bipolar devices. Advances in MOSFET pair-matching are analyzed; commercial capabilities are described; and the combination of subpicoampere input-bias levels with protected-gate devices is shown to be practical at elevated temperatures.

14993

Hart, A.R. (U.S. Navy, Naval Electronics Laboratory Center, San Diego, CA).
PERTURBATIONS IN THE RESPONSE OF INTEGRATED CIRCUITS TO INJECTED RF POWER.
Rept. No. TN 3032, Code No. 4600, NELC R501, August 22, 1975, 32 pp.

The RF vulnerability of integrated circuits was investigated. Both interference and failure testing were performed to define the relationships between RF vulnerability and (1) fabrication technology (CMOS vs. bipolar), (2) circuit function (NAND, NOR, etc), and (3) manufacturer.

Wide variations in interference and failure power levels were found both within a device type (e.g., 5474) and between manufacturers. These variations can produce differences between one device and another by as much as 20dB for the same application. As yet, electrical screens have not been useful in predicting the vulnerability levels. It was also found that interface testing did not predict the failure power level of a device.

Based on the ICs used in the tests, CMOS devices are not susceptible to interference as bipolar (either linear or digital). But little difference exists between bipolar and CMOS for RF failure susceptibility. Bipolar linear devices appear to be the most susceptible types of devices to RF interference although some digital bipolar devices may approach these levels.

The electrical indication of interference or failure was also found to vary widely. This fact makes the diagnosis of system failures and their causes even more difficult.

14994

Kirkpatrick, C.F. (Rockwell International, Downey, CA).
PROTECTIVE REQUIREMENTS FOR ELECTROSTATIC SENSITIVE ELECTRONICS.
Rept. No. MF0004-047, Code No. 03953, November 19, 1979, 20 pp.

The primary consideration for all electrostatic precautions is that they must be continuously performed. In the vicinity of unprotected static sensitive devices avoid activities which tend to be friction producing. Before performing any work operate ionized air blowers for two or three minutes until there is no residual charge at the work area as measured by a static meter.

The antistatic precautions taken to protect individual static sensitive devices shall also be taken as applicable to protect assemblies.

Dielectric strength or insulation resistance tests are not recommended for equipment containing static sensitive devices. All unused inputs of MOS and CMOS devices must be connected to either device supply or ground. DC voltages shall always be applied before signal voltages and signal voltages shall always be removed before DC voltages.

Facilities shall include static free work stations, including metal frame work benches and conductive surfaces.

Velostat (conductive black polyolefin) is electrically conductive. Carbon particles impregnated in the poly provide volume conductivity. Sloughed particles of carbon from this material preclude its use in most precision clean operations.

14995

Flood, J., and H.L. Pujol (RCA COS/MOS Digital Integrated Circuits).
GUIDE TO BETTER HANDLING AND OPERATION OF CMOS INTEGRATED CIRCUITS.
High Reliability Devices, 1976, pp. 6-8.

All CMOS devices are susceptible to damage by the discharge of electrostatic energy between any two pins. Their extremely high input impedance lends itself readily to the buildup of electrostatic charges.

Basic protection of these devices starts with personnel and materials all at the same or ground potential. Precautionary handling is extremely important. For example: in the sequence in which bonds are made, the V_{DD} (device supply) connection should always be made before the V_{SS} (ground) bond. Automatic handling equipment should include the use of ionized air blowers in addition to good grounding. PC boards incorporating ICs should have shorting bars installed prior to assembly.

Care must be taken in the use of input resistors as they may reduce speed because of the added RC delay.

Operation above maximum ratings can force CMOS devices into a PNP(SCR) latch-up mechanism. "Latchup" is considered to be the creation of a low resistance path between the power supply and ground on a circuit during an electrical pulse. For latchup to occur combined beta gain is greater than 1, all junctions are forward biased, and the bias supply must supply current above holding.

14996

McAteer, O.J. (Westinghouse Corp.).
ELECTROSTATIC DAMAGE IN HYBRID ASSEMBLIES.
IEEE Reliability and Maintainability Symposium, Catalogue No. 78CH1308-6R, Catalogue No. ISSN 0149-144X, January 17-19, 1978, pp. 434-442.

Recent experience with hybrid assemblies has included ESD problems in numerous part types including bipolar devices, thin film substrates, ECL and CMOS devices. The base-emitter junction was degraded to a low resistance short and the reverse I-V curve was shifted several tenths of a volt due to the effect of ESD on several Westinghouse bipolar op-amp chips for hybrid usage. Typical damage could be induced by standing up from a lab stool and touching the package lid. Beta degradation may also occur because of ESD.

The physical mechanism of damage is aluminum transport that may thermally crack the silox overcoat in severe cases. The shorts can occur between metallization crossovers in multiple layer metallizations. A quasi-square anomaly often is detected by SEM after static discharge. This square pattern was observed in simulated ESD testing.

ESD failures were observed to cause several tenths of a volt shift in the emitter outputs of ECL devices. Damaged oxide over the E-B junction could be seen near one end of each emitter contact area. Multiple damage to ECL from ESD resulted in several cases of shorts between V_{CC} and ECL outputs, also in leaky reverse base-emitter junctions.

The cholesteric liquid crystal method was used to detect the exact short site caused by ESD in several CMOS devices. Subsequent testing under various loads found CMOS devices least susceptible with nothing attached to any nodes rather than having one or more nodes grounded.

14997

Wetherald, M. (Tektronix Manufacturing).
SPECIAL HANDLING OF STATIC SENSITIVE DEVICES.
Tektronix Interoffice Communication, June 17, 1975, 12 pp.

Component evaluation and manufacturing engineering groups have been involved in some experiments to determine the magnitude of the

static problems with semiconductors in Tek Manufacturing. Several electronic devices were subjected to typical production handling, then tested. Out of 50 MOS devices tested, five had parameters degraded and five more were catastrophic failures. Techniques to minimize handling and the use of conductive containers such as Velostat can reduce losses in manufacturing. Multimeters and other testing devices must also be used with care on MOS IC's.

14998

Olin, R.P. (Control Data Corp.).
"CONDUCTILE" STATIC CONDUCTIVE VINYL FLOORING.
Rept. No. HPOC-79029-EM01, Charge No. 54kkM94, March 30, 1979.

The "conductile" test sample submitted by Vinyl Plastic Inc. (VPI), Sheboygan, Wisconsin passed the current CDC requirement for maximum generation of static electricity in a computer room environment.

The test conducted by Control Data Corp. measured the voltages generated when a tester generated standard voltages by shuffling his feet on a test carpet using neolite soles.

No measured voltage was generated when a test sample tile was cemented to a metal 2'x2' floor with conductive cement.

14999

Johnson, W.D., and R.R. Weekley (Hughes Aircraft Company, Los Angeles, CA).
MELAMINE LAMINATE AND RCAS-1200 WORK SURFACE MATERIALS, EVALUATION STUDY.
Rept. No. IDC 7611.34/76, January 16, 1978, 11 pp.

An evaluation was conducted on two work surface materials to determine if they are acceptable as static safe.

The test results indicate that melamine laminate is an acceptable "static safe" work surface. The antistatic properties of melamine laminate are unaffected by exposure to low relative humidity and to various cleaning agents.

The antistatic properties of RCAS-1200 "pink poly" are not degraded by low humidity but are seriously degraded by all cleaning agents except antistatic fabric softeners such as "Downy".

15000

Warsher, A. (Charles Stark Draper Laboratory, Cambridge, MA).
USE OF MELAMINE WORK SURFACES FOR ESD POTENTIAL BLEED-OFF.
Rept. No. PG-H-242-78, September 22, 1978, 11 pp.

Paper-base melamine sheets can be used for work surface tops under certain

conditions. The conditions are as follows: the top surface of the melamine be abraded away before applying a spring loaded contact for electrical ground, the ambient relative humidity be above 30% if the work surface will be relied upon for electrical discharge, the earth return circuit not be through an additional current limiting resistor, and other ESD measures be continued such as the use of operator wrist straps.

Metal bench tops using a 250,000 ohm resistor to ground are still the preferred method for ESD protection of work stations.

15001

Madzy, T.M. (IBM Corp, Endicott, NY).
FET CIRCUIT DESTRUCTION CAUSED BY
ELECTROSTATIC DISCHARGE.
IEEE - Trans. on Electron Devices, Vol. 23,
No. 9, September 1976, pp. 1099-1103.

MOSFETs are particularly susceptible to ESD damage because of the low destructive breakdown voltages of their oxides.

In IC FET packages the PD is normally another FET with its gate and source connected to the substrate and is in effect a voltage limiting diode with the result that ESD potentials are developed directly across its gate oxide. The I-V curve of the device can depend on whether or not a potential exists at the ground pin of the module.

The destruction of the gate oxide is due to joule heat and arc action when the potential across the device is 5-10 MV/cm. ESD pulses less than 12ns in width require large magnitudes to cause destruction. Pulses of greater than 130ns width require magnitudes of 44v.

The lowest ESD susceptibility level occurs when the substrate is connected to an electrostatic source through some very low impedance return and a charged human makes contact with one module pin.

15002

Enoch, A.F. (Sanders Associates, Inc. Nashua, NH).
ELECTROSTATIC DISCHARGE DAMAGE PREVENTION.
Sanders Associates Federal Systems Group,
Rept. No. 815032, Standard No. 228, FSCM94117,
August 31, 1976, 5 pp.

Sanders Associates, Inc. have established Corporate Standard SA-STD-228 for Electrostatic Discharge Damage Prevention. Corporate Standard 228 includes provisions for distribution of ESD sensitive device listings, purchase specification preparation, engineering drawing and parts list callouts, assembly markings and maintenance manual cautionary notes.

Employee training and basic awareness requirements are specified and the use of protective antistatic devices is required.

15003

Koenigsberg, H.M. (Hughes Aircraft Company, Los Angeles, CA).
ANTI-STATIC PROTECTION FOR THE PCB YELLOW ROOM AREA.
Rept. No. 4500-585, March 3, 1978, 5 pp.

The most practical method of minimizing or eliminating the effects of static electricity is by ionization using the high voltage discharge of alternating current. The contamination problem in the yellow room of PCB manufacturing is aggravated by the use of processing materials, paper articles and work in progress. Laminar flow hoods can effectively eliminate 2-3kv charges at 3½' distance within 5 seconds. Several sequential processing steps must be carried on and several different materials utilized before the net effect on product yield can be determined.

15005

Gardner, P.R. (TRW, Redondo Beach, CA).
HARDNESS ASSURANCE LATCHUP SCREEN PROCEDURE.
Defense Nuclear Agency, Rept. No. 31442-6001-
RU-00, Code No. B323077464, Z99QAXTD072-07,
M2590D, November 23, 1977, 23 pp.

There are two types of radiation induced latchups, a hard latchup and an incipient latchup. A hard latchup is a sustained functional failure. Incipient latchup is not sustained but lasts longer than can be explained by normal circuit times constants.

The source used to promulgate radiation induced latchup will be a flash X-ray machine or a Linac. A dry run radiation exposure and a pass status to verify dosimetry will be performed.

Oscilloscopes or pre-set comparators will monitor outputs to verify device parameters.

The method to analyze four layer integrated circuit latchup is valid for bipolar junction-isolated and dielectrically isolated integrated circuits.

The latchup or PNP sustaining mechanism in a bipolar integrated circuit occurs in four-layer bistable structures. One operating state is characterized by high impedance, low current while the second state is characterized by low impedance and high current.

The existence of a PNP structure within an integrated circuit does not imply that it is a sustainable latchup path even if the parameters for bistable action are present. For a latchup to be sustained, a bias of positive polarity from anode to cathode must be present; in addition, the current must not be limited below holding. For example, if an intermediate function is reverse-biased latchup is not possible.

15006

Anon. (Vinyl Plastics Inc, Sheboygan, WI).
INSTRUCTIONS FOR INSTALLATION AND MAINTENANCE
OF CONDUCTILE.

MK-20150175 Patterns: (CON2, CON3, CON4, CON6,
CON8, CON18), 7 pp.

Static conductive vinyl flooring must be installed on smooth, dry, clean, subfloors. New concrete must be properly cured preferably by covering it with polyethylene film. Under ideal conditions a drying time of at least eight weeks is required.

Conductive flooring will not be guaranteed if the rate of moisture emission from subfloor exceeds three pounds per 1000 sq ft per 24 hours. Conductile may be installed on radiant heated floors provided the surface temperature does not exceed 90°F.

Installation of conductile directly over wood strip or plank subfloors is not recommended.

15007

Hermansen, D.D. (TRW, Redondo Beach, CA).
PACKAGING SPECIFICATION ELECTRONIC, COM-
PONENTS, SMALL, PACKAGING OF.
Rept. No. PK4-22B, June 13, 1975, 19 pp.

This specification covers the preservation, packaging, field force protection, and container marking of all types and versions of established reliability small electronic components.

Components that are electrostatic sensitive as defined in M283308 or as determined by manufacturer/supplier shall be handled as specified in M283308 and protected as specified in 3.1.5.2. Electromagnetic, magnetic or radioactive field force protective metals shall not be in direct contact with the component.

Electrostatic protection shall be provided by a shorting of leads or by electrostatic shielding provided by the packaging method utilized.

Electromagnetic protection shall be provided by overwrapping the component already packaged as required for ESD with aluminum foil conforming to MIL-A-148.

Radioactive protection shall be accomplished through the use of lead-filled compositions completely encasing the component.

15008

Mirakentz, A. (TRW, Redondo Beach, CA).
INSTALLATION AND OPERATION OF STATIC-FREE
WORK-STATIONS.
Rept. No. 027, October 1, 1975, 5 pp.

The purpose of this manufacturing alert is to provide Manufacturing and Product Assurance personnel with general information

for the installation and operation of static-free work stations and for the proper handling of static sensitive devices.

The preferred work station is the standard metal-framed Line Master bench. The work surface must be covered with either a metal plate or an antistatic polyethylene sheet. It is recommended that metal plates be used primarily on bench tops where high heat generating equipment such as solder pots are used. In all cases both the antistat and metal bench must be grounded.

All tools and equipment used at the station must be grounded. Plastic lead forming tools shall not be used.

In special cases where grounding of the operator to the work station is impractical an air ionizer/blower must be used.

There are no special storage requirements for static sensitive devices provided they are properly packaged.

15009

Dawe, W.E. (TRW, Redondo Beach, CA).
ELECTROSTATIC (STATIC) SENSITIVE PARTS,
LISTINGS, IDENTIFICATION, MARKING, HANDLING,
AND PACKAGING OF.
Rept. No. M283308, Code Ident. No. 11982, July
21, 1975, 13 pp.

This document provides a list of components currently being procured at TRW that are considered electrostatic (static) sensitive. Also included are guidelines for handling and packaging.

Test fixtures shall be equipped with a short across the terminals which is disconnected after the device is inserted.

All low-impedance signal generators or power supplies should be disconnected or the power source output should be slowly reduced to zero before disconnecting from the device.

After burn-in, maintain electric bias until the device has cooled to room temperature. Cotton gloves shall be used during loading and unloading of burn-in racks.

15010

Swann, F.E. (TRW, Redondo Beach, CA).
HANDLING AND PROTECTION OF STATIC SENSITIVE
ELECTRONIC PARTS AND ASSEMBLIES.
Rept. No. FIPPO-00-06A, Code No. 11982, May
15, 1975, 13 pp.

TRW Systems Group has incorporated handling and protection fabrication/inspection process procedures for static sensitive electronic parts and assemblies. Procedures specified involved the material receiving area, receiving inspection and control, testing, and storage. Special procedures for X-ray analysis, power aging and radiation screening areas also are written. Component tinning, production line assembly areas, bonding, conformal coating and general area control are also covered.

15011

Sixel, D.E., and K.R. Gaspard (Honeywell, Defense Systems Division).
HANDLING OF ELECTROSTATIC SENSITIVE ELECTRONIC ITEMS.
Rept. No. ES8708, Code No. 08638, April 5, 1976, 27 pp.

Category 1 components of ESD sensitive parts are very sensitive to ESD induced degradation having the worst case sensitivity range of 0 to 170 volts. Category 1 assemblies are any assembly containing a Category 1 component. Category 2 components worst case voltage sensitivity is 171 to 2000 volts; Category 3 is 2001 to 15000 volts; Category 4 is 15000 volts.

All personnel involved in the handling of ESDS categories 1, 2 and 3 devices shall receive instructions and proper training in the implementation of the control measure requirements and guidelines specified herein. To be certified, all personnel shall attend and successfully complete a formal training program.

ESD sensitive parts shall be transported to and from the stockroom area in the "as received" package when the package has not been damaged. Do not open individually packaged parts for count or issuance (kitting). Personnel shall not unnecessarily handle any device received which indicates it is an "ESDS" device.

15012

Meul, J. (Raytheon Company).
ELECTROSTATIC SENSITIVE DEVICES, MARKING AND HANDLING THEREOF.
GIDEP Rept. No. 347.23.00.00-K9-02, Access No. E024-1176, GIDEP Originators Rept. No. 1-GEN-00075, August 20, 1974, 16 pp.

Prior to removing static sensitive devices from their protective packages the following pre-test conditions should exist: provide 40% (minimum) relative humidity at the test station; line all trays or boxes for carrying device with $\frac{1}{4}$ thickness conductive cushioning; avoid touching leads or contacts even though grounded; avoid unnecessary physical activities which tend to be friction producing. The original package should be in contact with the conductive surface of test station when being opened or closed. Foil wrapped devices may be placed in any type of container.

15013

Troeger, E.P. (Aerospace Industries Association of America, Inc. Washington, DC).
REPORT ON MC-118, STATIC SENSITIVE PARTS AND EQUIPMENT PROTECTION.
Report No. AO-MC 73-86, December 4, 1973, 20 pp.

Surveys showed industry was facing potential ESD damage to components and had serious problems throughout the manufacturing assembly and shipping activities.

Semiconductors, chips and other component parts are generally sensitive until fabricated or installed in assembly. To eliminate this possibility, the receiving inspection of electronic items should be moved to a controlled area and "good practice" suitable for handling static sensitive classes of parts should be initiated. The above findings showed a general lack of understanding of field force protection and the basic electrical phenomena involved.

15014

Tasca, D.M. (General Electric Company, Space Division, Philadelphia, PA).
PULSE POWER FAILURE MODES IN SEMICONDUCTORS.
IEEE - Trans. on Nuclear Science, Vol. NS-17, No. 6, December 1970, pp. 364-372.

It was observed that a common mode associated with permanent damage effects in reverse-biased junctions is the phenomenon known as "second breakdown." Both energy and current modes were observed.

The occurrence of thermal second breakdown which is energy-dependent was found to represent the point of incipient permanent damage at submicrosecond pulse conditions. In contrast the energy required for current mode second breakdown has not in itself been observed to represent incipient junction damage. Thermal second breakdown physically is a local thermal runaway effect at the junction induced by severe current concentration. Current mode second breakdown has not been fully understood or observed. It is initiated by relatively high material current densities under the emitter during collector to base junction reverse pulsing resulting in a forward bias on a portion of the emitter.

Comparison of the mathematical model with experimental data indicates that if the volume of the thermal second breakdown current constriction site across the junction and the critical initiation temperature are known then the model can be used to determine the pulsed power susceptibility of any general P-N junction. On a practical basis it is relatively easy to assign specific values to the initiation temperature and to empirically determine the typical current constriction site volumes.

15016

Lee, J. (Raytheon, Portsmouth, RI).
93L415 BOARD FAILURES.
Rept. No. 7380, Raytheon Part No. 907715-103, E075-0071, May 10, 1977, 3 pp.

The failure mechanism causing the input leakages of the 93L415 to increase was due to electrical overloading of the input protection diode caused by static discharge. The devices that failed were six 93L415s in ceramic packages. All six units exhibited at least one input pin which exceeded the high input current parameter specified at 40ua at $V_{IN} = 4.5v$ and $V_{CC} = 5.25v$.

15017

Patterson, J. (Teledyne Microelectronics, Manager Failure Analysis Laboratory).
A TEST METHOD TO DETECT ELECTROSTATIC DAMAGE IN THICK FILM RESISTORS.
IEEE - Advanced Techniques in Failure Analysis Symposium, 1978, pp. 35-38.

The test method described herein allows the examinations of high voltage characteristics of thick film resistors and reveals the voltages to which they have previously exposed. The model that best fits recorded data to explain why thick film resistors decrease in value when subjected to ESD is thin oxides surrounding resistive particles in thick film ink. During exposure to high electric fields these oxides break down permanently and provide additional conduction paths within resistors.

15018

Anon. (U.S. Navy, Naval Sea Systems Command).
MILITARY SPECIFICATIONS, STANDARDS AND CONTRACT CLAUSES SPECIFYING CONTROLS FOR PROTECTION AGAINST ELECTROSTATIC DISCHARGE.
Rept. No. NAVSEA S6000-AB-GTP-010, December 1978, 51 pp.

Excerpts of military documents regarding ESD controls are contained herein. Military documents MIL-E-16400G, MIL-STD-454E, MIL-M-38510, MIL-S-19500, and MIL-I-983E cover design specification requirements. Military documents MIL-S-19491E, MIL-M-55565A, MIL-STD-1475, MS90363, NAS853 and various NAVSEC contract clauses delineate packaging specifications. Technical manuals MIL-M-15071G, MIL-M-24100, MIL-M-21742A, MIL-STD-1604 and MIL-M-7298C contain overhaul and maintenance procedures for protection against ESD. MIL-STD-100A and MIL-D-1000A are drawing specification requirements for ESD items.

15019

Stadler, P.H. (Philco-Ford Corp., Aeronutronic Division, Newport Beach, CA, and Harry Diamond Laboratories, AMXDO-EM, Washington, DC).
FAILURE THRESHOLD AND RESISTANCE OF THE PROTECTED AND UNPROTECTED 2N2222 TRANSISTOR IN THE SHORT PULSE WIDTH REGIME.
Nuclear EMP, PEM-7, Contract No. DAAK02-70-C-0464, May 1972, 48 pp.

This work was authorized under MERDC, Ft. Belvoir, contract No. DAAK02-70-C-0464 funded by the Defense Nuclear Agency. The effort included the design, construction and checkout of a fast, high voltage pulser with a component test effort. This latter work is emphasized in this report; the operator's manual covers the details of the pulser.

15020

Hart, A.R. (U.S. Navy, Naval Electronics Laboratory Center, Electron Material Sciences Division, San Diego, CA).
RF FAILURE PREDICTION FOR MOS 4001 AND 4011 INTEGRATED CIRCUITS.
Rept. No. NELC R501, Code No. 4600, TN3107, January 19, 1976, 47 pp.

This report defines the effects of a single, high-power, 5 microsecond, 3 GHz RF pulse injected into the output of two types of MOS devices: 4001 (NOR Gate) and 4011 (NAND Gate). This report presents a possible theory which explains the 12dB difference in power level for RF failure of the devices tested and compares the effects of different manufacturers' chip layout designs on the RF susceptibility of these devices. A DC model was developed and applied to the RF problem and found to fit very well to the experimental data. The DC model predicted the RF susceptibility hierarchy for several manufacturers and helped to define potential ways of reducing the RF susceptibility of these types of MOS devices. This report also points out how some EMP radiation hardness protection circuits may actually increase the RF susceptibility of similar types of devices.

15022

Huntsman, J.R., and D.M. Yenni (3M Company, St. Paul, MN).
DON'T ZAP IT - BAG IT.
Quality, December 1978, pp. 18-21.

Advances in IC technology are increasing circuit densities and thus accentuating static damage susceptibility. Protective devices are not always a guarantee of protection. Insulators have a very large surface resistivity and therefore do not dissipate static electricity. Organic additives can increase their conductivity on their surfaces. Antistatic bags do not effectively protect their contents from external electric fields. Charges may accumulate, forming a significant voltage gradient from top to bottom. 3M Company has developed an effective field shielding antistatic bag consisting of an outer metallic coating, a center polyester film, and an inner antistatic polyethylene. The ESD pulse in this shielding bag lasts only several microseconds with a peak of 75v.

15023

Ramaley, J.W. (3M Company, St. Paul, MN).
VELOSTAT VS ANTI-STATIC FILMS.
Interoffice Correspondence, May 12, 1975, 15 pp.

Antistatic film surface resistivity tests show that it falls into the range of an insulator. Velostat is 100 million times more conductive than anti-static films. A test was run at 35% RH. A subject with static charge of 1000v touched a grounding strap of velostat conductive plastic. The voltage dropped to 0 volts instantaneously. The decay time was less than 1/10 second regardless of humidity or electrode. Age affects the anti-static qualities of certain anti-static films.

Electric ionizing air blowers induce low but significant voltages in ungrounded objects brought near it; nuclear powered blowers do not.

15024

Oishi, T. (U.S. Navy, Naval Sea Systems Command, Washington, DC).
ELECTROSTATIC DISCHARGE IMPACT ON ELECTRICAL/ELECTRONIC DEVICES, COMPONENTS, ASSEMBLIES AND EQUIPMENT.
Association of Scientists and Engineers 16th Annual Technical Symposium, 1979, and at the 6th Annual Contamination Control Seminar, May 5-7, 1981.

The hazard of ESD is an existing problem which is becoming more severe with the advancement of technology. Government and Navy personnel lack knowledge on the hazard of ESD. This lack of knowledge is resulting in unnecessary repair costs, excessive equipment downtime and reduced mission effectiveness in that electrical/electronic devices and equipment which incorporate them are being damaged throughout the equipment life-cycle during processing, assembly, inspection, packaging, shipping, storage, testing and maintenance.

An awareness program on ESD along with the implementation of an effective ESD control program can minimize the ESD hazard.

15025

Krulac, I.L. (IIT Research Institute, Reliability Analysis Center, Griffiss AFB, NY).
AUTOMATIC MACHINE PRECAUTIONS FOR MOS/CMOS.
Rept. No. RAC-74-01PM, 3 pp.

A retrospective search/survey was performed to determine precautions necessary in handling MOS or CMOS devices in automatic test and insertion equipment. The problem that exists in handling these devices is the build-up of large amounts of static voltages on portions of machine handling equipment. The static charge build-up is approximately 10,000 volts depending on humidity levels.

15026

Branberg, G. (Hewlett-Packard, Interoffice Correspondence).
L.I.D. ELECTRO-STATIC DISCHARGE STUDY. Rept. I, Rept. II, Rept. III and Rept. IV.
February 1978, April, 1978, May 1978, June 1978, respectively.

An electrostatic discharge (ESD) study was performed in order to provide the R&D engineer with data necessary to properly protect sensitive components from ESD damage and the production and service engineers with information necessary to determine appropriate antistatic production assembly and repair techniques.

The study consisted of an ESD susceptibility comparison on CMOS devices from various vendors. A latent failure life test was also performed.

A test station was assembled capable of delivering a repeatable discharge to the D.U.T. and a standard test method was developed for determining ESD sensitivities for this study.

15027

Kenworthy, C. (John Fluke MFC. Co., Inc.).
STATIC-SENSITIVE DEVICE FAILURES, A CONTROLLED EXPERIMENT.
January 14, 1977, 7 pp.

It is very apparent that the overall failure rate caused by static discharge can be reduced dramatically for both CMOS and low-power Schottky by careful handling. Opto-isolators can benefit from delicate handling. The failure rate for CMOS was cut 88% and 76% for low-power Schottky by the application of the recommended handling procedures.

15028

Polski, P.A. (Sperry/Univac).
ELECTROSTATIC DISCHARGE STUDY REPORT.
Rept. No. 12561, UD1-3792-2, March 30, 1978, 15 pp.

This study was initiated to determine what parts used by Sperry Univac Defense Systems Division are potentially sensitive to electrostatic discharge. Device structural features influence ESD susceptibility. Components very sensitive to ESD damage (Cat. I) include MOS with no input protection circuitry, dielectrically isolated semiconductors with internal capacitor contacts connected to external pins and microcircuits utilizing N+ guard ring construction (with metallization crossing over the guard ring). Category II devices include MOS with input protection, dielectrically isolated and fine metal bipolar, low power Schottky and Schottky TTL, high speed ECL,

high input impedance linear (greater than or equal to 10^7 ohms) junction FET's, small signal transistors with f_T greater than 500 MHz, and all devices that use metallization paths over active areas and ladder networks.

15030

Anderson, D.C. (Richmond-Division of Dixico Corp., Redlands, CA).
MILITARY RECOGNIZES NEED FOR ELECTROSTATIC DAMAGE PREVENTION IN ELECTRONIC DEVICES, COMPONENTS, ASSEMBLIES AND EQUIPMENT.
1979 Spring Symposium - American Defense Preparedness Association: Packaging, Handling, and Transportability Division, April 25-26, 1979, 4 pp.

Efforts to help standardize and increase awareness of the ESD protection problem are underway. Military Standard, MIL-STD-xxx entitled "Electrostatic Discharge Control Program for Electrical and Electronic Devices, Components, Assemblies and Equipment," and Military Handbook, MIL-HDBK-xxx entitled "Electrostatic Discharge Control Handbook for Electrical and Electronic Devices, Components, Assemblies and Equipment," were prepared under Mr. Toshio Oishi. Mr. Oishi is now Systems Effectiveness Branch Head, Naval Sea Systems Command, Combat Systems Directorate, Washington, D.C. 20362 (Code 61C) Phone 202/692-6426.

15033

Emberson, W.C. (IIT Research Institute, Chicago, IL).
ELECTROMAGNETIC PULSE (EMP) HARDWARE.
Contract No. DAHC20-72-C-0282, DCPA-WU-2213F, January 1973, 56 pp.

This report presents the results of a study to determine the applicability and effectiveness of commercially available EMP protective devices for the hardening of typical Civil Defense communication systems against the EMP resulting from an exo-atmospheric nuclear burst. The study was limited to the RF side of communication equipments with operating frequencies in the range of 100 kHz -100 MHz. Representative EMP-induced transients are presented and used as general guidance for determining the effectiveness of the recommended hardening techniques.

15046

Anon. (U.S. Navy, Naval Surface Weapons Center, White Oak, MD).
ELECTRO-MAGNETIC PULSE RADIATION ENVIRONMENT SIMULATOR FOR SHIPS.
Rept. No. NSWC-MP-79-37, 1979, 16 pp.

EMPRESS is a facility of the U.S. Navy to test ship behavior in a simulated EMP environment. This brochure presents what EMPRESS is, why it is needed, and how it is used.

15050

Schwank, J.R., G.D. Jarrell, and M.G. Armendariz (Sandia National Laboratories).
STUDY OF ELECTROSTATIC DISCHARGE EFFECTS ON COMMERCIAL CMOS DEVICES.
Rept. No. SAND79-1784, February 1980, 47 pp.

Experiments on CD4021A CMOS eight-stage shift registers were conducted to investigate the susceptibility of the device to electrostatic discharge (ESD), to investigate the possibility of latent functional failures of a device degraded by ESD, and to isolate the cause and location of failures during assembly. Experiments were also conducted on two buffered CMOS devices, 4021B and CD4081B, and two additional unbuffered ones, CD4011A and DC4013A, to compare the ability of two types to withstand ESD. After the CD4021A devices were subjected to ESD by using a human-body-equivalent circuit model, each one was given an operating life test at 150°C for 308 h (equivalent to 2000 years of operation at room temperature). None of them failed to (logically) function after the life test. The low-bias terminal, V_{SS} , and an output terminal were found to be the most susceptible to ESD pulses causing failures. All of the assembly failures in a recent production run were reproduced by subjecting devices to ESD pulses on the V_{SS} terminal. By using the same ESD circuit on both the "A" and "B" devices, it was found that gate oxide ruptures occurred at considerably lower voltages in the unbuffered devices.

15056

Sonenclar, R.J.
EIA SEES CODE OVERKILL - ELECTROSTATIC SAFEGUARDS.
Electronic Buyer's News, Issue 202, June 18, 1979.

The EIA has criticized the Government's effort to institute more rigid safeguards for the control of electrostatic discharge. Industry officials assert that only one half to three quarters of the users' industry has taken adequate steps to combat the problem. The Navy is seeking to develop a standard which would mandate compliance before companies using ESD sensitive devices would be approved for government contracts. The EIA cites cost factors and an "overkill" mentality as causing unreasonably high cost impact.

15057

Pease, R.L., D.R. Alexander, and C.R. Jenkins, (BDM Corp., Albuquerque International, Albuquerque, NM).
ELECTRICAL OVERSTRESS TEST PROGRAM AND INTEGRATED CIRCUIT FAILURE MODE EVALUATION.
Rept. No. DNA 4467F, Contract No. DNA 001-77-C-0156, Subtask 299QAXTB097-04, April 26, 1978, 108 pp.

This final report describes the SOS diode test structures which will be used for empirical investigation of electrical overstress failure. The test structures, in which important physical parameters are varied, are described in detail and a test plan is presented for the overstress testing that will generate failure data for a sensitivity analysis of pulse power failure level as a function of junction area, epitaxial thickness, junction radius of curvature, doping level and metallization and diffusion spikes. An electrical overstress failure mode and distribution study in integrated circuits is presented. Data on over 1200 devices which were tested on previous programs were analyzed to determine failure modes on DTL, RTL, TTL, ECL, MOS and linear integrated circuits. The failure distributions on over 3,000 devices from several different test programs were reviewed to identify "mavericks." These "mavericks" were investigated for distinctive failure modes or unusual preirradiation electrical characteristics.

15058

Anon. (U.S. Navy, Naval Material Command).
NAVSEA ZAPS ESD.
Overview, Spring 1979, pp. 17-21.

The Naval Sea Systems Command is preparing a new MIL-STD and a new MIL-HDBK to educate personnel as a primary deterrent to ESD damage. The Naval Material Command has asked NAVSEA to formulate an instruction on ESD damage prevention procedures also.

The Naval Supply Systems Command (NAVSUP) has instituted contract-required procedures for manufacturers to insure proper packaging of ESD sensitive devices. NSN's have been assigned to commercially available antistatic packaging materials.

The NEARTIP components analyzed by Honeywell have caused the establishment of facility-wide ESD control systems.

15059

Huang, C.L., F. Kwan, S.Y. Wang, P. Galle, and J.S. Barrera (Hewlett-Packard Co., San Jose, CA).
RELIABILITY ASPECTS OF 0.5um AND 1.0um GATE LOW NOISE GaAs FETS.
IEEE - 17th Reliability Physics Symposium, 1979, pp. 143-149.

GaAs FET failures are obviously catastrophic events. Long-term events such as changes in Schottky gate characteristics and intermetallic reactions can eventually cause loss of gate control. Specifically an explanation and solution to the potential reliability problem of electrostatic discharge-created changes in Schottky gate reverse leakage currents.

The changes vary in degree from just discernable creation of a resistive reverse current to catastrophic eruption of gate metal, GaAs channel and source contact metal.

15060

Anon. (U.S. Navy, Naval Sea Systems Command, Naval Electronic Systems Command).
ELECTROSTATIC DISCHARGE (ESD) DAMAGES INTEGRATED CIRCUITS AND DISCRETE SEMICONDUCTOR DEVICES.
Electronics Information Bulletin, NAVSEA 0967-LP-001-3975, May 15, 1978, 8 pp.

The purpose of this article is to provide an awareness of (1) common sources of static, (2) detrimental effects, and (3) available controls for protection from the damaging effects of electrostatic discharge (ESD). Particularly susceptible to damage from ESD are metal oxide semiconductors, discrete bipolar transistors and diodes. Damage does not always result in sudden failure but may produce degradation, often apparent as reduced reverse voltage breakdown.

15074

McAteer, O.J.
SHOCKING BLOW TO MILITARY ELECTRONICS.
Military Electronics/Countermeasures, June 1979, pp. 59-63.

ESD has been recognized in recent years as a major source of electronic device failures. The problem becomes even more acute for military applications where reliability is a critical parameter and semiconductor part counts are high. Subtleties in physical analysis make recognition of ESD failures difficult. More thorough analysis such as chemically etching the SiO₂ passivation layer and site isolation using special heat sensing cholesteric crystals are used. Capacitive coupling and loading between nodes is another subtlety making ESD failure analysis even more difficult.

15077

Cianos, N., and E.T. Pierce (Stanford Research Institute, Menlo Park, CA).
A GROUND-LIGHTNING ENVIRONMENT FOR ENGINEERING USAGE.
SRI Project 1834, Contract No. L.S.-2817-A3, August 1972, 136 pp.

Data on lightning incidence is examined to determine the number of lightning strikes to be expected over a period of time by climatological areas.

The physical parameters of lightning are discussed, with the main emphasis on the direct effects of flashes to grounds. Intra-cloud discharges and static and electromagnetic fields generated by lightning are also described.

15083

Woods, M.H., and G. Gear (Intel Corp., Santa Clara, CA).
A NEW ELECTROSTATIC DISCHARGE FAILURE MODE.
IEEE-Trans. on Electron Devices, Vol. ED-26, No. 1, January 1979, pp. 16-21; 16th Reliability Physics Symposium, 1978, pp. 146-150.

A new electrostatic discharge failure mode was discovered which affects MOS LSI components in hermetic packages with nonconductive lids. Failure can be induced by spraying package lids with canned coolant. It is shown that charge from the freeze spray causes breakdown in the air-gap between the die surface and the lid. As a result, localized surface charging and field inversion occurs in the array, which produces leakage currents and circuit failure. The failure mode can be characterized by its recovery with either a strong UV exposure to the die surface or a DI water rinse.

15084

Griffith, O.K., M.M.E. Bequwala, and R.E. Johnson (Rockwell International, Autonetics Group, Anaheim, CA).
NONDESTRUCTIVE SEM STUDIES OF LOCALIZED DEFECTS IN GATE DIELECTRIC FILMS OF MIS DEVICES.
IEEE - 14th Reliability Physics Symposium, Rept. No. X76-554/501, April 20, 1976, 4 pp.

A nondestructive technique to identify localized defects in the gate dielectric of MOS devices has been developed. The technique is based upon electron beam induced conductivity modulation which gives rise to a relatively large increase in gate current under an applied bias when the beam scans a localized defect area. Measurements on devices with low gate breakdown voltage have been made and correlated with regions where subsequent catastrophic gate breakdown occurred. A circuit description and physical model of the technique is presented.

15085

Tasca, D.M. (Boeing Aerospace Company, Seattle, WA).
PULSE POWER DAMAGE CHARACTERISTICS OF ELECTRICAL RESISTORS.

Vol. 1, Rept. No. AFWL-TR-75-108, Contract No. F29601-74-C-0008, D224-13058-1; TD-4-23, April 1976, 90 pp.

This report defines the EMP induced damage characteristics of a variety of electrical resistor types. The experiments evaluate the change in device resistance. Of the five resistor classes tested, wire wound resistors were most resistant followed by carbon composition, carbon film, metal film and metal oxide, respectively.

15086

Grimm, A.V. (Bendix, Kansas City Division).
LSI INTEGRATED CIRCUIT TEST DEVELOPMENT.
Rept. No. BDX-613-1017, Contract No. AT(29-1) 613 USAEC, March 1974, 62 pp.

Methods for handling and testing MOS semiconductor IC's used in the prevention of overstressing by ESD were investigated and developed. Testing was performed in six areas of static discharge damage: DC testing, process evaluation test circuits, DC testing of MOS LSI devices, functional testing of MOS devices, switching time testing of MOS devices and fault testing of MOS devices. The Fairchild 5C00 C with low frequency generation was capable of only limited testing of the MOS LSI devices.

15087

Anon. (Hewlett-Packard Co., Palo Alto, CA).
LAB MANUAL ENVIRONMENTAL EVALUATION AND QUALIFICATION TESTING.
May 1975, 55 pp.

This manual provides HP Data Systems Division with a single document covering many of the considerations associated with developing, testing (including a test for ESD susceptibility) and specifying the environmental capabilities of Data Systems Products.

15088

Leopold, H.S., L.A. Rosenthal, and G.R. Laib (U.S. Navy, Naval Surface Weapons Center, Silver Springs, MD).
INVESTIGATION OF TECHNIQUES TO REDUCE ELECTROSTATIC DISCHARGE SUSCEPTIBILITY OF EED'S CONTAINING PLASTIC PLUGS.
Rept. No. NSWC/WOL-TR-78-82, AD/A059982, August 25, 1978, 31 pp.

The substitution of a conductive plastic for the normal dielectric plastic was considered the most satisfactory retrofit to provide human electrostatic discharge protection for electroexplosive devices (EEDs) employing plastic initiator plugs. Conductive gaskets may also be satisfactorily used for protection in those cases where the length of the EED can be increased.

151091

DiCiaccio, C. (GTE Sylvania).
40 PIN PMOS INTEGRATED CIRCUIT.
Rept. No. E0176, Project No. 479-5735, May 26,
1976, pp. 2-8.

Three PMOS devices were subjected to increasing stress levels of ESD up to 10kv. PMOS IC's can successfully pass the test if the stress is applied to all inputs and outputs simultaneously; also, a toggle switch must be used instead of the lever switch to prevent arcing at high voltages. A combination of IDD and functional measurements was made.

151092

DiCiaccio, C. (GTE Sylvania, Solid State Scientific).
CMOS INTEGRATED CIRCUIT.
Rept. No. E0206, Project No. 983-3050, August 4, 1976, pp. 3-11.

The evaluation conducted on the CMOS product clearly indicates that Fairchild devices are susceptible to latch-up whereas Solid State Scientific's are not.

The devices that were ESD tested show degradation in post breakdown voltage measurements. The junction degradation is not functionally detectable. The long term reliability of those devices which exhibited junction degradation is questionable. Therefore, further effort is needed at this time to investigate those devices subjected to ESD stresses.

15104

Anon. (Fischer & Porter Co., Warminster, PA).
A DISCUSSION OF LIGHTNING PROTECTION FOR
ELECTRONIC PROCESS INSTRUMENTATION.
Instruction Bulletin 53E9007, 36 pp.

Industrial instruments have a fairly high withstand voltage against a surge voltage at the input, output and power supply terminals. For this reason many instruments are used without any lightning protectors. However, instruments utilized with important or critical process variables may require lightning protectors.

Some common lightning protectors used in industrial instruments are zener diodes, gas arresters, metal oxide varistors and Tranzorbs.

15110

Cook, D. (NCR Corp., Data Processing Division).
TRANSIENT SUPPRESSOR REPORT.
3354, June 30, 1975, 18 pp.

Voltage transients are one of the three general types of power line disturbances. The use of uninterruptable power supply can take care of voltage transients, but this is too expensive a solution if transients are the only problem of immediate concern. This report defines and describes voltage transients and identifies their sources. The probability of occurrence is discussed. The key characteristics desired for the suppressors were determined to be energy handling ability and response time.

15127

Halperin, S.A. (Analytical Chemical Laboratories, Elk Grove Village, IL).
COPING WITH STATIC ELECTRICITY - PART XV,
ELECTROSTATIC INSTRUMENTS: EYES FOR
ENVIRONMENTAL STATIC CONTROL.
Evaluation Engineering, Vol. 18, No. 6,
November/December 1979, pp. 68-72.

This article describes a new generation of electrostatic instruments designed for use in establishing and monitoring Environmental Static Control (ESC) programs. An overview as to the range of selection and application of types of instruments available for material selection, component classification, survey, monitoring and analysis is provided.

15139

Pakulski, F.J., and T.R. Touw (IBM Components Division, Hopewell Junction, NY).
ELECTRIC DISCHARGE TRIMMING OF GLAZE
RESISTORS.
Hybrid Microelectronics Symposium, 1968, pp. 145-151.

Glaze resistors of the PdO-Ag formulation have established their worth in numerous applications for several years. Their primary advantages of allowing fast, economic production with reliable results are well-known in the industry.

In most cases, it is required that the resistors be given a final adjustment to achieve the proper value for the intended application.

A method for adjusting the value of PdO glaze resistors by proper application of a high electric field is described. Material response and reliability after trimming are described. A model concerning the removal of silver from the PdO lattice is also discussed.

15140

Himmel, R.P. (Hughes Aircraft Co., Culver City, CA).
THICK FILM RESISTOR ADJUSTMENT BY HIGH VOLTAGE
DISCHARGE.
Electronic Components Conference, 1971, pp. 504-512.

A unique and little-understood characteristic of thick-film resistors is their sensitivity to high voltage, a phenomenon both useful (as in the case of resistance adjustment) and undesirable (as in the case of static electricity). In a recently concluded experiment the high voltage sensitivity of the latest generation of thick-film resistors was studied. The conclusions included: (1) most of the newer materials exhibit a sensitivity to high voltage; (2) high voltage sensitivity is more pronounced in high resistivity materials that typically reduce in resistivity upon exposure to high-voltage pulses; and (3) some of the newer materials exhibit a significant shift in their temperature coefficients of resistance (TCR) during pulse adjustment.

15143

Gaspard, K.R., and C.F. Mykkanen (Honeywell Inc., Component Applications Engineering Group, MN).
COPING WITH STATIC ELECTRICITY - PART XIX, STANDARDIZATION KEY TO WINNING ESD BATTLE. Evaluation Engineering, Vol. 19, No. 4, July/August 1980, pp. 78-82.

This article points out the need for a standardized approach to combating ESD-related failures. It discusses why ESD has been ignored in the past, what new product areas should be developed, and how standardization can eliminate ESD-caused failures.

15188

Bailey, D.T., R. Fisher, R.L. Hutchins, G.J. Rimbart, G.W. Wilson, and T.J. Zwolinski (BDM Corp., Albuquerque, NM).
DETAILED SUMMARY - EMP SPECIFICATION DEVELOPMENT VOL. II - SHIELDING ELEMENTS. Rept. No. BDM/A-77-145-TR-R3, Rept. No. AFWL-TR-79-163, Contract No. F29601-76-C-0093, May 1980, 364 pp.

This volume of the detailed summary presents the data and rationale supporting the conclusions reached with respect to shielding elements. This summary includes areas such as the specification selection in terms of quality assurance programs and procedures, the assignment of levels of shielding effectiveness to the various elements, the most significant conclusions reached and recommendations to be made, and a complete reference bibliography.

15188-01

Bailey, D.T., R. Fisher, R.L. Hutchins, G.J. Rimbart, G.W. Wilson, and L.J. Zwolinski (BDM Corp., Albuquerque, NM).
DETAILED SUMMARY - EMP SPECIFICATION DEVELOPMENT VOL. III - MIX OF SPECIFICATIONS.

Rept. No. BDM/A-77-145-TR-R3, Rept. No. AFWL-TR-79-163, Contract No. F29601-76-C-0093, May 1980, 118 pp.

This report discusses the development of methods for combining and mixing specifications into basic system hardening concepts. This report includes methods for achieving optimum hardening concepts that consider life cycle cost models and functional and shielding topologies. Several specific examples are presented to demonstrate the use of these methods.

15188-02

Zwolinski, T.J., R. Fisher, G.J. Rimbart, D.T. Bailey, and G.W. Wilson (BDM Corp., Albuquerque, NM).
ELECTROMAGNETIC PULSE (EMP) SPECIFICATION APPLICATIONS HANDBOOK. Rept. No. BDM/A-77-067-TR-R3, Rept. No. AFWL-TR-79-162, Contract No. F29601-76-C-0093, May 1980, 374 pp.

This handbook provides a set of specifications by which the elements of an EMP hardening program can be developed and implemented. These are consistent requirements to be met by the electronics subsystems and protective elements of a hardened system. EMP specifications and hardness assurance procedure given were developed with consideration of their cost impact.

15188-03

Bailey, D.T., R. Fisher, R.L. Hutchins, G.J. Rimbart, G.W. Wilson, and T.J. Zwolinski (BDM Corp., Albuquerque, NM).
EMP HARDENING GUIDELINES: SYSTEM LIFE CYCLE COST DESIGN CONSIDERATIONS. Rept. No. BDM/A-77-025-TR-R2, Rept. No. AFWL-TR-79-161, Contract No. F29601-76-C-0093, May 1980, 160 pp.

Cost-effective EMP design hardening guidelines are established for application by system designers during the conceptual design phase of the system acquisition process for new aeronautical systems. This document serves as a user's guide for engineers and managers who have the responsibility for system design. The EMP hardening guidelines contains specific system-related EMP survivability requirements, shielding subsystem requirements, and avionics subsystem requirements. A set of shielding elements is defined and the ranges of their effectiveness are discussed. A methodology is presented to select the optimum shielding subsystem to meet survivability and operational readiness requirements at minimum cost.

15204

Clark, O.M., and J.J. Pizzicaroli (General Semiconductor Industries, Inc., Tempe, AZ).
EFFECT OF LEAD WIRE LENGTHS ON PROTECTOR CLAMPING VOLTAGES.
Federal Aviation Administration - Florida Institute of Technology Workshop on Grounding and Lightning Technology, Rept. No. FAA-RD-79-6, March 1979, pp. 69-73.

Under high current pulse conditions, excessive lead lengths on suppressor components can be responsible for destruction of the protected circuit. This is caused by voltage build-up across the small but finite amount of inductance in the interconnecting leads of the protector. Some suppressor devices have been tested and observed to have more than twice the specified clamping voltage which was subsequently shown to be caused by inductive effects. Problems and corrective measures are illustrated and discussed in this paper.

15234

Yates, W.
FORUM: PROTECTING ICS FROM ELECTROSTATIC DISCHARGE.
Electronic Products, Vol. 23, No. 1, June 1980, pp. 31-36.

In an attempt to determine the extent of the ESD problem as it relates to ICs and to uncover ways of handling the problem, Electronic Products Magazine brought together a group of industry experts to present their views. The experts included manufacturers and user of ICs along with members of the static protection industry. They discussed problems caused by ESD and ways to prevent ESD.

15236

O'Donnell, H.B., and D.M. Tasca (General Electric, Space Division, Valley Forge Space Center, Philadelphia, PA).
DEVELOPMENT OF HIGH-LEVEL ELECTRICAL STRESS FAILURE THRESHOLD & PREDICTION MODEL FOR SMALL-SCALE JUNCTION INTEGRATED CIRCUITS.
Rept. No. HDL-CR-78-138-1, Contract No. DAAG 39-76-C-0138, AD/A060 874, September 1978, 192 pp.

This report summarizes the experimental and theoretical work performed in order to develop engineering-type prediction techniques to predict both surge impedances and failure levels of small-scale junction integrated circuits when exposed to EMP-type environments.

15243

Deavenport, J.E. (DEDCO, San Diego, CA).

EMI SUSCEPTIBILITY TESTING OF COMPUTER SYSTEMS.

Computer Design, March 1980, pp. 145-149.

Problems caused by electromagnetic interference are examined and accompanied by a description of a test instrument that provides quantitative determination of system noise susceptibility.

15284

Kosiarski, J.P. (Tecknit, Cranford, NJ).
THE USE OF ELECTRICALLY CONDUCTIVE ORGANIC SURFACE COATINGS FOR SHIELDING AND GROUNDING OF PLASTIC ENCLOSURES.
34th Reinforced Plastics/Composites Institute Technical Conference, February, 1979.

Shielding and grounding of plastic enclosures susceptible to EMI and static discharge are accomplished by metalizing the plastic. Numerous methods of metalization have evolved over the last few years. The ultimate choice of method will vary with the plastic part size and geometry, quantity, and degree of shielding or grounding required.

15285

Harper, C.A. (Westinghouse Electric Corp., Baltimore, MD).
PACKAGING HIGH-VOLTAGE ELECTRONICS.
Electronic Packaging and Production, Vol. 20, No. 8, August 1980, pp. 41-58.

The packaging of high-voltage systems can be both critical and complex. This is because the number of variables having an effect on high-voltage performance is high and many variables are interrelated, the types of voltage failures with these variables are interrelated, the types of many variables are interrelated. Voltage failure conditions are frequently transient in ways which prevent accurate knowledge of the actual voltage stress conditions for which electronic packaging is required. This article will first present the major fundamentals which must be considered in the packaging of high-voltage electronic systems, and this will be followed by discussion of the critical factors in the design of high-voltage electronic packages and in the all-important application of high-voltage materials.

15286

Smuckler, J.H. (Conductive Polymer Corp., Marblehead, MA) and P.M. Finnerty (Cabot Corp., Billerica, MA).
PERFORMANCE OF CONDUCTIVE CARBON BLACKS IN A TYPICAL PLASTICS SYSTEM.
Advances in Chemistry Series, No. 134, 1974, pp. 171-183.

Carbon black, used primarily as a reinforcing filler in rubber, exhibits properties of electrical conductivity and physical form which render it the preferred filler for imparting conductivity to normally insulative elastomeric and thermoplastic polymers. The properties of carbon black, important in imparting conductivity to polymer systems, are discussed. The effects of three different carbon black types at varying concentrations on the electrical, physical, and rheological properties of poly(ethylene vinyl acetate) (EVA) in both thermoplastic and thermoset form are also illustrated. Reference is also made to the phenomenon of significant resistivity variations with increasing temperature of carbon black-loaded plastics systems.

15302

Anon.
COPING WITH STATIC ELECTRICITY - PART XX, ESD REFERENCE & DIRECTORY.
Evaluation Engineering, Vol. 19, No. 5, September/October 1980, pp. 10-25.

This article is a reference and directory on ESD suppliers of materials and equipment as well as organizations offering services in the ESD field as consultants or as sponsors of training programs.

15469

Durgin, D.L., and R.M. Brown (BDM, Inc., Albuquerque, NM).
KEY SUPPRESSION DEVICE PARAMETERS FOR EMP HARDENING.
Nuclear EMP, PEM-38, March 1975, 18 pp.

The electrical transients induced by EMP exhibit unique characteristics which differ considerably from transients associated with other phenomena such as lightning, switching, and circuit malfunctions. The suppression techniques developed to handle more common transients can be used for EMP damage protection. This paper derives and/or defines a consistent set of parameters based on EMP circuit hardening requirements and on measurable component parameters and is concerned only with use of TPDs to prevent permanent damage. Three sets of parameters pertaining to pertinent TPD functional characteristics were defined as standby parameters, protection parameters and failure parameters.

15483

Anon. (Square D Company).
GROUNDING - HOSPITAL ISOLATING SYSTEMS.
1975, pp. 11-14.

Grounding in a patient-care and in an anesthetizing location is an important ingredient in safeguarding against shock and

electrocution. Proper grounding provides a means for dissipating static charges and shunting fault current and normal leakage currents away from attendants.

15484

Friedlander, G.D.
ELECTRICITY IN HOSPITALS: ELIMINATION OF LETHAL HAZARDS.
IEEE Spectrum, September 1971, pp. 40-51.

The problems of macroshock and microshock in hospitals have received considerable coverage recently in the press, in symposia sponsored by professional societies, and in technical publications. The general subject falls within a sensitive and controversial area in which proposals for upgrading the safety of medical-electrical equipments are being studied and/or implemented.

15532

Keller, J.K., B.A. Unger, R.G. Chemelli, and P.R. Bossard (Bell Laboratories, Allentown, PA, and Bell Laboratories, Murray Hill, NJ) A.R. Hart, and T. Teng (Hewlett Packard Co., Corvallis, OR).
COPING WITH STATIC ELECTRICITY - PART XXII, HIGHLIGHTS FROM EOS/ESD SYMPOSIUM PAPERS.
Evaluation Engineering, Vol. 20, No. 1, January/February 1981.

Papers presented at the EOS/ESD Symposium in San Diego explored problems of special concern in today's world of super-sophisticated electronics. This article consists of abstracts from three of those papers.

15533

Scovern, J.L. (ITT Courier Terminal Systems, Inc., Tempe, AZ).
REDUCING SOLDER DEFECTS USING TOPICAL ANTISTATS.
Circuits Manufacturing, Vol. 21, No. 4, April 1981.

Many people believe that one topical antistat is as good as another. That belief is absolutely false. Using a good topical antistat solution not only controls electrostatic damage during printed circuit board (PCB) processing but actually improves solderability, reducing solder defects by over 80%. This paper discusses the author's experiments and results using antistat during PCB processing.

15534

Baumgartner, G.T., and M.T. Brandt (Vinyl Plastics, Inc., Sheboygan, WI).
COPING WITH STATIC ELECTRICITY - PART XVIII, CONDUCTIVE FLOORING AND HOW IT WORKS.

Evaluation Engineering, Vol. 19, No. 3, May/June 1980, pp. 66-70.

In response to the rapidly growing industry awareness of the need for methods and materials to control ESD, conductive flooring is receiving increasing attention and is being incorporated into the ESD control programs of several leading electronics manufacturers.

15535

Rosenthal, L.A. (Union Carbide Corp., Research and Development Department Chemicals and Plastics, Bound Brook, NJ).
ELECTROSTATIC DISCHARGES FROM DIELECTRIC SURFACES.
January 15, 1975, 9 pp.

There is a general concern as to the potential hazard that may result from electrostatic discharges off dielectric surfaces in the presence of explosive hydrocarbon vapors. Two systems are considered. A dielectric supported by a grounded metallic electrode can accept a charge over the dielectric surface in the manner of an incomplete capacitor. A second case of interest is the simple thick dielectric surface wherein charges placed on the surface are trapped and produce an electric field. There are no ground surfaces to enhance the energy storage. This paper presents certain theoretical and experimental observations for these two different systems.

15536

Rzepecki, R.M. (Pervel Industries, Inc., Plainfield, CT).
STATIC PROTECTION FOR ELECTRONIC COMPONENTS.
Machine Design, Vol. 53, No. 7, March 26, 1981, pp. 97-104.

Electronic components are especially vulnerable to static electricity during breadboarding, manufacturing, packaging, and shipping. During all these activities, plastics can play an important role by providing just the right conductivity to prevent damage from static discharge. This article is an overview of ESD sources, effects, and gives characteristics of various conductive plastic materials and how they apply to static protection.

15546

Christou, A. (U.S. Navy, Naval Research Laboratory, Washington, DC).
ELECTRO-THERMOMIGRATION IN AL/SI, AU/SI INTERDIGITIZED TEST STRUCTURES.
Journal of Applied Physics, Vol. 44, No. 7, July 1973, pp. 2975-2979.

Metal migration induced by electric field and temperature gradients has been studied in aluminum-silicon and gold-silicon interdigitized test structures. At current densities of 2×10^6 A/cm² and temperature gradients of 75 °C/cm, migration occurred across the Si-SiO₂ interface. Calculated diffusion profiles show that below 350°C, mass transport is more rapid with aluminum. At temperatures between 350°C and 550°C, metal migration is more rapid with gold metallization. Metal migration was shown to be a multistaged process without the existence of a unique activation energy.

15558

DeForest, S.E. (University of California, Inst. for Pure and Applied Physical Science, La Jolla, CA).
SPECIFICATION OF GEOSYNCHRONOUS PLASMA ENVIRONMENT.
Rept. No. AFGL-TR-77-0031, Contract No. F19628-76-C-0214, AD/A041 910, February 1, 1977, 34 pp.

Data for UCSD plasma instruments on the ATS 5 & 6 satellites has been studied to specify the geosynchronous plasma environment as it affects electrostatic charging of spacecraft. The emphasis of the initial study has been primarily to service the needs of the design engineer, while simultaneously establishing the context in which a more general model could be developed. The report includes an environmental specification plus a review of geosynchronous plasma and wave phenomena.

15561

Morel, P.R., F.A. Hanser, and B. Sellers (Panametrics, Inc., Waltham, MA).
DESIGN OF INSTRUMENTATION SUITABLE FOR THE INVESTIGATION OF CHARGE BUILDUP PHENOMENA AT SYNCHRONOUS ORBIT.
Rept. No. AFGL-TR-79-0235, Contract No. F19628-74-C-0217, AD/A081 378, October 1978, 104 pp.

A satellite-borne Rapid Scan Particle Spectrometer (RSPS) has been designed to measure the charge buildup phenomena at synchronous orbit. Simultaneous measurements along two orthogonal axes are made. Each axis incorporates 4 electrostatic analyzers (ESA) and 2 solid state spectrometers (SSS). Four ESAs (low energy p, low energy e; high energy p, high energy e) and two SSSs (proton, electron) with four and five energy bins, respectively, in each analyzer provide a logical compromise of energy resolution and high time resolution. The low energy ESAs cover the energy range 0.05 to 1.7 keV; the high energy ESAs cover the 1.7 to 60 keV

range. The electron SSSs cover the 30 to 1000 keV range and the proton SSSs cover the 70 to 7000 keV range. A complete energy spectrum is generated every 1 second. The digital data output consists of a 9 bit mantissa and a 3 bit exponent, allowing accumulation of greater than 1.3×10^5 counts. A command control allows the ESA or SSS sweep rate to be decreased, or fixed, enhancing the time resolution of portions of the spectrum. A digital count ratemeter with 250 usec integration time is included. A multiplexer controlled by ground command selects the ratemeter input from one of the 8 ESAs or 8 SSSs. Very high time resolution data can be generated by this circuit. Two instruments have been fabricated, tested and calibrated. The first of these was launched into near-synchronous orbit on board the SCATHA satellite on 30 January 1979.

15562

Adamo, R.C., and J.E. Nanevich (SRI International, Menlo Park, CA).
CHEMICAL PHYSICS OF CHARGE MECHANISMS IN NONMETALLIC SPACECRAFT MATERIALS.
Rept. No. AFOSR-TR-80-0125, Contract No. F49620-77-C-0113, AD/A081 487, May 1979, 37 pp.

The interactions of spacecraft and space systems with the changing solar illumination and charged-particle environments in the vacuum of space result in the occurrence of a number of electrostatic and electromagnetic phenomena. These phenomena, commonly referred to collectively as spacecraft charging effects, can produce undesirable and sometimes serious problems with the performance and operation of military, commercial and NASA spacecraft.

15569

Roe, J.M. (McDonnell Douglas Astronautics Co., St. Louis, MO).
MICROWAVE INTERFERENCE EFFECTS IN INTEGRATED CIRCUITS.
IEEE - 17th Electromagnetic Compatibility Symposium, Session 4A18, October 7-9, 1975, 6 pp.

The susceptibility of components to conducted EM energy is required to determine the severity of potential problems in specific cases and to establish the degree of protection required to ensure proper system operation. Representative circuit types are studied to determine underlying physical mechanisms from which models can be derived to extend the results across entire device families.

15576

Visnapuu, L.Y. (U.S. Air Force Systems Command, Foreign Technology Division).
ATOMIZER WITH INDUCTIVE ELECTRODE.
Report No. FTD-ID(RS)-T-1051-77, AD/B024391L, 1973, 4 pp.

This is an invention in the field of pneumatic devices for producing electrically charged particles in a gas medium. It can be used for the settling of sprayed substances on various surfaces; for example, in the aerosol disinfection method and in neutralizing electrostatic charges.

15581

Tasca, D.M., H.B. O'Donnell, and S.J. Stokes (General Electric Co., Space Division, Philadelphia, PA).
PULSE POWER RESPONSE AND DAMAGE CHARACTERISTICS OF CAPACITORS.
Rept. No. AFWL-TR-76-316, Report No. 76SDS4279, Contract No. F29601-75-C-0130, June 1977, 154 pp.

This project summarizes the experimental and theoretical work performed to define EMP pulse response and damage characteristics of a variety of capacitor types. 2079 capacitor units were experimentally evaluated. Of these, 1201 were of the electrostatic type and 878 were of the electrolytic type.

15583

Aleksandrov, V.G., B.I. Bazanov, and A.V. Mayorov (U.S. Army Foreign Science and Technology Center).
INDIVIDUAL PROTECTION AGAINST MICROWAVE RADIATION AND STATIC ELECTRICITY.
Rept. No. FSTC-1440-79, AD/B047 639, April 1980, 7 pp.

This report deals with microwave radiation and static electricity protective gear, the various types of gear available, and what working conditions would warrant the wearing of protective garb.

15584

Naplava, A. (Research Institute for Processing and Applications of Plastics, Nitra).
INTRODUCTION TO THE ANTISTATICS OF PLASTICS.
Rept. No. FSTC-HT-1031-79, Plasty a kaučuk, Vol. 15, No. 10, AD/B046 562L, 1978, pp. 300-304.

This article contains a brief outline of the principles of the formation of an electrostatic charge and the method for its elimination. The practical application of the

method is shown specifically as it relates to plastics. Basic methods for elimination of an electrostatic charge are described together with a detailed analysis of antistatic finishing of plastics with emphasis on thermoplastics. Various types of antistatics are characterized with a view to their applications.

15585

Solomon, P.M., and J.M. Aitken (IBM, Thomas J. Watson Research Center, Yorktown Heights, NY). CURRENT AND C-V INSTABILITIES IN SiO₂ AT HIGH FIELDS. Rept. No. ETR-77-0023, Contract No. F19628-76-C-0249, AD/A043 740, September 1977, 6 pp.

Results have been obtained concerning the interrelation of current and C-V instabilities in MOS capacitors subjected to negative gate high field pulsing. Rising current transients and negative C-V shifts both show the formation of positive charge in the oxide. However, this charge appears to be situated close to the electrodes rather than in the bulk of the oxide and the temperature dependence of the rate of charge accumulation near the electrodes is different for the aluminum and silicon electrodes.

15662

Jordan, A.S., J.C. Irvin, and W.O. Schlosser (Bell Laboratories, Murray Hill, NJ). A LARGE-SCALE RELIABILITY STUDY OF BURNOUT FAILURE IN GaAs POWER FETS. IEEE - 18th Reliability Physics Symposium, April 8-10, 1980, Catalogue No. 80CH1531-3, pp. 123-133.

Burnout can be the dominant failure mode in GaAs power FETs. Since this is a process without electrical precursors, special experimental and statistical treatment appropriate to censored data has to be employed. The resulting failure distribution is lognormal and depending on the operating conditions a maximum failure rate between 400 and 4500 FITs is projected.

15672

Hart, A., T. Teng, and A. McKenna (Hewlett Packard Co., Corvallis, OR). RELIABILITY INFLUENCES FROM ELECTRICAL OVERSTRESS ON LSI DEVICES. IEEE - 18th Reliability Physics Symposium, April 8-10, 1980, Catalogue No. 80CH1531-3, pp. 190-196.

Reliability prediction of MOS LSI devices by testing at elevated temperature can be influenced by electrostatic discharge and electrical overstress conditions during the test period. MOS devices that used junction

diodes in the input protection structure were found to be more susceptible to failure from electrostatic discharge in 125°C ambient temperature than at 25°C. Failure analysis and modeling indicate that this effect is more severe for MOS LSI devices than for bipolar devices due to the doping levels used in the MOS technology. These effects will impact accelerated life testing, simulation testing of electronic systems to be operated at elevated temperatures and failure analysis techniques performed at elevated temperatures.

1572

Smith, J.S. (Lockheed Palo Alto Research Laboratory, Palo Alto, CA). ELECTRICAL OVERSTRESS FAILURE ANALYSIS IN MICROCIRCUITS. IEEE - 16th Reliability Physics Symposium, April 18-20, 1978, Catalogue No. 78CH1294-8PHY, pp. 41-46.

A major cause of semiconductor failure is electrical overstress (EOS). Examination of the failed device will often yield sufficient information to determine the dimensions of the electrical transient causing failure. The purpose of this paper is to identify the clues and relevant features that will permit the failure analyst to estimate the dimensions of the electrical transient involved.

15726

Wunsch, D.C. (BDM Corp., Albuquerque, NM). THE APPLICATION OF ELECTRICAL OVERSTRESS MODELS TO GATE PROTECTIVE NETWORKS. IEEE - 16th Reliability Physics Symposium, April 18-20, 1978, Catalogue No. 78CH1294-8PHY, pp. 47-55.

The study of electrical overstress failure in bipolar semiconductor devices from transients induced from nuclear electromagnetic pulses resulted in understanding of failure mechanism, models to predict failure levels, test techniques, and guidance for hardness assurance and reliability of gate input protective networks. The applicability of failure mechanisms and models for components of gate input protective networks such as resistors, diodes, and interconnect metallization stripes is shown.

15732

Calvin, H., H. Hyatt, H. Mellberg, and D. Pellinen (Experimental Physics Corp., Hayward, CA). MEASUREMENT OF FAST TRANSIENTS AND APPLICATION TO HUMAN ESD. IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 225-230.

Voltage and current diagnostics have been developed with nanosecond response for measuring electrostatic discharges of humans. Calibration techniques and waveform corrections for actual electrostatic discharges from a number of people will be and are compared with equivalent circuit models.

15734

Perkins, J. (Hi-Rel Laboratories).
COPING WITH STATIC ELECTRICITY - PART XXIII,
ARE YOU IGNORING ESD-SENSITIVE COMPONENTS?
Evaluation Engineering, Vol. 20, No. 3,
May/June 1981, pp. 84-93.

MOS and linear devices need protection from electrostatic discharge. Bipolar devices (including TTL logic and discrete transistors) require protection, too. Yet the same potential for degradation and failure exists. This article presents descriptions of how integrated circuits and discrete components can be damaged by electrostatic discharge.

15742

Copeland, J.T. (NASA, Materials Testing Branch, Kennedy Space Center, FL).
EVALUATION OF THE ELECTROSTATIC CHARGE DISSIPATION PROPERTIES OF ANTISTATIC NYLON SHEET MATERIAL, RCAS 2400, AS A FUNCTION OF RELATIVE HUMIDITY.
Rept. No. MTB-066-72, June 1972, 6 pp.

Preliminary tests indicated that the electrostatic properties of materials are highly dependent on environmental conditions and on the particular type of apparatus used for testing. An attempt was therefore made to develop an apparatus and test method which would provide reliable measurements.

15743

Walker, R.C. (IIT Research Institute, Reliability Analysis Center, Griffiss AFB, NY) and T. Oishi (U.S. Navy, NAVSEA, Washington, DC).
EOS/ESD SUSCEPTIBILITY - EMERGENCE AS A DESIGN CONSTRAINT.
1980 Government Microcircuit Applications Conference, Contract No. F30602-78-C-0281.

It is the purpose of this paper to illustrate that for some time a design constraint namely EOS/ESD susceptibility has been overlooked in the design of electronic equipment and must now be recognized and instituted as a design criteria to avoid costly redesign and retrofit programs. Not taking EOS/ESD susceptibility into account will result in program cost overruns from production waste, equipment delivery delays, and spares usage.

15746

Bhatti, I.S., E. Fuller, and F.B. Jenne (American Microsystems, Inc., Santa Clara, CA).
VMOS ELECTROSTATIC PROTECTION.
IEEE - 16th Reliability Physics Symposium, April 18-20, 1978, Catalogue No. 78CH1294-8PHY, pp. 140-145.

Present state of the art MOS devices with 1000Å thick gate oxides have breakdown voltages in the 60-80 volts range. Due to higher fields in the oxide at the bottom of the V-groove, VMOS devices with the same oxide thickness have lower breakdown voltages (25-30 volts). A VMOS protection device with higher protection capability than conventional MOS protection devices has been designed and tested. It consists of a poly resistor connected to a n-p-n diode, followed by an implanted n+ diffusion which acts as a distributed RC network attenuating the input voltage spikes. The final section consists of a planar NMOS transistor connected between the n+ diffusion and the VMOS gate. Tests show that this type of protection device is superior to conventional protection devices.

15769

Berbeco, G.R. (Charleswater Products, Inc., Needham, MA).
PASSIVE STATIC PROTECTION: THEORY AND PRACTICE.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 1-11.

A technical literature survey is presented of theoretical and experimental work on static protection in the electronics industry. These results are compiled and discussed with respect to the usefulness of alternative passive static protection systems. A survey of end-users of passive static protection systems has been conducted, and these practical results are compared with the published literature data. The advantages and disadvantages of alternative systems' approaches are summarized.

15770

Overbay, D.E., H.Z. Snyder, and J.M. Calderbank (E-Systems, Inc., ECI Division, St. Petersburg, FL).
THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 12-16.

This paper attempts to quantify and provide models for the electrostatic charge levels generated and the residual charges

remaining in high humidity conditions. The results of a controlled experiment with sufficient replications to assure statistical significance will be presented.

15771

Bossard, P.R., R.G. Chemelli, and B.A. Unger (Bell Laboratories., Murray Hill, NJ).
ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 17-22.

Integrated circuit failures can be caused by discharging a device through a low impedance path. Discharge pulses with average power densities of approximately (10^9 W/cm) occur with subnanosecond time constants. These pulses contain sufficient power to damage or melt silicon IC components. A simple equivalent circuit that describes the discharge pulse agrees with experimentally observed results.

15772

Wu, C., and E.D. Paradise (IBM Corp., Poughkeepsie, NY).
ELECTROSTATIC DISCHARGE (ESD) MONITOR DESIGN.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue EOS-2, September 9-11, 1980, pp. 23-25.

This paper is based on work performed during interference analysis for computer systems. Emphasis is on the designing of a high-efficiency, economically feasible ESD monitor which detects external ESD events of a given magnitude on designated positions of a system. Design characteristics, test results and possible ways for improvement are also discussed.

15773

Philipp, H.R., and L.M. Levinson (General Electric Corporate Research and Development, Schenectady, NY).
TRANSIENT PROTECTION WITH ZnO VARISTORS: TECHNICAL CONSIDERATIONS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 26-34.

ZnO varistors are novel ceramic devices used for the protection of electronic circuits against transient overvoltages. A technical description of the operation of this device is given including conduction mechanisms, response time and energy handling capability. Its applicability to a wide variety of transient phenomena is discussed.

15774

Hopkins, D.C. (General Electric Co., Syracuse, NY).
PROTECTIVE LEVEL COMPARISONS FOR VOLTAGE TRANSIENT SUPPRESSORS (120V, AC TYPE).
IITRI - EOS/ESD Symposium, September 9-11, 1980, RAC Catalogue No. EOS-2, pp. 35-43.

This report compares test results of voltage suppression capability for a selected number of suppressors. The following test conditions were used for testing: (1) .5 us rise time to rest, followed by a 100 KHz ring with a 40% reduction in each successive peak; (2) .5 us - 100 KHz ring wave applied to an L filter (200 uH inductor and a .25 uF shunt capacitor); (3) a 2500 volt peak surge having 2 us maximum rise time to crest and a 10 us minimum decay time to half crest; and (4) the 2 us x 10 u wave of condition (3) applied to the L filter of condition (2). Results from tests using these waveforms were also correlated with the cost of the devices.

15775

Bazarian, A. (General Instrument Corp., Chicago, IL).
GAS TUBE SURGE ARRESTERS FOR CONTROL OF TRANSIENT VOLTAGES.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 44-53.

This article summarizes briefly the state-of-the-art of gas discharge surge arrestors including a description of Uni-Imp devices, miniature CommGaps and the recent development of carbon block replacement arrestors for the telecommunications industry. Applicability to power line surges and signal line transients will be discussed. Characteristics of various types of devices with respect to electrical and environmental parameters will be presented.

15776

McAteer, O.J., R.E. Twist (Westinghouse Electric Corp.) and R.C. Walker (IIT Research Institute).
IDENTIFICATION OF LATENT ESD FAILURES.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 54-57.

At the present time there is much interest in the subject of latent ESD failures. A latent ESD failure is defined as a time-dependent failure that occurs under use conditions because of earlier exposure to electrostatic discharge that did not result in

an immediately detectable out-of-spec condition. There is considerable disagreement among ESD specialists as to whether or not latent failures of this type are a reality. The purpose of this paper is to present the results of accelerated life tests conducted on Trident program parts of several semiconductor technologies after both single and multiple ESD exposures.

15777

Zajac, H. (Tektronix, Inc., Beaverton, OR).
STUDY OF EFFECTS OF ELECTRO-STATIC DISCHARGE ON SOLID-STATE DEVICES.
National Electronic Packaging and Products Conference, Vol. I, 1980.

A model was developed for simulation of charged-personnel ESD (Electro-static Discharge) damage to selected solid-state devices. ESD damage levels are presented, and recommendations for handling static-sensitive devices are given.

15778

Alexander, D.R. (Sandia National Laboratories, Albuquerque, NM) E.W. Enlow, and R.J. Karaskiewicz (BDM Co., Albuquerque, NM).
FAILURE THRESHOLD DISTRIBUTIONS IN BIPOLAR TRANSISTORS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 59-66.

A sample of 10,000 bipolar silicon transistors had been tested to provide information on the functional form and parameter values for failure threshold distributions arising from exposure to electrical overstress pulses. The sample was chosen to permit evaluation of the effects of topological and diffusion profile variations on the failure threshold. Testing results are summarized in terms of parameter values for mathematically defined distributions which fit the data within a 5% level of significance.

15779

Castle, G.S.P., and D.R. Hibbert (University of Western Ontario, Faculty of Engineering Science, London, Ontario) and W.D. Greason (Northern Telecom, Canada Limited, London, Ontario).
ANALYSIS OF ESD DAMAGE IN JFET PREAMPLIFIERS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 67-72.

JFET preamplifiers, used in electric microphones, can be damaged by ESD from human bodies. Unprotected microphones were subjected to ESD simulation tests, and damaged units were analyzed to determine the discharge

path and failure mechanism. Thermal vaporization of the contact finger metallization was revealed as the failure mode.

15780

Keller, J.K. (Bell Laboratories, Allentown, PA).
PROTECTION OF INTEGRATED CIRCUITS FROM DESTRUCTION BY ELECTROSTATIC DISCHARGE.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 73-80.

Protection of MOS integrated circuits from electrostatic discharge (ESD) is a necessity. To allow selection of the most efficient on-chip protection network, an experimental test method was developed. This paper briefly describes various networks and their evaluation using this technique. From the data gathered, a new design was proposed and tested. Guidelines for chip layout and resultant voltage levels of ESD protection are presented, especially as related to this design.

15781

Luisi, J.A. (Rockwell International, Anaheim, CA).
SOS PROTECTION - THE DESIGN PROBLEM.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 81-86.

This paper discusses the design aspects of protection networks for SOS circuits. Topics such as critical parameters, design constraints, desirable features, and design perspectives are covered. An example is presented to illustrate some of the compromises required.

15782

Hart, A.R., and T. Teng (Hewlett Packard Co., Corvallis Division, Corvallis, OR).
LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue EOS-2, September 9-11, 1980, pp. 87-94.

Process and design layout variations can drastically change the ESD protection capability of proven input protection structures on LSI devices. Resistor-Diode type structures are investigated for lot-to-lot and wafer-to-wafer variations and their effects on ESD failure voltage. Failure modes and mechanisms are described. Data from ESD tests on devices using corrective redesign approaches allowing for these effects will be shown.

15783

Turner, T.E., and S. Morris (Mostek Corp., Carrollton, TX).
ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 95-103.

This paper compares the sensitivities of several common N-MOS input protection networks to a wide range of simulated electrostatic zaps. Layout sensitivities of these circuits are also explored.

15784

Schwank, J.R., R.P. Baker, and M.G. Armendariz (Sandia National Laboratories, Albuquerque, NM).
SURPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 104-111.

CMOS ESD failures in a product where, by design, the device input terminals are not accessible to ESD led to this study of device susceptibility and an analysis of the long-term reliability of devices in assemblies from that production line. This paper shows some surprising patterns of device susceptibility and shows that the probability of long-term failure in devices whose electrical characteristics have been degraded by electrostatic discharge is small.

15785

Hower, P.L. (Westinghouse Research and Development Center, Pittsburgh, PA).
HIGH-FIELD PHENOMENA AND FAILURE MECHANISMS IN BIPOLAR TRANSISTORS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 112-116.

Various avalanche mechanisms can initiate second breakdown and other undesirable phenomena in switching transistors. The present understanding of avalanche injection will be reviewed with emphasis on the events that occur during inductive turn-off of a bipolar transistor.

15786

Mathews, D. (U.S. Army Missile Command, Redstone Arsenal, AL).
SOME DESIGN CRITERIA FOR AVOIDING SECOND BREAKDOWN IN BIPOLAR DEVICES.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 117-121.

Design criteria are demonstrated by which certain undesirable structural and doping configurations can be avoided in bipolar device designs, based on the physics of hot spot and melt channel formation. The roles of avalanche breakdown, ratios of certain structural dimensions, and other factors are explored. The Wunsch model is extended to a distributed source model.

15787

Knight, E.R., and P.P. Budenstein (Auburn University, Physics Department, AL).
EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 122-129.

Experiments were performed on thin film (0.4 μm) silicon-on-sapphire (SOS) diodes ($\text{p}^+\text{-n-n}^+$) to determine the effect of junction diffusion spikes (5 μm length) and doping level (10^{15} to 10^{17} atoms/ cm^3) on current configurations and second breakdown susceptibility for pulses 10 μs in duration. Voltage, current and energy thresholds were obtained. The results provide perspective on some types of "maverick" devices, on second breakdown testing methodology, and on device design for reducing second breakdown susceptibility.

15788

Ward, A.L. (U.S. Army Electronics Research and Development Command, Harry Diamond Laboratories, Adelphi, MD).
OSCILLATING VOLTAGE PULSES AND SECOND BREAKDOWN.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 130-139.

Electrical overstress on semiconductor devices is often oscillating (e.g., lightning and EMP), but theoretical considerations of such pulses have been severely limited. An electrothermal model computer program has now been applied to study high-current forward conduction in silicon diodes and reverse-bias switching transients, which result in avalanche breakdown.

15789

Horgan, E.L. (TRW Defense and Space Systems Group, Redondo Beach, CA).
ASSESSING ELECTRICAL OVERSTRESS EFFECTS ON ELECTRONIC SYSTEMS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 140-148.

An overview of existing methodologies utilized by TRW Systems Group for the statistical assessment of electronic equipment is presented. Analysis guidelines for the evaluation of both direct-drive and buried circuit potential vulnerabilities are considered. The treatment includes a discussion of damped sine frequency spectrum versus calculated transient threats, system probability of survival, modeling and computerized analysis.

15790

Smyth, J.B., V.A.J. Van Lint, and A.R. Hart (Mission Research Corp., La Jolla, CA). SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS. IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 149-153.

A thermal model to bound the burnout phenomenon associated with electrical overstress in solar cells is presented. Analyses suggest that for a typical cell undergoing an overstress of duration between 100ns and 100ms, failure will result from melting of metallization at the input point.

15791

Durgin, D.L. (Booz-Allen & Hamilton, Inc., Bethesda, MD). AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS. IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 154-160.

Electronic devices and equipment may be subjected to electrical transients caused by several stimuli including lightning, nuclear electromagnetic pulse (NEMP), electromagnetic interference (EMI), and handling-related electrostatic discharge. The characteristics and severity of the resulting electrical transients vary considerably depending on the specific source. This paper describes the various sources of electrical overstress and the unique problems they create relative to analysis, simulation and protection design.

15792

Hess, R.F. (Sperry Flight Systems, Phoenix, AZ). TEST WAVEFORMS AND TECHNIQUES TO ASSESS THE THREAT TO ELECTRONIC DEVICES OF LIGHTNING-INDUCED TRANSIENTS. IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 161-166.

Various design trends in aerospace vehicle electrical/electronic equipment have resulted in a heightened concern about sub-

system hardness to the EM transients produced by lightning. The Society of Automotive Engineers (SAE) Committee AE-4L (lightning) to improve the ability to define and obtain equipment hardened against the lightning-induced transients is preparing definitions for test waveforms, test techniques, and hardness categories. This paper provides a status report of this effort.

15793

Crouch, K.E. (Lightning Technologies, Inc., Pittsfield, MA). LIGHTNING PROTECTION DESIGN FOR A PHOTOVOLTAIC CONCENTRATOR. IITRI - EOS/ESD Symposium, September 9-11, 1980, RAC Catalogue No. EOS-2, pp. 167-175.

An energy source being investigated by the United States Department of Energy (DOE) is photovoltaic generation of electricity from sunlight. Most of such arrays use large areas of solar cells which face the sun. Since silicon solar cells are relatively expensive, photovoltaic concentrator systems are being developed, where the sunlight is optically focused on the cells. These solar cells will be located in populous areas with high incident sunlight. Many of the locations have a high incidence of thunderstorms as well. This paper presents the theory by which lightning-induced electromagnetic pulses (EMP) can cause failure in a photovoltaic system.

15794

Kressler, D.R. (Bell Laboratories, Whippany, NJ). SURGE TESTS ON PLUG-IN TRANSFORMERS. IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 176-183.

Transformers powering communications equipment can be damaged by energy surges on either power or communications lines. Providing a relatively low impedance fault-current path through the transformer and reducing the containment of discharge energy will minimize physical damage. This paper describes the measures and data taken to accomplish this goal in the design of a small, wall-mounted transformer intended for use on the premises of telephone company subscribers.

15795

Antinone, R.J. (The BDM Corp., Albuquerque, NM). MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION. IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 184-188.

A large number of microcircuits fabricated with modern technologies have been tested to determine typical electrical over-stress tolerance. Qualification procedures have been recommended for electrostatic discharge and system transient generated over-stress. Test results, including statistical distribution information, will be presented along with a discussion of testing problems, maverick devices, and testing-induced reliability reduction.

15796

Halperin, S.A. (Analytical Chemical Laboratories, Elk Grove Village, IL).
FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 192-205.

The flow of ESDS components for primary manufacture through assembly and end use of operational equipment consists of several static loss areas. Investigation reveals that each facility in the production chain shares similar static problems. A basic technique of identifying these repetitious loss areas, applying effective long-term problem solutions, and maintaining facility control can eliminate the bulk of those ESD losses attributable to environmental problems. This presentation summarizes the efforts of many corporate engineers, manufacturers, and independent consultants to identify and isolate various operational ESD problems, and introduces the Facility Evaluation guideline.

15797

Domingos, H. (Clarkson College of Technology, Dept. of Electrical and Computer Engineering, Potsdam, NY).
BASIC CONSIDERATIONS IN ELECTRO-THERMAL OVERSTRESS IN ELECTRONIC COMPONENTS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 206-212.

When an electronic device fails due to excessive power dissipation, several factors must be considered in an analysis of the failure: 1) the amount and spatial distribution of the power; 2) the thermal properties of the materials; and 3) the critical temperature which causes failure. This paper summarizes the important aspects and gives general guidelines which should be considered in the design and application of various components.

15798

Bolasny, R.E. (Scientific Enterprises, Inc., Broomfield, CO).

STATIC CONTROL SYSTEMS.

IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 213-217.

This paper discusses recent innovative technological advances which have made possible static controlling systems which operate at high rates of ion generation without the production of ozone or EMI and modern micro-processor technology which has made possible extremely accurate and sensitive static monitoring and measurement instruments.

15799

Sohl, J.E. (Honeywell, Inc., St. Petersburg, FL).
AN EVALUATION OF WRIST STRAP PARAMETERS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-2, September 9-11, 1980, pp. 218-224.

A comprehensive investigation was undertaken to evaluate the human engineering of wrist straps; several alarming results were found. Two points of view are taken: first was the effect of the wrist strap on the operator (operator acceptance); second was the effect of the operator on the wrist strap (durability and reliability). Two sample wrist straps from every major supplier representing the majority of designs presently on the market were included in the study.

15816

Bernett, M.K., and H. Ravner (U.S. Navy, Naval Research Laboratory, Washington, DC).
ALTERNATE ANTISTATIC MATERIALS FOR INSTRUMENT BEARING PACKAGING.
Presented at Communication Control Meeting; also in ASLE Transactions. This document shall not be released to Foreign Governments without approval of the Strategic Systems Project Office or the Ballistic Missile Office.

Antistatic materials in current use as instrument bearing packaging consist of nylon or polyethylene films containing small amounts of surface-seeking antistatic agents. Previous NRL work showed that, on contact, such agents contaminated the bearing metal surface and/or the bearing lubricant. To lessen or eliminate these problems, an investigation was carried out on 1) alternate antistatic agents applied to the polymer films as internal additives or topical coatings, and 2) alternative film materials. Effects of exposure to these alternates on pure lubricants, lubricated bearing steel surfaces, and clean steel surfaces were examined. The results provided valuable information on possibly deleterious transfer of the antistatic agent or other constituents to any contacting surface material.

15818

Bernett, M.K., and H. Ravner (U.S. Navy, Naval Research Laboratory, Washington, DC).
ANTISTATIC AGENTS, LUBRICANTS, AND PRECISION BEARINGS.

Presented at the 36th Annual Meeting of American Society of Lubrication Engineers in Pittsburgh, PA, May 11-14, 1981, ASLE Transactions, Preprint No. 81-AM-1E-3, 5 pp.

Currently used antistatic agents incorporated into polyethylene or nylon films have shown adverse effects on contact with precision miniature bearings and their lubricants. Concern for improvement prompted a search for alternate materials, with the problem being addressed by investigating chemically characterized antistatic agents incorporated in the polymer films, antistatic agents applied topically to the polymer film, and alternative films. Effects of exposure of these alternative materials to pure lubricants, lubricated bearing steel surfaces, and clean steel surfaces were studied. The results suggest possibly deleterious transfer of the antistatic agents to any contacting surface and are discussed in terms of alteration of lubricant properties, lubricant displacement, and surface wettability.

15819

Woods, W.R. (Jet Propulsion Laboratory, Pasadena, CA).

TEST REPORT ON NEW EQUIPMENT AND TECHNIQUES FOR CONTROLLING/MINIMIZING ELECTROSTATIC CHARGE BUILDUP.

Rept. No. 900-987, April 17, 1981, 9 pp.

Some equipment was recently evaluated at JPL that is designed to provide a flood of positive and negative ions in approximately equal quantities into a room typically, but not necessarily, incorporating laminar air flow. In the order of something less than one minute, this is intended to effectively drain any electrostatic charge from almost anything that might inadvertently have been charged up by rubbing, separation, air flow or other phenomena. The equipment consists of plus and minus high voltage power supplies connected to high voltage insulated wires that have been penetrated at regular intervals with sharp needle-like emitters, somewhat similar to phonograph needles. The sharp needles at high potential emit large quantities of ions of both polarities which, when swept throughout the room by air flow and prior to combining and neutralizing each other, allow discharging of objects that the ionized air comes into contact with.

Cable configurations, needle spacing, voltages, and other parameters were varied in the JPL tests to determine which were effective and which of the arrangements gave

the best results. One configuration was markedly superior to all others evaluated and did produce a very beneficial effect. Within the bounds of the one-week time period available for the testing, the conclusion was reached that the equipment could be of significant benefit to many JPL facilities involved with electrostatic-sensitive electronic hardware. With a typical room installation requiring very little installing cost and the equipment priced in the several hundreds to very few thousands of dollars bracket, it would appear to be extremely cost-effective as well as providing a significant additional safeguard for our flight and other sensitive electronic hardware that is vulnerable to ESD damage.

15932

Unger, B.A. (Bell Laboratories, Murray Hill, NJ).

ELECTROSTATIC DISCHARGE FAILURES OF SEMICONDUCTOR DEVICES.

19th Annual Reliability Physics Proceeding, April 7-9, 1981, Catalogue No. 81CH1619-6, pp. 193-199.

Electrostatic discharge (ESD) is a significant cause of device failures at all stages of device and equipment production, assembly, test, installation and field use. Even though device designs include protection circuitry, it is relatively easy to generate static potentials during handling and shipping that exceed the limits of the protection networks. Damage from electrostatic discharge can cause either complete device failure by parametric shifts or device weakness by locally heating, melting, or otherwise damaging oxides, junctions or device components.

15933

Goel, A. (American Microsystems, Inc., Santa Clara, CA).

PROCEDURE FOR TESTING ELECTROSTATIC DISCHARGE SUSCEPTIBILITY OF MOS DEVICES.

19th Annual Reliability Physics Proceeding, Catalogue No. 81CH1619-6, April 7-9, 1981, pp. 200-203.

This paper delineates a method for determining the susceptibility levels of packaged devices to electrostatic discharge potential. This paper presents examples of protection network configurations, along with failure threshold levels, and the damage mechanisms.

15936

Fisch, D.E. (Mostek Corp., Carrollton, TX).

A NEW TECHNIQUE FOR INPUT PROTECTION TESTING.

19th Annual Reliability Physics Proceeding, Catalogue No. 81CH1619-6, April 7-9, 1981, pp. 212-217.

Input protection circuits are evaluated in a typical manner by resistively discharging a capacitor into the tested device with some of its pins grounded. These techniques usually result in junction damage in or near the input protection circuit rather than in gate oxide ruptures as is seen in most electrostatic damage field failures. A new testing technique has been developed to eliminate this inconsistency.

15938

Dechiaro, L.F. (Bell Laboratories, Allentown, PA).
ELECTRO-THERMOMIGRATION IN NMOS LSI DEVICES.
19th Annual Reliability Physics Proceeding, April 7-9, 1981, Catalog No. 81CH1619-6, pp. 223-229.

Electro-thermomigration of aluminum metallization through contact windows into the substrate accounts for many of the burn-in failures for certain NMOS LSI devices. The developmental history of this failure mode was studied by an analysis of the failed devices and by controlled electrostatic discharge stressing.

15978

Stevens, N.J., F.D. Berkopec, and J.V. Staskus (Lewis Research Center, Cleveland, OH).
TESTING OF TYPICAL SPACECRAFT MATERIALS IN A SIMULATED SUBSTORM ENVIRONMENT.
Proceedings of the Spacecraft Charging Technology Conference, Rept. No. AFGL-TR-77-0051, Rept. No. NASA TMX-73537, AFSG NO. 364, AD/A045 459, February 24, 1977, pp. 431-457.

A series of survey tests have been conducted in the Lewis Research Center substorm simulation facility. The test specimens were spacecraft paints, silvered Teflon, thermal blankets and solar array segments. The samples, ranging in size from 300 to 1000 cm², were exposed to monoenergetic electron energies from 2 to 20 keV at a current density of 1 nA/cm². The samples generally behaved as capacitors with strong voltage gradients at their edges. The charging characteristics of the silvered Teflon, Kapton, and solar cell covers were controlled by the secondary emission characteristics. Insulators that did not discharge were the spacecraft paints and the quartz fiber cloth thermal blanket sample. All over samples did experience discharges when the surface voltage reached -8 to -16 kV. The discharges were photographed. The breakdown voltage for each sample was determined, and the average energy lost in the discharge was computed.

15979

Purvis, C.K., N.J. Stevens, and J.C. Oglebo (Lewis Research Center, Cleveland, OH).
CHARGING CHARACTERISTICS OF MATERIALS COMPARISON OF EXPERIMENTAL RESULTS WITH SIMPLE ANALYTICAL MODELS.
Proceedings of the Spacecraft Charging Technology Conference, Rept. No. AFGL-TR-77-0051, Rept. No. NASA TMX-73537, AFSG No. 364, AD/A045 459, February 24, 1977, pp. 459-486.

An understanding of the behavior of materials, of dielectrics in particular, under charged particle bombardment is essential to the prediction and prevention of the adverse effects of spacecraft charging. This paper presents an effort to obtain such an understanding through a combined analytical and experimental approach. A one-dimensional model for charging of samples in the Lewis Research Center test facility is used in conjunction with experimental data taken in this facility to develop "material charging characteristics" for silvered Teflon. These characteristics are then used in a one-dimensional model for charging in space to examine expected response. Relative charging rates as well as relative charging levels for silvered Teflon and metal are discussed.

15980

Lehn, W.L. (U.S. Air Force Materials Laboratory, Wright-Patterson AFB, OH).
CONDUCTIVE SPACECRAFT MATERIALS DEVELOPMENT PROGRAM.
Proceedings of the Spacecraft Charging Technology Conference, Rept. No. AFGL-TR-77-0051, Rept. No. NASA TMX-73537, AFSG No. 364, AD/A045 459, February 24, 1977, pp. 559-569.

The control of absolute and differential charging of spacecraft cannot be effected without the development of new and improved or modified materials or techniques that will provide electrical continuity over the surface of the spacecraft. The materials' photoemission, secondary emission, thermo-optical, physical, and electrical properties in the space vacuum environment both in the presence and absence of electrical stress and ultraviolet, electron, and particulate radiation are important to the achievement of charge control. The materials must be stable or have predictable response to exposure to the space environment for long periods of time. The materials of interest include conductive polymers, paints, transparent films and coatings as well as fabric coating interweaves. The program initiated by the Air Force Materials Laboratory (AFML) and related efforts to develop these new and modified materials will be discussed in this article.

15981

Gilligan, J.E. (IIT Research Institute, Technology Center, Chicago, IL) and R.E. Wolf, C. Ray (DeSoto, Inc., Des Plaines, IL). **ELECTRICALLY CONDUCTIVE PAINTS FOR SATELLITES.** Proceedings of the Spacecraft Charging Technology Conference, Rept. No. AFGL-TR-77-0051, Rept. No. NASA TMX-73537, AFSG No. 364, AD/A045 459, February 24, 1977, pp. 593-611.

A program was conducted to develop and test electrically conductive paint coatings for spacecraft. A wide variety of organic and inorganic coatings were formulated using conductive binders, conductive pigments, and similar approaches. Z-93, IITRI's standard specification inorganic thermal control coating, exhibits good electrical properties ($\sim 10^9$ ohms) and is a very space stable coating system. Several coatings based on a conductive pigment (antimony-doped tin oxide) in silicone and silicate binders offer considerable promise. Paint systems using commercially available conductive polymers also appear to be of interest but will require substantial development. Evaluations were made based on reflectance in space environmental testing.

15982

Shai, M.C. (NASA, Goddard Space Flight Center, Greenbelt, MD). **FORMULATION FOR ELECTRICALLY CONDUCTIVE THERMAL-CONTROL COATINGS.** Proceedings of the Spacecraft Charging Technology Conference, Rept. No. AFGL-TR-77-0051, Rept. No. NASA TMX-73537, AFSG No. 364, AD/A045 459, February 24, 1977, pp. 613-620.

Formulation of electrically conductive, thermal-control coatings was undertaken for use on the International Sun Earth Explorer (ISEE) spacecraft. Unsuccessful formulation efforts as well as the successful use of oxide pigments fired at 1175°C are described. Problems attributed to reactivity of specific coating vehicles exposed to high humidity are discussed. The emphasis of this report is placed on coating formulation and application techniques. Methods of varying optical properties are also described as well as formulation of white, low-absorptance coatings.

15983

Amore, L.J., A.E. Eagles (General Electric Co., Space Division, Valley Forge, PA). **MATERIALS AND TECHNIQUES FOR SPACECRAFT STATIC CHARGE CONTROL.** Proceedings of the Spacecraft Charging Technology Conference, Rept. No. AFGL-TR-77-0051, Rept. No. NASA TMX-73537, AFSG No. 364, Contract Nos. F33615-76-C-5075 and F33615-76-C-5258, AD/A045 459, February 24, 1977, pp. 621-654.

This report presents an overview of the design, development, fabrication, and testing of transparent conductive coatings and conductive lattices deposited or formed on high resistivity spacecraft dielectric materials to obtain control of static charge buildup on spacecraft external surfaces. It discussed fabrication techniques for the deposition of indium/tin oxide coatings and copper grid networks on Kapton and FEP Teflon films and special frit coatings for OSR and solar cell cover glasses. The techniques include sputtering, photoetching, silkscreening, and mechanical processes. This report also describes a facility designed and built to simulate the electron plasma at geosynchronous altitudes along with test procedures. The results of material characterizations as well as electron irradiation aging effects in this facility for spacecraft polymers treated to control static charge are presented. The data presents results for electron beam energies up to 30kV and electron current densities of 30nA/cm². Parameters measured include secondary emission, surface leakage, and through the sample currents as a function of primary beam energy and voltage.

15984

Belanger, V.J., and A.E. Eagles (General Electric Company, Space Division, Valley Forge, PA). **SECONDARY EMISSION CONDUCTIVITY OF HIGH PURITY SILICA FABRIC.** Proceedings of the Spacecraft Charging Technology Conference, Rept. No. AFGL-TR-77-0051, Rept. No. NASA TMX-73537, AFSG No. 364, Contract No. F33615-75-C-5267, AD/A045 459, February 24, 1977, pp. 655-668.

High purity silica fabrics have been proposed for use as a material to control the effects of electrostatic charging of satellites at synchronous altitudes. These materials have exhibited very quiet behavior when placed in simulated charging environments as opposed to other dielectrics used for passive thermal control which exhibit varying degrees of electrical arcing. Secondary emission conductivity is proposed as a mechanism for this superior behavior.

Design of experiments to measure the phenomena and data taken in GE research facilities on silica fabrics are discussed as they relate to electrostatic discharge (ESD) control on geosynchronous orbit spacecraft. Studies include the apparent change in resistivity of the material as a function of the electron beam energy, flux intensity, and the effect of varying electric fields impressed across the material under test.

15985

Adamo, R.C., J.E. Nanevich (Stanford Research Institute, Electromagnetic Sciences Labora-

tory) and N. Grier (Lewis Research Center, NASA).

CONDUCTIVITY EFFECTS IN HIGH-VOLTAGE SPACECRAFT INSULATING MATERIALS.

Proceedings of the Spacecraft Charging Technology Conference, Rept. No. AFGL-TR-77-0051, Rept. No. NASA TMX-73537, AFSG No. 364, AD/A045 459, February 24, 1977, pp. 669-686.

A series of laboratory measurements have been performed to explore the effects of various external parameters on the conductivity properties of several typical and potential spacecraft insulating materials in a simulated space environment. The materials tested included Kapton, Teflon, quartz, and polyvinylidene fluoride. The parameters varied in these tests included sample thickness, temperature, applied voltage, illumination intensity and wavelength, and electron beam energy and current density. Tests were performed both with conventional optically transparent gold-front-surface electrodes and with the front surfaces of the test samples exposed directly to an electron beam. All tests were conducted in a vacuum chamber at a pressure of approximately 10^{-6} torr. This paper summarizes some of the more interesting general properties of the materials tested.

15986

Vishmann, W., C.M. Shai, and E.L. Sanford (NASA, Goddard Space Flight Center, Greenbelt, MD).

INVESTIGATION OF CONDUCTIVE THERMAL CONTROL COATINGS BY A CONTACTLESS METHOD IN VACUO.

Proceedings of the Spacecraft Charging Technology Conference, Rept. No. AFGL-TR-77-0051, AFSG No. 364, AD/A045 459, February 24, 1977, pp. 687-698.

A technique for determining the conductance per unit area of thermal control coatings for "electrostatically clean" spacecraft is described. In order to simulate orbital conditions more closely, current density - voltage ($j - v$) curves are obtained by a contactless method in which the paint on an aluminum substrate is the anode of a vacuum diode configuration with a tungsten filament cathode. Conductances greater than 10^{-9} A/V cm^2 have been observed on black paints containing carbon and in white and green paints filled with zinc oxide which has been fired in order to induce defect conductivity. Because of surface effects and the non-homogeneous nature of paints, large discrepancies are found between measurements taken using the contactless method and measurements employing metallic contacts, particularly at low current densities. Therefore, measurements with metallic contacts are considered to be of questionable value in deciding the suitability of coatings for electrostatic charge control.

15988

Ling, D. (General Electric Co., Valley Forge Space Center, Philadelphia, PA).

COMMON APPROACH TO SOLVING SGEMP, DEMP, AND ESD SURVIVABILITY.

Proceedings of the Spacecraft Charging Technology Conference, Rept. No. AFGL-TR-77-0051, Rept. No. NASA TMX-73537, AFSG No. 364, AD/A045 459, February 24, 1977, pp. 789-803.

System Generated Electromagnetic Pulse (SGEMP) and Dispersed Electromagnetic Pulse (DEMP) are nuclear-generated spacecraft environments. Electrostatic Discharge (ESD) is a natural spacecraft environment resulting from differential charging in magnetic substorms. All three phenomena, though differing in origin, result in the same problem to the spacecraft: Electromagnetic Interference (EMI). A common design approach utilizing a spacecraft structural Faraday Cage is presented which helps solve the EMI problem. Other system design techniques are also discussed which minimize the magnitude of these environments through control of materials and electrical grounding configuration.

15990

Lytle, W.J., and O.J. McAteer (Westinghouse Defense and Space Center, Baltimore, MD).

CHARACTERISTIC TRAITS OF SEMICONDUCTOR FAILURES.

IEEE - Annual Symposium on Reliability, February 3-5, 1970, Vol. 3, No. 1, pp. 386-393.

This paper discusses the relative importance of visual microscopic data as it pertains to recognizing the characteristic traits of semiconductor failures. This visual data can be a tremendous aid to the analyst in identifying the cause of semiconductor failure due to external influence. Residual damage observed on a microcircuit surface is often the result of temperature excursions localized at the chip surface. Temperature excursions that occur with certain types of damage to microcircuits are discussed in terms of voltage, current and time and are thereby related to the nature of the external abuse.

Also presented are case histories which describe the usefulness of these characteristic traits when applied during system failure analysis.

15991

Garrett, H.B. (Jet Propulsion Laboratory).

NEUTRALIZING CHARGED-UP SPACECRAFT.

IEEE - Spectrum, Vol. 19, No. 7, July 1981, pp. 44-47.

This article presents explanations by which spacecraft can get charged up by space

plasma, how this charge can cause malfunctions or failures, and ways this charge buildup can be controlled. It also presents a summary of the information obtained by the Scatha (spacecraft charging at high altitudes) satellite, flight P78-2.

15993

Beall, J.R. (Martin Marietta Corp., Denver, CO).
EBIC GENERATION, IMAGING AND TYPICAL APPLICATIONS.
Second Annual Microelectronics Measurement Technology Seminar Proceeding, 1980, 10 pp.

Electron Beam Induced Current (EBIC) is a practical technique for locating and imaging subsurface defects in semiconductors. It is also practical to perform physical measurements using EBIC. The generation processes of EBIC in semiconductors and the techniques for measurement and imaging are described. Although the generation processes and imaging techniques are relatively straightforward, detailed interpretation of EBIC data requires a familiarity with semiconductor construction and layout. Examples demonstrating typical EBIC applications are described.

15994

McAteer, O.J. (Westinghouse, Baltimore, MD).
A CLUE FROM COLUMBO.
Quality, December 1980, pp. 54-55.

This article shows that there is more to failure analysis than sophisticated lab techniques. It compares electronic failures to a murder mystery where the failed part is regarded as the analog of the murder victim.

15995

DeForest, S.E., and E.C. Whipple (University of California, La Jolla, CA).
SPECIFICATION OF THE NATURAL PLASMA ENVIRONMENT AT GEOSYNCHRONOUS ORBIT.
Rept. No. AFGL-TR-79-0060, Contract No. F19628-77-C-0014, December 10, 1978, 26 pp.

The use of UCSD plasma instruments on board the ATS spacecraft could be used to specify an environmental mode which would be of use to the Air Force in developing design specifications for spacecraft to prevent faulty operation due to environmentally induced electrostatic charging.

15998

Passow, R.A. (U.S. Air Force Institute of Technology, Wright-Patterson AFB, OH).
SPACECRAFT CHARGING.
Rept. No. AFIT-CNE-PH-78-19, AD/A064 754, December 1978, 104 pp.

If a spacecraft is exposed to a steady stream of current density, the charge of which is deposited on the surface of a cylindrical, conducting spacecraft, internal electromagnetic fields are generated. If the internal fields are of sufficient strength, undesirable electronic noise or damage may result. This thesis presents three approaches for calculating the induced E-field: separation of variables, variational calculus, and the use of Green's functions.

15999

Benaissa, B., L. Levy, A. Paillous, and D. Sarraill (ONERTA-CERT, Dept. of Studies & Research in Space Technology, France).
SATELLITE SPACECRAFT CHARGING CONTROL MATERIALS.
Rept. No. AFWAL-TR-80-4029, Contract No. AFOSR-78-3704, April 1980, 154 pp.

The feasibility of conductive adhesive techniques for the electrical interconnection of ITO-coated second surface mirrors has been studied. The good electrostatic performance and the durability of components combining ITO-coated aluminized Kapton and aluminum straps by means of silver loaded silicone have been confirmed by a prequalification program.

The charge dissipation mechanisms for silica fabrics in a geosynchronous magnetic substorm environment have been studied by means of various sample configurations that have been tested under electron beam. Some recommendations have been given for a better use of silica fabrics as thermal control coatings in space.

16014

Kinzig, B.J., and H. Ravner (U.S. Navy, Naval Research Laboratory, Washington, DC).
PROBLEMS ENCOUNTERED WITH ANTISTATIC PACKAGING.
NRL Memorandum Report 3873, November 1978, 20 pp.

Packaging of miniature aerospace components in antistatic polyethylene or nylon is generally considered an attractive route to eliminate major problems in their handling and storage. Although most electronic components appear compatible with antistatic packaging materials, lubricated parts, such as precision ball bearings, can apparently be adversely affected. Surfaces exposed to lubricants, for example, may become nonwetted or the lubricant may become grease-like after relatively short exposure to antistatic containers. That such packaging adversely affects lubricated parts suggests potential problems involving unwanted surface-active effects for nonlubricated parts as well.

Our recent studies indicate that the surfactant material incorporated into the packaging film may be responsible for the adverse effects observed.

16015

Gaspard, K.R., M. Shirk, and J. Sadlak (Honeywell, Avionics and Defense Systems). UNDERSTANDING AND CONTROLLING ELECTROSTATIC DISCHARGE. Component Comments, Rept. No. 175, February 13, 1978, 10 pp.

This component comment addresses the areas of comprehensive cost-effective methodologies for the control of electrostatic potentials. This component comment is organized as follows: Testing/Results, major concerns of Design (Reliability, Quality, Production services, and Procurement), Control Methods, and Conclusions. Voltage sensitivity ranges were Category I, 0-170v; Category II, 171-2000v; Category III, 2001 to 15000v; Category IV, 15001 and above.

16022

Dabkowski, J. (IIT Research Institute, Chicago, IL). INVESTIGATE FEASIBILITY OF ELECTROMAGNETIC PULSE TESTING FOR RELIABILITY SCREENING OF SEMICONDUCTOR DEVICES. Rept. No. E6443, November 1978, 50 pp.

Tests presently used for the screening of microelectronics are generally patterned after MIL-STD-883. In addition to the accepted screening tests, it has become apparent that an additional test procedure is necessary for some technologies. MIL-M-38510 incorporates a test requirement to qualify ESD protective circuitry on the CMOS chip.

EMP tests are primarily oriented towards establishing damage thresholds and failure criteria for semiconductors exposed to an electromagnetic pulse.

Due to thermal breakdown failure effects a commonality between accepted reliability screening tests and EMP tests can be shown to exist.

16055

Danley, L.W. (General Semiconductor Industries, Inc., Tempe, AZ). PARAMETER TRADE-OFFS IN HIGH-VOLTAGE HIGH-SPEED SWITCHING POWER TRANSISTORS. Third National Solid-State Power Conversion Conference, June 1976, 11 pp.

A continuing problem confronting the power supply designer is the selection of the "ideal" power transistor, one that provides not only high speed and high voltage but also good second breakdown capability, all within a

single part. Current device technology, however, imposes interactive restraints upon these parameters, forcing compromises that are less than the designer's ideal component.

This paper presents an examination of these interactive factors in terms that are both familiar and meaningful to the power supply designer, providing a practical and useful baseline for the knowledgeable specification of state-of-the-art devices.

16067

Pujol, H.L. (RCA, Solid State Division, Somerville, NJ). COS/MOS ELECTROSTATIC-DISCHARGE PROTECTION NETWORKS. Rept. No. ICAN-6572, February 1977, 4 pp.

RCA's two families of CMOS devices, the standard A series (3 to 15 volts) and the high voltage B series (3 to 20 volts), are equipped with networks to protect the gate oxide of the devices against damage resulting from discharge of electrostatic energy between any two pins. Figures show the various protection networks incorporated in all COS/MOS products.

16068

Albing, B. (Hickok Electrical Instrument Company, Cleveland, OH). COMPARATOR DETECTS POWER SUPPLY OVERVOLTAGES, CATCHES GLITCHES. Electronic Design, Vol. 27, No. 15, July 19, 1979, p. 120.

Power-supply outputs can be monitored for intermittent overvoltage conditions by a comparator circuit that will light LED's and sound a beeper whenever a transient occurs. The circuit can be modified easily to latch the LED and beeper continuously on. This allows the circuit to run without constant monitoring.

16069

Somsak, W. (Transaction Technology Inc., Los Angeles, CA). COPING WITH STATIC ELECTRICITY - PART XIII, ARE YOU ALSO A VICTIM OF ESD? Evaluation Engineering, Vol. 18, No. 4, July/August 1979, pp. 20-27.

This presentation will identify potential static problem areas within the working environment. The military hardware industry more than the commercial has taken great strides to educate its contractors on electrostatic discharge. The Navy has distributed two proposed documents for review.

16074

Anon. (Reliability Sciences, Inc., Arlington, VA).

ELECTROSTATIC DISCHARGE (ESD) LIBRARY LIST.
Rept. No. 428-0036-004, Contract No. N00197-79-C-0107, May 10, 1979, 64 pp.

This document is a library list of ESD articles prepared for the Naval Ship Engineering Center. The article gives library descriptors and separately categorizes articles relating to general information, device sensitivities, and ESD control/elimination.

16074-01

Anon. (Reliability Sciences, Inc., Arlington, VA).
IDENTIFICATION OF SUPPLIERS OF ESD PROTECTIVE MATERIALS AND EQUIPMENT.
Rept. No. 428-0036-002, Contract No. N00197-79-C-0107, May 11, 1979.

Sixty-two manufacturers are identified from various sources as potential suppliers of material and equipment for the protection of sensitive devices for electrostatic discharge. Supplies are categorized as antistatic plastic, conductive plastic, and equipment or tools.

16075

McDermott, J.
ZAP THE ZAPPER BEFORE IT ZAPS YOUR DESIGNS - IMPROVED ICS, PROTECTIVE COMPONENTS HELP.
EDN, Vol. 25, No. 16, September 5, 1980, pp. 59-64.

Electrostatic discharge can destroy ICs at all stages of equipment manufacture, including quality control checks, board stuffing and testing, and even in field maintenance. IC and component manufacturers have developed a variety of products and techniques to deal with this problem.

16076

Walker, R.C. (IITRI/RAC, Griffiss AFB, NY).
ELECTROSTATIC DAMAGE TO SEMICONDUCTORS.
Reliability Technology for Cardiac Pacemakers III - A Workshop Report, June 1979, pp. 69-73.

The Reliability Analysis Center (RAC) has found it convenient to classify ESD sensitive devices into three groups. These groupings should be considered generalizations, and it is cautioned that damage thresholds within generic classifications can vary widely. When in doubt, individual part types should be tested for sensitivity.

ESD-type overstress can induce latent failure mechanisms in both MOS structures and bipolar junctions which are not necessarily detectable with typical electrical tests. The overstress degrades the device, making it susceptible to failure some time after initial voltage transient in applications where voltage excursions are encountered.

16114

Pshaenich, A. (Motorola Semiconductor Products, Inc., Phoenix, AZ).
DRIVING INDUCTIVE LOADS?
Electronic Design, Vol. 25, No. 4, February 15, 1977, pp. 86-91.

Most monolithic Darlingtontons have a built in (C-E) diode that is usually ignored. This diode is capable of serving as a surge suppressor for inductive loads. Because the C-E diode is usually ignored its characteristics are seldom given in spec sheets. Measurements compare favorably with several discrete rectifiers.

Fast recovery rectifiers are characterized by low reverse-recovery times. They are not particularly fast on forward recovery. Moreover, when compared to standard or even fast recovery diodes, no major difference in circuit operation can be detected for C-E diodes as a result of variation in reverse-recovery times.

16115

Graham, G.W. (Atlas Chemical Industries, Inc., Chemicals Division).
PREDICTING THE STATIC BEHAVIOR OF FIBERS AND TESTING THE EFFECTIVENESS OF ANTISTATIC AGENTS.
Textile Chemical Bulletin, 1952, 4 pp.

The test procedure described here is designed to simulate the mechanism by which fibers become charged in actual mill operations. It is based on the theory that if a textile material cannot be charged with static electricity through friction against itself and certain other materials, static should be no problem.

16116

Taylor, R. (Litton Systems, Inc., Guidance and Control Systems Division, Woodland Hills, CA).
PHYSICS OF ELECTROSTATIC CHARGE GENERATION IN INDUSTRIAL PROCESSES.
Internal Report, 1970, 16 pp.

The manufacturing process areas discussed in this paper are conformal coating/potting, hybrid facility, areas using cryogenic coolants, vapor degreasers, ultraviolet light inspection, vacuum pack processing, and Parylene coating process.

The Helmholtz effect-layer theory, Hertz effect and Van der Waals forces are used to explain charge generation. Spraying and dip coating was found not to generate electric charges. Nonoven drying causes a charge of 40 volts due to Van der Waals forces. Assemblies cured in laminar flow ovens are subject to charges when not grounded. Cryogenic cooling will cause charge generation due to the accumulation of moisture on the part with the

effect of Van der Waals forces. Ultraviolet light exposure greater than 30 minutes will cause charge generation because of the Hertz effect. Charges up to 80 kilovolts can be generated when removing a polyethylene sheet from its packaging. Handling processes such as wiping with Kimwipe can cause generation of 500 volts.

16117

Clark, O.M. (General Semiconductor Industries, Inc., Tempe, AZ).
DEVICES AND METHODS FOR EMP TRANSIENT SUPPRESSION.
IEEE - Electromagnetic Compatibility Symposium, 75CH1002-5EMC, October 1975, 6 pp.

The subject of EMP (Electromagnetic Pulse) has been developed into prominence in recent years because of potential nuclear threat.

Although gas-filled spark gaps were originally designed to protect telephone apparatus from induced lightning surges they have exhibited fast turn-on characteristics when subjected to the much stronger EMP pulse. Response to laboratory simulated EMP pulses has shown that metal oxide varistors will also clamp fast rise time pulses but undergo reverse degradation upon multiple pulsing.

Both devices have been used for large system protection subject to respective limitations of short turn on times and high voltage clamping.

16118

Lane, C.H. (U.S. Air Force, Rome Air Development Center, Griffiss AFB, NY).
ELECTRICAL OVERSTRESS, "ZAP", FAILURES OF SILICON PN JUNCTIONS (U).
Job Order No. 55190000, Report No. RADCR/RC-TM-71-4, May 1971, 38 pp.

This study of electrical overstress reveals the cause of the failure and explains the appearance of a "zapped" junction. It demonstrates the dependence of long pulse type zap failures on aluminum alloying and migration.

16123

Halperin, S.A. (Analytical Chemical Laboratories, Elk Grove Village, IL).
COPING WITH STATIC ELECTRICITY-PART XIV, TOPICAL ANTISTATIC PRIMER.
Evaluation Engineering, Vol 18, No. 5, September/October 1979, pp. 56-62.

Topical antistats are generally liquids which, when applied, render a material static controlled. They consist basically of two components: 1) a carrier to transport the antistatic mechanism and 2) the mechanism which performs the preventive function.

A new approach to the static problem treats static as a symptom and environmental factors as the cause of it. It follows the thought that static is a natural phenomenon and to prevent it we must counteract the natural elements that create it.

16124

Shumka, A., E.L. Miller, and R.R. Piety (Jet Propulsion Laboratory, Pasadena, CA).
FAILURE MODES AND ANALYSIS TECHNIQUES FOR CMOS MICROCIRCUITS.
IEEE - Advance Technique Failure Analysis Symposium, Contract No. NAS 7-11, 1977, pp. 75-87.

The type of damage which is produced by ESD is a function of the part characteristics, voltage level and polarity energy available and the rise/fall time of the ESD pulse. After the part is soldered to the circuit board, the attached circuitry connectors and arrangement of exposed interconnections may greatly influence ESD susceptibility.

16142

Branberg, G. (Hewlett-Packard Co., Loveland, CO).
ELECTRO-STATIC DISCHARGE AND CMOS LOGIC.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 55-63.

This report describes a method of organizing and implementing a standardized test method for evaluating ESD susceptibility of CMOS components. Also described are methods for detecting mechanisms of latent failure and other related phenomenon. Procedures for decapsulation and electrical probing of the die are also presented as a method of isolating the cause of failure. As shown by the results, the phenomenon of ESD is controllable and its effects statistically predictable.

16143

Yenni, D.M., and J.R. Huntsman (3M Company, St. Paul, MN).
THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 45-54.

Military Specification MIL-B-81705 has been relied on to define static protective materials. Advancing technology has made its methods antiquated.

The single most important characteristic of any packaging material is its conductivity. To fully characterize a film as being static protective, all that is needed is a resistivity test. Existing ASTM test procedures can be used.

16144

McCullough, D.T., C.H. Lane, and R.A. Blore (U.S. Air Force, Rome Air Development Center, Griffiss AFB, NY).
RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 36-40.

A proposed electrical overstress (EOS) test method for MIL-STD-883, "Test Methods and Procedures for Microelectronics," was applied as a characterization and screening procedure to a population of gold doped 4002 CMOS devices. To evaluate the possibility of subsequent reliability degradation of devices passing the screen, a high temperature accelerated life test was performed on screened and unscreened devices. For screening, a voltage pulse of sufficient magnitude to fail about 3% of the parts was applied. No significant differences were detected between the failure rates of the screened and unscreened device populations.

16145

Madzy, T.M., and L.A. Price, II (IBM Corp., Systems Products Division, Endicott, NY).
MODULE ELECTROSTATIC DISCHARGE SIMULATOR.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 36-40.

Under certain conditions electrostatic discharge (ESD) can cause catastrophic failure in both bipolar and field effect transistor (FET) devices. This paper presents a test technique and describes a testing device that simulates ESD produced by human handling.

16146

McMahon, E.J., T.N. Bhar (Reliability Sciences, Inc. Arlington, VA) and T. Oishi (Naval Sea Systems Command, Washington, DC).
PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 27-35.

Many electrical and electronic devices and components are sensitive to Electrostatic Discharge (ESD). However, ESD controls generally have not been widely implemented by either industry or government. This lack of controls has resulted in increased costs, decreased equipment reliability and increased equipment downtime. To address these problems the Naval Sea Systems Command, under DOD Project Nos. RELI-014 and RELI-012 is developing a military standard and handbook on implementation of ESD control programs. Background, content and status of these documents are presented. Additionally, ESD areas requiring further work are discussed.

16147

DerMarderosian, A., and L. Rideout (Raytheon Co., Equipment Division, Sudbury, MA).
THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 22-26.

Sporadic electrical signal losses were noted during system qualification testing in a cyclic gaseous pressure/vacuum environment. There were electrical timing disturbances noted at depressurization.

A static charge hypothesis was developed that involved movement of the potting compound. During pressurization, gas bleeds into areas of poor adherence between the module frame and silicon encapsulant. During depressurization the entrapped gas will stress the potting, causing a separation at the bonded interface, thereby generating a charge.

16148

Halperin, S.A. (Analytical Chemical Laboratories, Elk Grove Village, IL).
STATIC CONTROL USING TOPICAL ANTISTATS.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 13-21.

Triboelectric static charges can be prevented by using properly selected topical antistats. Utilizing the concept of Environmental Static Control (ESC), the burden of a company's overall static control program can be shifted from the line employee to a management team made up of operations and maintenance personnel. If proper instrumentation is employed, constant performance feedback and detailed analysis are available. As a result, the optimal return in static prevention, at the lowest possible cost can be achieved.

16149

Storm, D.C. (Aerospace Corp., El Segundo, CA).
CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 4-6.

This paper discusses the sources of electrostatic discharge (ESD) and the detailed requirements for protecting electronic parts and assemblies that may be sensitive to ESD. The procedures could be employed on future space projects to ensure that proper safeguards are taken during manufacturing and testing to protect space flight hardware from ESD hazards.

16150

Briggs, C., Jr. (Charles Stark Draper Laboratory, Inc., Cambridge, MA).
ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH - TOP SURFACE MATERIALS.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 7-12.

Testing has been conducted at The Charles Stark Draper Laboratory, Inc. (CSDL) on several typical or potential bench-top materials. The tests consisted of charging bench-top samples and then discharging them to a ground. All samples exhibited an exponential decay of voltage with time. The only exceptions were vacuum-baked samples of melamine and Benalux-type materials. The author is also certain that pink poly would be an exception if it were vacuum baked. All samples produced a visible static discharge arc when the charged test specimen was grounded.

16151

Uetsuki, T., and S. Mitani (Hitachi, Ltd., Production Engineering Research Laboratory, 292 Yoshida-Machi, Totsuka-Ku, Yokohama 244, Japan).
FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 88-96.

The differential input pair transistors of an operational amplifier are susceptible to severe damage from EOS/ESD.

Typical failure modes of TTL IC's include degradation of the I-V characteristic or short of the input protection diode.

EOS/ESD can easily cause degradation of the electrical characteristics or catastrophic damage.

16152

King, W.M. (Electromagnetic Compatibility Advisor, Santa Monica, CA).
DYNAMIC WAVEFORM CHARACTERISTICS OF PERSONNEL ELECTROSTATIC DISCHARGE.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 78-87.

This paper briefly summarizes a study that was initiated to advance knowledge of Personnel Electrostatic Discharge (ESD) by developing descriptions of the "Source" waveforms resulting from the ESD of personnel associated with operation of Electronic Data Processing (EDP) systems. The study was extended to include measurements of the waveforms of ESD from (and through) mobile furnishings and the ESD of personnel through various handheld metallic objects that were intervening in the discharge path. The

conceptual direction of this effort was aimed toward eventual development of ESD test simulation equipment and methodology, based on matching the waveforms found during the primary "source" evaluation effort through to the design of the test simulation equipment. From the standpoint of systems susceptibility performance, the conclusions provided by this effort have achieved good correlation in terms of systems operation in active-use situations. Although directed toward systems-susceptibility considerations, the waveform results of this study could easily be applied to equivalent circuit models for purposes of evaluating semiconductor device/component ESD damage.

16153

Rutherford, D.H. (Raytheon Company, Electromagnetic Systems Division, Goleta, CA) and J. Perkins (Hi-Rel Laboratories, Inc., Monrovia, CA).
EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 64-77.

A large percentage of the microcircuits submitted for failure analysis that are actually defective have been found to be damaged by electrical overstress. It is not unusual to see 60 to 75% of actual failures the result of some sort of overstress conditions. Prior reports of failures of some digital microcircuits gives the impression that certain families of devices have different damage susceptibility levels. This paper describes a series of stress tests performed on several digital microcircuits and the failures that were induced. Procedures used for failure analysis of the damaged microcircuits are discussed.

16154

Madison, J.A. (Westinghouse Electric Corp., Baltimore, MD).
THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 205-209.

When performing failure analysis at the system or printed wiring board level for a high reliability program, any associated part that could have been overstressed is identified and removed. The procedure is summarized and the circuit analysis is illustrated by several examples. A summary of the secondary part type replacements and the related overstress characteristics are given. The procedure has been successful in preventing system level failures from this cause over a five-year period involving 300

printed circuit boards and 200 power supply assemblies that contain 10,000 multichip hybrid packages.

16155

Cabayan, H.S., F.J. Deadrick, L.C. Martin, and R.W. Mensing (Lawrence Livermore Laboratory, Livermore, CA).
STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 198-204.

A study of general problems of dealing with uncertainties and their impact on failure analysis in assessment of EMP effects on military systems has suggested a probabilistic approach. Major uncertainties arise in both the interaction and coupling and susceptibility phases of assessment studies. A probabilistic approach, as outlined in this paper, can accommodate all sources of uncertainties. Although propagation of uncertainties by analytical methods is possible for very simple systems, the approach suggested is based on Monte Carlo methods and uses available computer programs such as FAST and NET-2. The results of the two simple experiments demonstrate the validity of the tools used and shows the potential usefulness for more complex systems.

16156

Clark, O.M. (General Semiconductor Industries, Inc., Tempe, AZ).
ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 193-197.

The vulnerability of a semiconductor device increases as the slope of the transient voltage wavefront increases. The microstructures characteristic of new semiconductor technology are very fragile and are easily destroyed with the fast rise-time transients originating from electrostatic discharge (ESD). A new silicon transient suppressor structure has been developed specifically for clamping the fast rise-time of ESD and represents more than an order of magnitude improvement over conventional silicon suppressors. Effectiveness of both of these types of suppressors is evaluated and reported in this paper.

16157

Minear, R.L., and G.A. Dodson (Bell Telephone Laboratories, Reading, PA).
THE PHANTOM EMITTER - AN ESD - RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 188-192.

The immunity of an NPN IC transistor to ESD damage can be markedly improved by simple design changes. The resulting "phantom emitter" transistor used in bipolar op-amp circuits makes their inputs much more damage resistant. The "phantom emitter" diffusion is shorted to the normal base contact by metal and plays no part in normal device operation.

16158

Petrizio, C.J. (RCA Solid State Division, Somerville, NJ).
ELECTRICAL OVERSTRESS VERSUS DEVICE GEOMETRY.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 183-187.

Each section of a CMOS quad two-input NOR gate was independently stressed. The resulting failures can be related to device geometry. Review of the test data indicates excessive quiescent leakage (I_{SS}). The failures occurred farthest from the V_{SS} contact. The higher input diode resistance results in a higher voltage drop and increased dissipation. An additional P-well contact was proposed to reduce the voltage drop.

16159

Soden, J.M. (Sandia Laboratories, Albuquerque, NM).
THE DIELECTRIC STRENGTH OF SILICON DIOXIDE IN A CMOS TRANSISTOR STRUCTURE.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 176-182.

It is important to know if the processes required to fabricate the MOS device structure such as oxide etch and regrowth and topographical features such as edges and steps have significant effect upon the SiO_2 gate oxide maximum dielectric strength. Also important to know is how gate oxide defects in the MOS structure affect this maximum dielectric strength.

The primary breakdowns occurred at topographical edges at the gate/field oxide interface and the secondary distribution of breakdowns at random locations in the central region of the gate. The maximum dielectric strength in the primary distribution is within about .5MV/cm of that reported for uniform thickness SiO_2 in capacitor studies.

16160

Teng, T., A.R. Hart, and A. McKenna (Hewlett-Packard Co., Corvallis Division, Corvallis, OR).
SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 168-175.

An investigation of random failures during 125°C burn-in of LSI MOS Memory devices led to a study of the effects of elevated temperature on ESD susceptibility. An experiment was conducted on the ESD susceptibility versus temperature on MOS LSI devices including PMOS, NMOS, and CMOS devices produced by three IC manufacturers. A reduction in ESD failure voltage (V_f) is found at 125°C compared with room temperature levels. An explanation of bulk doped silicon resistivity variation in the input junction protection diode versus temperature combined with processing nonuniformities is offered and supported with a simplified power and current model and physical failure analysis.

This phenomenon affects high temperature testing used for life test, activation energy determination, receiving inspection, outgoing screening, Hi Rel and military specification testing and MOS applications in extreme temperature environments.

16161

Formanek, V.C. (IIT Research Institute, Chicago, IL).
DAMAGE RESPONSE OF SELECTED INTERFACE INTEGRATED CIRCUITS TO A SIMULATED EMP WAVEFORM.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 158-167.

The damaging effects of a 20 MHz damped sinusoid on 18 types of powered devices are presented. Failure levels are given in terms of peak currents and voltages. The three most sensitive devices are also modeled in terms of failure energy and failure modes are presented.

16174

Kusnezov, N., and J.S. Smith (Lockheed, Palo Alto Research Labs, Palo Alto, CA).
MODELING OF ELECTRICAL OVERSTRESS IN SILICON DEVICES.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 133-139.

This paper describes qualitative results of the work to date and is intended to show only general trends. A quantitative analysis of the junction burnout problem remains to be analyzed, and these results will appear in a later paper. The justification for going to more than a simple one-dimensional analysis is described. The extension of the 1-D to 2 or 3-D analysis is briefly explained and has been restricted to what has been learned from the viewpoint of power dissipation. Folding-in temperature effects serve generally to wash out the basic results that are best illustrated by studying the initial power dissipation.

16200

Baruah, A., and P.P. Budenstein (Auburn University, Auburn, AL).
AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF-SILICON-ON SAPPHIRE DIODES.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 126-132.

Second breakdown is generally regarded as one of the principal failure modes of silicon electronic components.

The susceptibility of a particular device to second breakdown depends upon device geometry, spacings, contours, doping levels and heat sinking. The filamentation process involves large currents in a small region of space in short intervals. In modeling the high current pulse effects on P-N junctions, there is an interval when devices are ballasted by the junction voltage; however, when the temperature of the junction becomes high enough the voltage drops precipitously and the filament evolves rapidly.

16201

Schnetker, T.R. (Gould Inc., OSD, Cleveland, OH).
HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 122-125.

The heart of an effective ESD control program is commitment to the program by production operators throughout the facility. The unseen nature of electrostatic damage makes it much more difficult to control than the usual quality defects. Consideration of small work group behavior in the design of electrostatic control programs will lead to real acceptance of electrostatic work rules.

16202

Blackburn, D.L., and D.W. Berning (National Bureau of Standards, Electron Devices Division, Washington, DC).
REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 116-121.

Second breakdown in bipolar transistors has been divided into two regimes, forward and reverse. The phenomenon of thermal instability and its relationship to forward bias second breakdown is well understood; the events preceding reverse bias second breakdown are not well understood. Data curves show that the voltage at which second breakdown occurs decreases as the reverse bias increases. This supports the theory that the

focusing of current to the center of the emitter fingers during turnoff is the mechanism that leads to reverse bias second breakdown.

16204

Whalen, J.J. (SUNY at Buffalo, Amherst, NY) and H. Domingos (Clarkson College of Technology, Potsdam, NY).
SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, 7 pp.

Square and RF pulse overstress data for bipolar UHF transistors are compared. For pulses incident upon the base-emitter terminals the pulses with lowest energy required to cause device failure were reverse polarity square pulses. The comparison indicates that a data format of absorbed pulse energy up to time of failure vs time to failure is well suited for comparing data produced by different types of signals.

16206

Ward, A.L. (Harry Diamond Laboratories, Adelphi, MD).
DOPING PROFILES AND SECOND BREAKDOWN.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 109-115.

With the understanding of second breakdown, one should be able to design devices less susceptible to burnout. The electrothermal computer program has been used to study second breakdown in linearly graded, double- and single-sided abrupt and diffused junction diodes. Tentative design principles are given.

16207

Anand, Y. (Microwave Associates, Inc., Burlington, MA) G. Morris, and V. Higgins (U.S. Army Electronics Technology and Device Laboratory, ERADCOM, Fort Monmouth, NJ).
ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 97-103.

A recently developed platinum-silicon Schottky barrier diode was found to be least sensitive to burnout by electrostatic discharge.

Electrostatically burned-out diodes from both natural and circuit simulation techniques exhibited failure points at the periphery of the diode junction similar to that observed for RF burnout depending on junction parameter. A strong correlation exists between electrostatic and RF burnout of Schottky barrier diodes.

16208

Moore, M.G. (Harris Semiconductor, Products Division, Melbourne, FL).
ESD SUSCEPTIBILITIES OF HIGH PERFORMANCE ANALOG INTEGRATED CIRCUITS.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 104-108.

The operational amplifier, sample hold amplifier and comparator all share a similar input stage configuration - the bipolar differential input stage. If we apply an ESD pulse to either the inverting or non-inverting input with the other grounded, then there is a conduction path involving both a forward and reverse biased P-N junction.

A second classification of analog circuits is CMOS analog switches and multiplexers. Degradation may occur in three areas: switch cell; address cell; and decode. Switch cell degradation can be both MOS dielectric and P-N junction damage that may result in input-output off state isolation degradation as a result of PN junction damage or solid DC voltages and switching waveforms, depending upon damage location in the MOS dielectric. The address cell is susceptible only to MOS dielectric structure damage destroying the input MOSFET gate. The decode degradation, though an internal circuit structure because of small geometry MOSFETs, can be compromised through the capacitive divider model.

16213

Clark, O.M. (General Semiconductor Industries, Inc., Tempe, AZ).
EMP TRANSIENT SUPPRESSION.
Nuclear EMP, PEM-31, August 1974, 22 pp.

TransZorbs T.M. have been proven to be effective in suppressing fast rise-times, EMP type transients. Small in size, having sub-nanosecond response times and with current handling capabilities at levels of more than 500 amperes, TransZorbs have been found to be suitable in many transient protection applications. This paper describes what TransZorbs are, how they work, and how to employ them for EMP protection. Results of pulse testing are given, along with a description of capacitance effects and means to reduce these effects. Various hybrid schemes in which TransZorbs are used in conjunction with other types of protective devices are also discussed.

16226

Biddle, J.G. (Hughes Aircraft Company).
AIR IONIZING GRIDS - A COMPARATIVE ANALYSIS.
Internal Report, October 19, 1979, 6 pp.

Tests on air ionizing grids were conducted to determine which grids would

reduce to less than 100v a static charge of 15kv. The companies that submitted their products to independent testing were Scientific Enterprises, Static Inc., Simco and Westcorp. The laminar flow hood used in the experiment was a vertical down flow type made by Dexon Corp.

16247

Williams, R.L., Jr. (Harry Diamond Laboratories, Adelphi, MD).
TEST PROCEDURES FOR EVALUATING TERMINAL PROTECTION DEVICES USED IN EMP APPLICATIONS.
Rept. No. HDL-TR-1709, AD-A019-098, June 1975, 86 pp.

Certain commercially available components have been tested to establish test procedures for characterizing terminal protection devices used in electromagnetic-pulse (EMP) applications. The devices tested include spark gaps, filters, avalanche diodes, and various other nonlinear components. Response time and energy leak were recorded for each test. Insertion loss and approximate failure level were measured for each device. Results are presented in tabular form. The devices that appear suitable for terminal protection include spark gaps, some filters, and some semiconductor devices with breakdown voltage less than 50.

16267

Kahn, S.R. (IIT Research Institute, Chicago, IL).
EFFECTS OF EMP TESTING ON SEMICONDUCTOR LONG TERM RELIABILITY.
Rept. No. DNA 4468F, Contract No. DNA 001-76-C-0243, NWED Subtask R99QAXE8097-61, November 1977, 80 pp.

The objective of this report was to determine the effects of stressing semiconductor devices with EMP-like transients. The effects of EMP stressing on the devices was assessed by comparing the observed failure rates of the various samples under these accelerated life test conditions.

16285

Cooke, J.L., D.E. Duncan, J.J. Schawarz, and L.H. Skinner (Boeing Aerospace Company, Seattle, WA and BDM Corporation, Albuquerque, NM).
USERS MANUAL FOR SUPERSAP 2.
Rept. No. AFWL-TR-75-70, Contract No. F29601-74-C-0008, D224-13047-2; BDM/A-120-74-TRR1, March 1976, 208 pp.

This report presents user information for the computer code Supersap 2. Supersap 2 is a data storage and retrieval program. It is designed to manipulate data from two large

data bases in support of EMP susceptibility threshold analysis. The component data base contains data on approximately 86,000 electronic component types. The system description data base is user defined. Supersap 2 uses a command language to provide user control of a variety of data manipulations.

16302

McAteer, O.J. (Westinghouse Electric Corporation, Baltimore, MD).
AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 1-3, and Sept. 1980, RAC Catalogue No. EOS-2, pp. 189-191.

The need for electrostatic discharge (ESD) awareness on the part of personnel at typical electronic manufacturing facilities is described. Some of the underlying reasons for intuitive disbelief in the static problem are discussed as well as the consequences of nonawareness. The development of an effective training program and proper manner of delivery to the appropriate personnel is presented.

16313

Rose, S.E. (Honeywell, Inc., San Diego, CA).
STATIC ELECTRICITY CAN CAUSE BIPOLAR IC FAILURES.
Evaluation Engineering, Vol. 10, No. 3, May/June 1971, pp. 21-24.

This article indicates that bipolar devices can be damaged by static electricity. The three basic failure characteristics of TTL gates subjected to electrostatic discharge are base-emitter junction shorts, partial oxide passivation layer breakdowns resulting in high leakage currents, and open metallization.

16314

Berbeco, G.R. (Charleswater Products, Inc., Needham, MA).
STATIC PROTECTION IN ELECTRONICS MANUFACTURING.
Electronic Packaging and Production, Vol. 20, No. 7, July 1980, pp. 148-158.

An effective static protection program includes setting up a static protection system, employee education and awareness, and regular monitoring of work areas. This article presents an overview of static generation, dissipation, and protection methods.

16330

Clark, O.M. (General Semiconductor Industries, Inc., Tempe, AZ).
VOLTAGE CLAMPING LEVELS FOR SEVERAL TRANSZORB TRANSIENT SUPPRESSION DEVICES.
Nuclear EMP, PEM-33, March 1975, 6 pp.

Voltage clamping levels for the 1N5629A, 1N5545A, 1N5654A, and 1N5664A TransZorbTM silicon transient-suppression devices in a DO-13 package are presented as data in photographs of test waveform. A graph is compiled which illustrates the clamping voltage at a time point of 80nsec for each of the devices. The duration of the test pulse was 250nsec with a slope of 4KV per nsec for the rise portion. Clamping levels are nearly constant for test current amplitudes for up to 120A.

16376

Adair, R.P. (Unitrode Corporation).
TRANSIENT-VOLTAGE SUPPRESSORS SUIT PC-BOARD PROTECTION NEEDS.
EDN, Vol. 24, No. 15, August 20, 1979, pp. 105-109.

When transient voltages occur, system voltages and currents can surge to levels many times greater than their steady state values, permanently damaging semiconductor components. Zener transient-voltage suppressors offer a simple inexpensive method of shunting aside these transients before they reach sensitive components.

16377

Formanek, V.C., and I.N. Mindel (IIT Research Institute, Chicago, IL).
EMP TO ESD VZAP DATA CONVERSION AND CONSIDERATIONS.
1979, 30 pp.

The physical damage mechanisms for ESD and EMP are basically the same. The principal differences are the voltage source and coupling mechanism resulting in different driving voltage waveforms and source impedances.

The principal objective of this report is to find common or equating parameters between EOS and ESD.

16378

Myers, S. (Honeywell, Aerospace Division, St. Petersburg, FL).
A TOTAL APPROACH TO ELECTROSTATIC PROTECTION IN THE PRODUCTION ENVIRONMENT.
1977 Packaging, Handling, and Transportability Division, American Defense Preparedness Association, 16 pp.

Static electricity can never be eliminated but it can be controlled. Today electronic environment demands that each and every packaging engineer accept his responsibility to see that electrostatic discharge is properly addressed.

This article provides information that will aid him in meeting this responsibility.

16379

Huntsman, J.R. (3M Static Control Systems, St. Paul, MN).
SELECTED REFERENCES TO THE THEORY AND EXPERIMENT OF STATIC ELECTRICITY AND ELECTROSTATIC DAMAGE TO ELECTRONIC DEVICES.
November 1979, 16 pp.

This is a list of references compiled by 3M Static Control Systems relating to the theory and experiment of static electricity.

16438

Gaspard, K.R. (Honeywell, Inc.).
ELECTROSTATIC DISCHARGE (ESD) STUDY.
Report No. 0132-74-1008, Contract No. N00123-73-C-0132, April 1975, 56 pp.

This report documents the results of a study to develop an ordnance document which defines: electrostatic discharge sensitive parts; requirements for handling, shipping, storage, and testing of these parts; and methods to assure conformance to the requirements. Included in this report is the completed document written in military standard format along with back-up information discussing electrostatic discharge theory and applications and the categorization of purchased parts into four major electrostatic discharge sensitivity levels.

16475

Sankar, A., and T.S. Lin (TRW Systems Group, Redondo Beach, CA).
GENERALIZED ELECTROMAGNETIC VULNERABILITY PROBLEMS.
IEEE - First Symposium and Technical Exhibition on Electromagnetic Compatibility, Catalogue No. 75CH1012-MONT, 1975, pp. 264-269.

This paper has three purposes. The first is to propose a thesis that a system approach is needed to solve any electromagnetic vulnerability (EMV) problem in a comprehensive manner. The second is to present a generalized analysis approach to assist the system designer to optimize system and equipment performance through EMV analysis and control. The third is to enumerate and highlight the basic similarities and differences among the various available and applicable engineering "fixes" and design practices to solve EMV problems.

16476

Madzy, T.M. (IBM Corp., System Products Division, Endicott, NY).
STATIC DISCHARGE MODELING TECHNIQUES FOR EVALUATION OF INTEGRATED (FET) CIRCUIT DESTRUCTION.

IEEE - First Symposium and Technical Exhibition on Electromagnetic Compatibility, Catalogue No. 75CH1012-4MONT, 1975, pp. 134-139.

Under certain environmental conditions, electrostatic discharge can cause catastrophic failure in both bipolar and FET integrated circuits. This paper presents a technique to test FET devices using a simulated human static discharge and also presents a mathematical model that can predict a catastrophic failure as a function of voltage developed across the FET device and the energy dissipated. Both theoretical and experimental data are presented.

16477

Clark, O.M. (General Semiconductor Industries, Inc., Tempe, AZ).
SUPPRESSION OF FAST RISE-TIME TRANSIENTS.
IEEE - First Symposium and Technical Exhibition on Electromagnetic Compatibility, Catalogue No. 75CH1012-4MONT, 1975, pp. 66-71.

Highly specialized silicon pn junction devices have been developed for suppressing fast rise-time transients associated with induced lightning and EMP. Methods for low inductance insertion and techniques for effective reduction of capacitance will be both illustrated and discussed in this paper. Hybrid technology using the best qualities and both gas-filled spark gaps and silicon junction devices will be characterized including applications, capabilities and limitations.

16478

Clark, O.M. (General Semiconductor Industries, Inc., Tempe, AZ).
SUPPRESSING TRANSIENT VOLTAGES TO FCC 19528, PART 68.
Transzorb Application Note #106, August 18, 1978, 5 pp.

This application note is intended to provide background information and design criteria for combining TransZorbs and gas surge arresters for protection of telecommunication equipment against harmful transient voltage effects as described in FCC Docket 19528, Part 68.

16486

Clark, O.M. (General Semiconductor Industries, Inc., Tempe, AZ).
A GUIDE FOR TRANSIENT SUPPRESSION USING TRANSZORB.
1978, 58 pp.

This paper discusses the nature of transient voltages; protective measures and their effectiveness, along with some specific applications unique to the TransZorb.

16487

Clark, O.M. (General Semiconductor Industries, Inc., Tempe, AZ).
EMP TRANSIENT SUPPRESSION USING SILICON AVALANCHE SUPPRESSORS.
DNA/IITRI Sponsored Seminar at Eglin AFB, October 1977, 18 pp.

Electromagnetic pulse (EMP) as generated by an exoatmospheric nuclear detonation is characterized by an extremely fast rise-time pulse. MOS circuits and small area geometry semiconductors are particularly vulnerable to the fast rise-time transients of EMP origin. CMOS devices are quite sensitive and destruct at energy levels below 100 microjoules. Because of the potential severe threat to sensitive electronic components and equipment by EMP transients, effective suppression techniques and protective devices must be employed which are specifically designed to provide adequate protection from this destructive fast rise-time transient exposure. This paper discusses devices and methodology which are intended to serve as guidelines and to offer some alternatives to be considered in designing EMP transient suppression into electronic equipment.

16488

Clark, O.M. (General Semiconductor Industries, Inc., Tempe, AZ).
LONG-TERM PULSE LIFE AND DESIGN CRITERIA FOR TRANSZORB TRANSIENT VOLTAGE SUPPRESSORS.
NASA Contract Nos. NAS8-30811 and NAS8-31547, April 1, 1979, 14 pp.

This is a summary of final reports on the long-term reliability of TransZorb under actual pulse test conditions. From the extensive data gathered in this study, meaningful reliability curves were developed to guide the engineer in optimizing component use for circuit protection and maximizing the long-term reliability criteria of the TransZorb.

16489

Chen, C.L. (Purdue University, School of Electrical Engineering, West Lafayette, IN).
TRANSIENT PROTECTION DEVICES.
IEEE - Electromagnetic Compatibility Symposium, Catalogue No. 75CH1002-5EMC, 1975, pp. 3A1a1-3A1a3.

More solid-state diodes, transistors and integrated circuit components are used in control, communication and avionic equipment. These solid-state components are highly susceptible to lightning surges or other forms of electromagnetic disturbances. This paper reviews and compares the operation and characteristics of various transient protectors with particular emphasis placed on the

protectors suitable for the protection of low-voltage solid-state components.

16490

Huddleston, G.K., and G.G. Bush (Georgia Institute of Technology, School of Electrical Engineering, Atlanta, GA).
LIGHTNING PROTECTION FOR STATUS AND CONTROL LINES OF THE MARK III INSTRUMENT LANDING SYSTEM.

IEEE - Electromagnetic Compatibility Symposium, Catalogue No. 75CH1002-5EMC, 1975, pp. 3AIb1-3AIb3.

Solid-state circuits connected to buried control cables are susceptible to damage from surges induced on the cable conductors by lightning and electromagnetic pulse. The lightning protection requirements for solid-state circuits of the Mark III Instrument Landing System which are connected to buried control cables are presented in this paper.

16491

Vance, E.F. (Stanford Research Institute, Menlo Park, CA).
EMP-INDUCED TRANSIENTS IN LONG CABLES.

IEEE - Electromagnetic Compatibility Symposium, Catalogue No. 75CH1002-5EMC, 1975, pp. 3AI1a1-3AI1a6.

Sensitivity of modern components and circuit-design techniques to transient upset or damage is increasing. For this reason it is important that the system designer recognize the potential problems of transients induced on power, communication, and other long interconnecting cables. This paper discusses the currents induced in such cables by high-altitude nuclear EMP and suggests some protective measures that may be used by the circuit designer.

16493

Brundrett, G.W. (Electricity Council Research Centre, Chester, CH16ES, Gt. Britain).
A REVIEW OF THE FACTORS INFLUENCING ELECTROSTATIC SHOCKS IN OFFICES.
Journal of Electrostatics, 2(1976/1977), March 21, 1977, pp. 295-315.

This article deals with personal electrical parameters and the effect of electrostatic buildup with the wearing of different clothing. It also covers the capacitance and personal sensitivity to shock difference between men and women, physical generation factors of material and the effect of weather. It also identifies the choice of solutions now available to the designer.

16502

Martin, L.C. (Lawrence Livermore Laboratory, University of California, Livermore, CA).

COMPARATIVE EMP DESIGN PRACTICES.

IEEE - Electromagnetic Compatibility Symposium, Catalogue No. 75CH1002-5EMC, 1975, pp. 3AI1c1-3AI1c5.

The nuclear electromagnetic pulse creates potentially severe problems in hardening against electromagnetic effects. Each hardening effort is usually supported through development or application of sets of rules, practices, constraints, etc., which aid in decision-making through the design process. This paper addresses the nature of many such practices and provides specific comparisons for a number of them taken from several relatively independent sources.

16504

Van Keuren, E. (RCA Government Communications and Automated Systems Division, Camden, NJ).

EFFECTS OF EMP INDUCED TRANSIENTS ON INTEGRATED CIRCUITS.

IEEE - Electromagnetic Compatibility Symposium, Catalogue No. 75CH1002-5EMC, 1975, pp. 3AI1e1-3AI1e5.

This paper presents the results of testing by RCA of fourteen types of integrated circuits to determine their short pulse failure threshold. The primary intent of the tests was to determine for each circuit what would be the lowest amplitude of pulse which would cause permanent damage and prevent the circuit from operating. For these tests it was preferred that the actual devices and the circuits in which they are employed be measured. Pulses used during the tests ranged from 25 ns to 20 us, with emphasis on the range below 1 us.

16505

Latorre, V.R., and L.R. Spogen, Jr. (University of California, Lawrence Livermore Laboratory, Livermore, CA).

INGREDIENTS OF PROTECTION ENGINEERING.

IEEE - First Symposium and Technical Exhibition on Electromagnetic Compatibility, Catalogue No. 75CH1012-4MONT, 1975, pp. 407-412.

A basic protection engineering concept is developed for the protection of an electronic/electrical system from an electromagnetic environment. The concept is general and therefore applicable to many systems. It consists of five stages. A detailed discussion of all functions performed in each

stage is described, the input data to these functions identified, and, means by which the functional operations are satisfied are summarized.

16506

Van Keuren, E., R. Hendrickson, and R. Magyarics (RCA Government Communications and Automated Systems Division, Camden, NJ). CIRCUIT FAILURE THRESHOLD DUE TO TRANSIENT INDUCED STRESSES. IEEE - First Symposium and Technical Exhibition on Electromagnetic Compatibility, Catalogue No. 75CH1012-4MONT, 1975, pp. 500-505.

Presented in this paper are the testing results by RCA of various types of integrated circuits to determine their short pulse failure thresholds. The circuits investigated are interface ICs, which are prone to damage by transient pulses coupled into cables electrically connected to the IC.

16507

Anon. COPING WITH STATIC ELECTRICITY - PART XVI, ESD CONTROL DOCUMENTS BEING READIED. Evaluation Engineering, Vol. 19, No. 1, January/February 1980, pp. 72-74.

ESD controls have not been widely implemented by either industry or government. This lack of control has resulted in increased cost, decreased equipment reliability and increased equipment downtime. The Naval Sea Systems Command has developed MIL-STD-1686 and MIL-HDBK-263 for implementing ESD control programs. This article is abstracted from a background-and-status report on the MIL-STD and MIL-HDBK prepared by E.J. McMahon and T.N. Bhar, Reliability Sciences, Inc., and Toshio Oishi of the Naval Sea Systems Command. ESD areas requiring further work are also discussed.

16555

Mardiguian, A.E. (U.S. Air Force Weapons Laboratory, Kirtland AFB, NM). MICROCRACKS AND METALLIZATION BURNOUT. AFWL-TR-78-92, September 1979, 88 pp.

This report describes the work done to determine the extent to which the reliability of integrated circuits suffers when those integrated circuits contain small cracks (microcracks) in their metallization. It was hypothesized that microcracked devices would undergo metallization at lower current pulses than unmicrocracked devices. The microcracked devices in this study did not suffer metallization burnout (MBO) at a level significantly different from the uncracked devices.

16564

Mykkanen, C.F. (Honeywell Defense Systems Division, Hopkins, MN). COPING WITH STATIC ELECTRICITY-PART XVII, SPECIAL REPORT ON ESD CONTROL PRODUCTS. Evaluation Engineering, Vol. 19, No. 2, March/April 1980, pp. 42-44.

This article consists of Honeywell Defense Systems Division's results from several studies on ESD control products. It also recommends some solutions to the problems that were encountered and suggests where and when the products should be used.

16565

Thiede, G.D. (General Dynamics, Convair Division). SUSCEPTIBLE SEMICONDUCTOR DEVICES, PREVENTION OF SURGE CURRENT DAMAGE TO - PROCESS SPECIFICATION FOR. Contract No. NAS3-13514, Specification No. 0-73543, Code Identification No. 14170, March 19, 1974, 10 pp.

This specification describes procedures that are to be used when handling and packaging semiconductor devices that have been identified as being susceptible to surge current damage.

16632

Eagles, A.E., L.J. Amore, and V.J. Belanger (General Electric Space Division, Philadelphia, PA). SPACECRAFT STATIC CHARGE CONTROL MATERIALS. Rept. No. AFML-TR-77-105, Part I, Contract No. F33615-76-C-5075, AD/B024 315, June 1977, 70 pp. Distribution limited to U.S. Government agencies only.

A description of the design, development, fabrication and testing of transparent conductive coatings and conductive lattices deposited or formed on high resistivity spacecraft dielectric materials to obtain controlled static charge buildup on spacecraft external surfaces is presented. Through development of sputtering techniques and thin film evaporation methods, FEP Teflon and Kapton have been successfully modified to eliminate discharges on surfaces as a result of being exposed to electron beam energies of 25 KeV and a current density of 30 nA/cm². Processing methods have been described for indium oxide and indium oxide/tin oxide coatings on FEP and Kapton, and fabrication techniques for grounding techniques are discussed.

16633

Eagles, A.E., R.E. Schmidt, and L.J. Amore (General Electric Space Division, Philadelphia, PA).
TRANSPARENT ANTISTATIC SATELLITE MATERIALS.
Report No. AFML-TR-77-174, Part I, Contract No. F33615-76-C-5258, AD/B027 345, October 1977, 76 pp.
Distribution limited to U.S. Government agencies only.

The charging and subsequent discharging of high surface charges which are generated on non-conductive satellite surfaces have been identified as one of the chief causes of spurious performance of Air Force satellites. These discharges can cause upsets in the electronics systems which disrupt the normal functioning and data transmission of the satellite. A description is presented of the development, fabrication and testing of transparent conductive coatings deposited on the spacecraft and modifications to high resistivity transparent spacecraft dielectric materials to obtain control of static charge buildup on the spacecraft external surfaces.

16634

Tompkins, J.E. (Harry Diamond Laboratories, Adelphi, MD).
SOME SYSTEM-INTERACTION EFFECTS OF NEUTRONS IN THE SOURCE REGION.
Rept. No. HDL-TM-80-19, Control No. 1L162120AH25, AD/B049 055, June 1980, 20 pp.

Estimates are made of the emission and resulting Compton currents, air conductivities, and electric fields produced by high-energy neutrons from a nearby nuclear detonation incident on an iron plate. Results for 14-MeV neutrons indicate that appreciable Compton current and electric field are generated in the immediate vicinity of an iron plate due to the neutrongamma reaction process. The magnitudes of the electric fields are such that the phenomena should be considered when assessing the survivability of armored-vehicle mounted military communications equipment.

16669

Carlson, H.R. (U.S. Army, Armament Research and Development Command, Aberdeen Proving Ground, MD).
CLOUD PHYSICS REVISITED.
May 1981, 11 pp.

The approach taken in the paper is to present cloud physics theory as it is now understood from work carried out in the Chemical System Laboratory over the past 15 years. Experimental data then are presented with appropriate literature references, to

show that the agreement between experiment and theory is so good that little room is left for traditional interpretations of certain phenomena.

16683

Anon. (U.S. Navy, NAVSEA, Washington, DC).
ELECTROSTATIC DISCHARGE TRAINING MANUAL.
Rept. No. NAVSEA SE003-AA-TRN-010, September 1980, 204 pp.

Many electronic parts are susceptible to damage from electrostatic discharge (ESD). ESD control programs are required to protect these parts during manufacture, assembly, test, repair/rework, maintenance, and other handling operations. Such control programs must be implemented throughout the life cycle of these electronic parts. The intent of this training manual is to complement an ESD Awareness Training Course, which is a key part of any effective ESD control program.

16692

*Rupe, B.I. (U.S. Navy, Naval Avionics Center, Indianapolis, IN).
NONDESTRUCTIVE TESTING FOR SURFACE RESISTIVITY.
July 15, 1981, 7 pp.; also in Evaluation Engineering, January/February 1982, pp. 84-88.

This paper describes a test adapter designed in accordance with formulas stated in ANSI/ASTM D257 for determining the surface resistivities of materials using the concentric ring contact method. "Fringing" effects are virtually eliminated and calculations are reduced to an $\times 10$ multiplication factor. Problems of electrical contact with slightly uneven hard surfaces are solved by the mechanical properties.

*Presently employed by the Reliability Analysis Center, Griffiss AFB, NY.

16693

Marhefka, M. (Shell Container Systems, Ambler, PA).
COPING WITH STATIC ELECTRICITY - PART XXIV, AN INEXPENSIVE FIXTURE DESIGN FOR MONITORING SURFACE RESISTIVITY.
Evaluation Engineering, July/August 1981, pp. 28-32.

This paper presents a fixture design that can be used to measure the surface resistivity of static control materials. The fixture is inexpensive to fabricate, utilizes readily available materials and common fabrication techniques, and can monitor the surface resistivity of a variety of material configurations.

16694

Mykkanen, C.F. (Honeywell Defense Systems Division, Hopkins, MN).
WHAT DOES IT TAKE TO TURN YOU ON WITH ESD CONTROL.
Evaluation Engineering, July/August 1981, pp. 34-36.

This article is a talk that was given by C. Fred Mykkanen to the Naval Combat Systems Office in Pearl Harbor, Hawaii, as part of a formal ESD presentation made by C. Fred Mykkanen and Roy C. Walker (Reliability Analysis Center). It is a "pep talk" to motivate an audience to protect their ESD-sensitive components.

16695

Weigl, J.W.
ANTISTATIC FOOTWEAR.
September 20, 1980, 9 pp.

This article consists of a non-confidential disclosure of the technology of antistatic shoes, shoe soles and heels. John W. Weigl's patent for the antistatic footwear is also included.

16696

Teslenko, L. (Solid State Scientific, Montgomery, PA).
IMPROVING CMOS INPUT PROTECTION.
20 pp.

This report presents the results of an investigation which was launched to determine how much energy could be capacitively discharged into CMOS input protection circuitry before device failure occurred. An analysis was made to determine what mechanism had degraded which component of the input network. Several layout designs were considered, and simplified equivalent circuit models were drawn and characterized. The resultant information was then used to propose design guidelines and methods of improving input ruggedness and reliability. A topological layout was derived for recommended use in future CMOS integrated circuits.

16697

Frank, D.E. (McDonnell Douglas).
THE MYTHS AND REALITIES OF ELECTROSTATIC DISCHARGE.
Douglas Service, Vol. 37, November/December 1980, pp. 22-28.

This article discusses misconceptions about electrostatic discharge that are cause for alarm. It is hoped that this article has taken a step towards convincing the reader that ESD is real and will surely continue to become a more significant problem unless the necessary precautions are taken.

16833

Whalen, J.J., M.L. Thorn, E. Rastefano (State University of NY at Buffalo, Amherst, NY) and M.C. Calactera (Air Force Avionics Laboratory, Wright Patterson AFB, Dayton, OH).
MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS.
IITRI - EOS/ESD Symposium Proceedings, Sept. 1979, RAC Catalogue No. EOS-1, pp. 147-157.

Two dominant failure modes in overstressed MESFET's have been observed. One is the gate-to-source low resistance path (5 to 25 ohms) which frequently is correlated with metal migration (mainly gold) from the source metallization to the gate metallization. This failure mode was dominant when MESFET's failed at lower power levels as at 10 nsec. The other dominant failure mode is either a reduction in I_{DSS} or a drain-to-source short which is correlated with massive damage in the channel region between source and gate metallizations. This failure mode was dominant when MESFET's failed at this power levels as at 1.5 nsec.

16947

Ochoa, A., and P.V. Dressendorfer (Sandia National Laboratories, Albuquerque, NM).
A DISCUSSION OF THE ROLE OF DISTRIBUTED EFFECTS IN LATCH-UP.
IEEE - 18th Annual Conference on Nuclear and Space Radiation Effects, July 20-24, 1981, 9 pp.

Latch-up in monolithic integrated circuits is caused by the activation of four-layer SCR paths in certain technologies. A lumped element cross-coupled bipolar model has been widely used to discuss this parasitic SCR action with reasonable success. In the push toward VLSI structures, latch-up modeling and prediction based upon the simple model has proven inadequate. The deviations can be explained by an extension of the model into a network that couples parallel paths and by ensuring that measured parameters for the model reflect those of the latch-up situation. This paper discusses these points to allow the continued use of the lumped model in latch-up studies.

16948

Anon.
ESD-CONTROL STILL IN INFANCY - BUT GROWING.
Evaluation Engineering, Vol. 20, No. 5, September/October 1981, pp. 104-124.

Electronic device manufacturers are still unaware as to how serious ESD damage can be, and many who are aware are unwilling to spend what it costs to develop adequate ESD-control programs. This is the opinion of almost five dozen companies across the country involved in

manufacturing ESD-control products or providing ESD-related services.

16949

Stultz, T.J., J.L. Crowley (Lockheed Palo Alto Research Laboratories, Palo Alto, CA) and M.R. Hartoog (NCA Corp., Sunnyvale, CA).
COMPUTER-AIDED LATCHUP ANALYSIS OF INTEGRATED CIRCUITS.
IEEE - 18th Annual Conference on Nuclear and Space Radiation Effects, July 20-24, 1981, 11 pp.

A computer-aided procedure for performing integrated circuit latch-up analyzer is presented. The procedure is the result of merging a computerized integrated circuit design rule checking system with latch-up preventative design rules. The procedure was applied to an IC which was previously analyzed by hand. The results were exactly the same, except that it only took 4 hours with the computer-aided approach and 80 hours with the manual procedure. Also discussed are plans for additional improvements to the system.

16950

Pease, R.L. (Mission Research Corp., Albuquerque, NM).
LATCH-UP IN BIPOLAR LSI DEVICES.
IEEE - 18th Annual Conference on Nuclear and Space Radiation Effects, July 20-24, 1981, 36 pp.

Four-layer latch-up is a phenomenon which can occur in integrated circuits because of the presence of parasitic pnpn paths which if properly biased may be triggered "on" by ionizing radiation. This can prevent the operation of the circuit until the power supply bias is reduced to a value low enough to break the latch.

This paper presents a latch-up analysis procedure for four-layer (pnpn) latch-up and applies it to specific bipolar LSI devices which represent several current bipolar LSI technologies. The results of the analysis were verified by radiation tests.

16951

Dressendorfer, P.V., and A. Ochoa (Sandia National Laboratories, Albuquerque, NM).
AN ANALYSIS OF THE MODES OF OPERATION OF PARASITIC SCR's.
IEEE - 18th Annual Conference on Nuclear and Space Radiation Effects, July 20-24, 1981, 14 pp.

Four-layer parasitic SCR paths exist in bulk CMOS integrated circuits which can be activated by transient ionizing radiation, by overvoltage stress, and by other means causing latch-up. These parasitic SCRs often have

characteristics which are not explained by simple SCR theory. This paper analyses a cross-coupled transistor model to explain how these characteristics can occur in parasitic four-layer paths.

16955

Berry, J.E. (Burroughs Corp., Office Systems Group, Camarillo, CA).
STATIC CONTROL IN BARE BOARD TESTING.
Electronic Packaging and Production, Vol. 21, No. 08, August 1981, pp. 161-162.

The need to control static in electronic assemblies is gaining recognition in the industry. Yet many test engineers are not aware that electrostatic discharge (ESD) can wreak havoc during testing a multilayer bare board. This article describes an experience which demonstrates that ESD problems can occur in the unlikeliest places. It also gives corrective actions that may be taken to control ESD problems in those places.

16961

Denson, W.K., and R.C. Walker (Reliability Analysis Center, Griffiss AFB, NY).
ESD SENSITIVITY IDENTIFICATION MARKINGS ON HARDWARE.
Rept. No. 00711-20-1, Contract No. F30602-78-C-0281, June 15, 1981.

The objective of this study is to recommend hardware marking guidelines to be incorporated into DOD-HDBK-263 (excluding Electrically Initiated Explosive Devices), dated 2 May 1980. The present issue of DOD-HDBK-263 provides limited guidance in marking hardware.

17013

Storm, D.C. (Aerospace Corp., El Segundo, CA).
STANDARD FOR HANDLING OF ELECTROSTATIC PARTS AND ASSEMBLIES.
Rept. No. TOR-0079 94902-04-2, Contract No. F04701-78-C-0079, February 15, 1979, 20 pp.

This document establishes common procedures and precautionary measures for the protection of ESD sensitive devices and components. Work station, clothing, protective packaging, and design documentation are covered in detail.

17016

Martzloff, F.D. (General Electric Co., Electronic Power Conditioning & Control Laboratory, Schenectady, NY).
A GUIDELINE ON TRANSIENT OVERVOLTAGES IN LOW-VOLTAGE AC POWER CIRCUITS.
Rept. No. 77CRD221, September 1977, 6 pp.

Transient overvoltages occurring in low-voltage ac power circuits can be the cause of misoperation and product failure for residential as well as industrial systems. This guideline describes what is known and what is not known about the environment, with recommendations on how to cope with the situation.

The origin of transient overvoltages -- lightning and load switching -- are discussed in the context of ac circuits of less than 600V. Available data on frequency of occurrence as a function of voltage levels are presented. Waveshape of 'representative' transients are discussed and a proposal made for a simple test wave. Energy and source impedance of the transients are discussed with reference to the energy-handling capability of available transient suppressors. Power system size and energy of transients are compared.

17037

Waxler, D. (U.S. Army Armament Research and Development Command, Large Caliber Weapon Systems Laboratory, Dover, NJ).
MODELING THE EFFECTS OF LIGHTNING ON ELECTRICAL EQUIPMENT.
Rept. No. ARLCD-TR-78029, AD/A064591, AD-E400 253, November 1978, 54 pp.

A model was developed for computing the safety and reliability of electrical equipment in a lightning environment. The model specifies the parameters of lightning that are pertinent in causing damage to equipment. This report indicates how the model is to be used for testing equipment to determine failure levels. Using these failure levels, it also shows how to compute the actual safety and reliability to be expected in field use, where lightning is a threat.

17038

Regulinski, T.L., and J.T. DiJak (U.S. Air Force, Rome Air Development Center, Rome, NY).
FAA LIGHTNING PROTECTION STUDY: RELIABILITY LIFE OF LIGHTNING PROTECTION DEVICES UNDER SIMULATED LIGHTNING CONDITIONS.
Rept. No. FAA-RD-76-92, Contract No. DOT-FA72WAT-356, AD/A025 786, December 1975, 75 pp.

This report deals with the experimental design of reliability life testing program, with its implementation, and with the analysis of failure data generated. Four different types of lightning protection devices were tested under simulated lightning conditions. Nineteen MOV failures and twenty-four TransZorb failures were observed out of a total testing sample of 50 and 55, respectively, when subjected to approximately 150 surges of simulated lightning energy.

17055

Winters, R.D. (General Semiconductor Industries, Inc., Tempe, AZ).
POWER SUPPLY VOLTAGE TRANSIENT ANALYSIS AND PROTECTION.
Third National Solid-State Power Conversion Conference, Proceedings of POWERCON 3, Application Note 1011, June 1976, 11 pp.

A voltage transient is an unexpected change in voltage caused by an unpredictable occurrence. Voltage transients and power surges differ by their causes, magnitude, destructive capabilities, and energy. The technology for suppressing the two are often quite different too. Transients are characterized by high-voltage departures which are less than 8.4 milliseconds in duration. Power surges are characterized by low voltage excursions, lasting greater than 8.4 milliseconds. This paper separates transients into four categories: lightning, EMP, static discharge and inductive switching. It deals primarily with the transients associated with inductive switching; however, with proper component selection and design consideration, the transient suppressor can protect a system from all transient sources. Lightning, EMP, and static are each a study into themselves, but are briefly discussed in this paper.

17075

Sabaroff, S. (Hughes Aircraft Company, El Segundo, CA).
STATIC ELECTRICITY CASE HISTORIES.
Spacecraft Electromagnetic Interference Workshop held at Jet Propulsion Lab., 33-402, February 1968, pp. 203-214.

The major sources of static charge are on or near the earth. The list could include fuel handling, plastics, rocket engine charging, precipitation, friction, lightning, booster separation and many others.

Static charge buildup on spacecraft and humans has been investigated throughout the industry. Transistor and SCR failures have also been related to static effects.

17076

Rogers, P.R. (General Electric Company, Philadelphia, PA).
TRANSIENT COMPATIBILITY MEASUREMENTS IN SPACECRAFT.
Spacecraft Electromagnetic Interference Workshop held at Jet Propulsion Lab., 33-402, February 1968, pp. 197-202.

The capability of measuring broadband and narrowband frequency domain voltages has existed for many years. In any given system the fundamental and most spurious frequencies are known. The source of interfering

transients is usually the operation of relays, tuning components, and other high current level changes mostly on main power buses.

17077

Whittlesey, A.C. (Jet Propulsion Laboratory, Pasadena, CA).
SPACECRAFT INTERFACE CIRCUITRY SENSITIVITY ANALYSIS.
Spacecraft Electromagnetic Interference Workshop held at Jet Propulsion Lab., 33-402, February 1968, pp. 171-184.

The study presented concerns Mariner/Mars Spacecraft. This study was done after the spacecraft was conceived, designed and launched into space. It was limited to intersubsystem problems because of the way the JPL builds.

17078

Schenker, B. (Lockheed Missiles & Space Co., Sunnyvale, CA).
TRANSIENT MEASUREMENTS IN AEROSPACE VEHICLES.
Spacecraft Electromagnetic Interference Workshop held at Jet Propulsion Lab., 33-402, February 1968, pp. 163-169.

Two methods of transient voltage measurement at selected critical points in an aerospace vehicle are described in this paper. These measurements are for the purpose of injecting 6dB higher voltages into aerospace vehicles to demonstrate compliance with specification MIL-E-6051C. Both methods have given positive results in attaining the required objective, but the memory voltmeter/oscillograph combination is preferred because of its simplicity. This latter method is planned to be used in future EMI system compatibility tests.

17079

Butts, A.J., and R.W. Ellis (Martin Marietta Corp., Denver Division, Denver CO).
CONTROL OF ELECTROSTATIC INTERFERENCE IN SPACECRAFT.
Spacecraft Electromagnetic Interference Workshop held at Jet Propulsion Lab., 33-402, February 1968, pp. 215-220.

A study of various electrostatic phenomena will show that both an insulating material and a charging mechanism are always involved. The charging mechanism involves motions of particles, liquids, gases, or in some instances the insulating material itself. There is one factor that can be controlled to some degree: the resistivity of the materials exposed to these charging mechanisms. If conductive materials were always used no electrostatic charge could be developed, and a situation that could be called electrostatic compatibility (ESC) would exist.

17080

Hoffart, H.M. (General Electric Co., Valley Forge Space Technology Laboratories, King of Prussia, PA).
THE CONCEPT OF SINGLE-POINT GROUNDING.
Spacecraft Electromagnetic Interference Workshop held at Jet Propulsion Lab., 33-402, February 1968, pp. 221-230.

Grounding concepts must be designed on a system level rather than on an individual equipment basis because of interface requirements. Effective grounding is not difficult to achieve if properly approached within the discipline of electromagnetic compatibility. The single-point grounding concept is shown to exhibit advantages if effectively implemented. The use of litzwire due to the interweaving of insulated strands will display a low impedance characteristic up to the low MHz area of the frequency spectrum. At the subsystem end, litzwire is used to separately reference the signal and static grounds.

17082

Skanadore, W.R. (General Semiconductor Industries, Inc., Tempe, AZ).
REDUCING CONDUCTED EMI WITH A NEW ULTRA-LOW-CAPACITANCE SWITCHING TRANSISTOR CONFIGURATION.
Proceedings of POWERCON 5, May 6, 1978, 20 pp.

A brief review of the various sources of EMI in the switching power supply is presented. Capacitive coupling of the transistor collector (case) to ground is shown to be a major cause of conducted EMI.

Conventional solutions (e.g., "screened heatsinks") are examined and shown to be much less than optimal. The isolated TO-3 is presented as an effective solution to this problem. Electrical, thermal, and mechanical properties are compared to "standard" configurations. Data showing the comparative reduction in conducted EMI (obtained by an independent testing facility) is provided.

17151

Hyatt, H., H. Calvin, and H. Mellberg (Experimental Physics Corp., Hayward, CA).
A CLOSER LOOK AT THE HUMAN ESD EVENT.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 1-8.

This paper presents some of the electronic industry's tests and procedures for simulating human ESD and how observed ESD events relate to these industry-designed tests. Risettime and leading edge structure of an ESD event is determined by several independent elements in the discharge path:

specifically, the corona losses prior to and during spark formation, electronic structure of the complete discharge circuit, spark formation processes, and the circumstances immediately prior to discharge. Industry test procedures are not consistent and span a greater range of transients than is typical for an ESD event. Limitations on the previously mentioned independent elements in the discharge path must be considered when simulation standards are specified. These constraints lead to a new model for the human ESD circuit.

17152

Blinde, D., and L. Lavoie (Honeywell Inc., Defense Systems Division, Hopkins, MN). QUANTITATIVE EFFECTS OF RELATIVE AND ABSOLUTE HUMIDITY ON ESD GENERATION/SUPPRESSION. IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 9-13.

The importance of ESD control is widely recognized, but effective and efficient control techniques are still being developed. Grounding through use of conductive floor tile, bench tops, packaging, and wrist straps have been effectively used. Widespread control of ESD has been achieved by environmentally limiting charge build-up using slightly ionized air or maintaining plant and laboratory humidity at a suitably high level.

17153

McAteer, O.J., and R.E. Twist (Westinghouse Electric Corp., Baltimore, MD). ANALYSIS OF ELECTROSTATIC DISCHARGE FAILURES. IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 9-13.

Identification of ESD problems can be difficult without the use of sound failure analysis procedures. This paper highlights some of the techniques that have proven the most beneficial in identifying the cause and corrective action for static failures. Some key steps that are frequently valuable in ESD analysis are circumstantial evidence of static accumulation, failure duplication tests, chemical etching, liquid crystals and scanning electron microscopy.

17154

Frank, D.E. (McDonnell Douglas Corp., Douglas Aircraft Co., Long Beach, CA). THE PERFECT "10" - CAN YOU REALLY HAVE ONE? IITRI - EOS/ESD Symposium Proceedings, Douglas Paper 7087, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 21-27.

The Douglas Aircraft Company, after researching numerous papers and investigations

in the area of reliability failure analysis and semiconductor physics, concluded that only a relatively small amount of ESD damage resulted in hard or reported failures. Douglas realized that regardless of the quality of their own ESD protection program, their ESD program would never be a perfect "10" unless everyone from manufacturer, system assembly houses, their customers, the military, and commercial airlines had comparable programs. In this effort to achieve the "10" goals, Douglas embarked upon an informative program.

17155

McFarland, W.Y. (Western Electric Co., Denver, CO).

THE ECONOMIC BENEFITS OF AN EFFECTIVE ELECTROSTATIC DISCHARGE AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS.

IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 28-33.

An increasing awareness of IC failures at the device, circuit pack, and PBX system levels prompted an investigation of possible electrostatic discharge damage to semiconductor devices when handled either individually or in circuit packs. Discussions were held with engineers who studied and solved the same types of problems on a smaller scale at other Western Electric plants. Several suppliers of static control equipment were also consulted. This was followed by a Denver Works In-House study that revealed the need for implementing the ESD Awareness and Control Program described.

17156

Head, G.O. (Lear Siegler, Inc., Instrument Division, Grand Rapids, MI).

A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT.

IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 40-43.

An excess of new electrostatic discharge protective material and equipment has been marketed over the past few years. Many vendors have produced similar products. These materials and equipment range in quality from very useful to potentially damaging. Materials and equipment seemingly very similar may differ in the actual ESD protection they offer. Surface resistance is probably the single most important characteristic in ESD protective material. A few easy, low-cost tests, explained in this paper, can help determine these products' ESD protection capabilities. This paper also includes methods used to identify serious problems in widely used blowers and high voltage relays.

17157

Tenzer, F.D. (Packaging Industries of California, Biola, CA) H.C. Hartmann, and M.A. Johnson (Hewlett-Packard Co., Data Terminals Division, Sunnyvale, CA).

AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS.

IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 44-48.

A large number of antistatic cushion wrap materials are available on the market today. Each of the manufacturers of the products made claims as to their cushioning and electrostatic discharge protection capabilities. At present there are seven manufacturers of antistatic cushion wrap material. Six samples of each material were collected at random by Hewlett-Packard Data Terminals Division. Tests were performed in accordance with existing federal or industrial standards. Significant differences in ESD and cushioning characteristics were found among the products tested.

17158

Pedulla, J., and P. Malinaric (Chomerics, Inc., Woburn, MA).

CHO-TRAP, A NOVEL VOLTAGE TRANSIENT PROTECTION PACKAGING MATERIAL.

IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 49-56.

Cho-Trap is a trade name for a new transient protection composite material with non-linear current voltage characteristics. The material acts like an insulator at circuit voltages and becomes a conductor when the voltage increases. These properties can be utilized to provide protection against transient electrical overstress. Cho-Trap can be custom-formulated as an elastomer for optimum packaging and protection.

17159

Unger, B., R. Chemelli, P. Bossard, and M. Hudock (Bell Laboratories, Murray Hill, NJ).

EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES.

IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 57-64.

It has been reported that device failure can occur from the discharge of triboelectrically charged IC pins. Since most devices are shipped in tubes, an obvious place to look for the generation of charge on a device is during the transport, loading or unloading of devices. This paper presents data on the triboelectric charging characteristics of

devices resulting from sliding and vibrating in tubes made from metal and various plastic materials. The data show the variation of charge generated on plastic and hermetic packages with various lead frames, epoxy and silicon.

17160

Topolski, A.S. (E.I. DuPont De Nemours & Co., Wurtland, KY).

INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS.

IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 65-74.

This paper compares the various procedures and equipment for testing antistatic packaging materials to determine the most compatible method for production use. It uses the static decay measurement with humidity and temperature preconditioning as the basic qualification technique. Samples are measured and their quality quantified. These same samples are then evaluated at other ambient conditions using the static decay, surface resistivity, surface charge, and volume conductivity tests.

17161

Kolyer, J.M., and W.E. Anderson (Rockwell International, Autonetics Strategic Systems Division, Anaheim, CA).

SELECTION OF PACKAGING MATERIALS FOR ELECTROSTATIC DISCHARGE-SENSITIVE (ESDS) ITEMS.

IITRI - EOS/ESD Symposium Proceedings, Rept. No. X81-501/201, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 75-84.

It is difficult to select packaging materials for ESDS items because vendors of materials make conflicting claims and performance requirements are indefinite. New ESDS devices are being introduced which are more sensitive than the old. This paper evaluates seven packaging materials. Properties such as transparency, puncture resistance, and heat seal strength were measured. Packaging materials were exposed to environmental stresses far in excess of those anticipated. Results are tabulated, and failure mechanisms are discussed. A distinction is made between suitable materials for in-plant use and shipping. A brief review is given of the context of static control plant procedures in which the protective bags are used.

17162

Pancholy, R.K. (Rockwell International, Microelectronics Research and Development Center, Anaheim, CA).

THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD.

IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 85-89.

This paper examines the increased susceptibility of MOS VLSI circuits to electrical overstress/electrostatic discharge (EOS/ESD) conditions due to scaling of feature sizes such as metal widths, junction depths and gate oxide thickness of 1um technology. Failure modes such as thermal overstress, metallization failure, electromigration, silicon resistor failure, gate oxide breakdown, latch-up and packaging-related failure modes are described.

17163

Hulett, T.V. (Microprocessor Design, Motorola Semiconductor Group, Austin, TX).
ON-CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES.

IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 90-96.

This paper summarizes a study that was initiated to improve the on-chip protection of high density NMOS devices. The capability of approximately 100 different input protection schemes were examined. This was done by producing a test vehicle in a high density NMOS process. The input protection networks studied are combinations of seven basic structures. The ability of each structure to successfully protect the internal circuitry is presented. Guidelines for design and layout of future protection circuits are also presented.

17164

Taylor, R. (Mostek Corp., Carrollton, TX).
INPUT PROTECTION DESIGN FOR THE 3u NMOS PROCESS.

IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 97-100.

This paper attempts to demonstrate how the application of established theoretical principles to the conceptual design and layout of input protection systems can provide such an increase in effectiveness in a manner compatible with high-volume, high-density processing techniques.

17165

Jensen, M.C., and R.T. Milburn (Motorola, Inc., Phoenix, AZ).
DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE.

IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 101-105.

Many silicon planar transistors are scrapped after lot processing or reliability testing due to hFE degradation caused by excessive reverse current applied to the emitter-base junction. The objective of this paper is to identify specific symptoms that are unique to these types of degraded devices and which will enable the failure analyst to isolate the cause of failure.

17166

Enders, J. (Standard Elektrik Lorenz, AG, A German Company of ITT).

SUSCEPTIBILITY OF ICS IN ELECTROSTATIC DAMAGE STEP-STRESS TESTS.

IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 106-113.

During failure analysis activities, a large number of ICs were detected which definitely failed due to electrostatic overstress (EOS). In order to quantify the risk of ESD susceptibility of modern ICs, a step-stress test procedure was developed. The results of ESD step-stress tests clearly indicate that the susceptibility of all presently available integrated circuits to electrostatic damage during handling, transport and production is critical. From a user's point of view, the specification of WIN min values according to a standardized ESD test method for ICs is urgently needed to quantify the risk and to make evaluation results comparable.

17167

Young, P.A., R.J. Karaskiewicz, (BDM Corp., Albuquerque, NM) and D.R. Alexander (Sandia National Laboratories, Albuquerque, NM).

ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES.

IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, Contract No. F29601-77-C-0099, pp. 114-119.

The rapid development of integrated circuit technology has resulted in electronic systems which incorporate components whose vulnerability to electrical overstress is uninvestigated. The reaction of these emerging technologies to electrical discharge and EMP cannot be adequately assessed, and they may be quite susceptible to damage from these effects. This paper describes the goal to examine those technologies which appear most likely to be used in modern LSI and VLSI devices. Seven different integrated circuit technologies and eleven circuit functions were selected for analysis and electrical overstress testing. All parts were subjected to electrical overstress pulses on the input,

output, and power supply terminals. Failure was induced by increasing the amplitude of the overstress pulse until observable damage occurred. The device under test was examined for changes in terminal electrical parameters and functional operation after each pulse. The results of the failure threshold investigation are reported as average failure power as a function of pulse width.

17168

Pierce, D.G., and D.L. Durgin (Booz-Allen & Hamilton, Inc., Albuquerque, NM).
AN OVERVIEW OF ELECTRICAL OVERSTRESS EFFECTS ON SEMICONDUCTOR DEVICES.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 120-131.

The purpose of this paper is to provide a comprehensive review of the effects of the various types of EOS on semiconductor devices and to foster an awareness of the similarities between these effects. The information is based on a thorough evaluation of past and ongoing programs in the ESD and EMP communities and provides a comprehensive review of the technical tools and data that are currently available.

17169

Kusnezov, N., and J.S. Smith (Lockheed Palo Alto Research Laboratory, Palo Alto, CA).
MODELING OF EOS IN SILICON DEVICES.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 132-138.

A computer code has been written which describes in two dimensions the transient thermal behavior of silicon junctions as the result of excessive power dissipation. The code essentially merges a transient thermal analysis program with an instantaneous power dissipation program. This code must be verified experimentally, and this has not yet been done. The results obtained are consistent both in function and magnitude with existing EOS and EMP data, and no violations of EOS have been suggested by the code.

17170

Thomas, R.E. (Kaman Sciences Corp., Colorado Springs, CO).
SEMICONDUCTOR DEVICE FAILURE CRITERIA FOR SINUSOIDAL STRESSES.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 139-144.

Rectangular pulse testing can be used to predict semiconductor device failure under sinusoidal stress by defining equivalent rec-

tangular pulses. Four different pulse equivalence criteria are analyzed to determine the bounds on frequency conversion factors. This data can be used to estimate error bounds on the failure power resulting from waveform effects. The analysis suggests that waveform effects are not a major source of uncertainty in EMP vulnerability assessments.

17171

Wallig, L.R. (DuPont Co., Riston Products Division, Wilmington, DE).
ARE CLEAN ROOMS REALLY NECESSARY FOR FINE-LINE PRINTED CIRCUITS?
Circuits Manufacturing, Vol. 21, No. 11, November 1981, pp. 54-60.

As printed wiring boards with two or more conductor lines between IC pads become increasingly common, fabricators are faced with the need for greater environmental control. Clean rooms have been the solution in semiconductor processing, and many printed wiring board producers have gone the same route. This paper discusses the necessity of clean rooms for printing wiring boards, the required levels of cleanliness, at what cost the levels are achieved, the temperature and humidity controls, and the existing alternatives.

17172

Enlow, E.W. (The BDM Corp., Albuquerque, NM).
DETERMINING AN EMITTER-BASE FAILURE THRESHOLD DISTRIBUTION OF NPN TRANSISTORS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, Contract No. F29601-77-C-0099, pp. 145-150.

A composite failure threshold probability distribution has been developed to predict emitter-base electrical overstress junction failure of NPN transistors. This composite distribution provides a better probabilistic representation than the lognormal and Weibull distributions that are currently employed in survivability/vulnerability analyses of electronic circuits subjected to electrical overstress. The Component Statistical Characterization (CSC) data base was used in this analysis. In the CSC program, the lognormal was the most rejected of the five distributions tested for prediction of emitter-base transistor failure. The Weibull distribution is an excellent predictor for emitter-base nominal device failure. However, it is inadequate for predicting "maverick" devices and devices which are weaker than nominal.

17173

Horgan, E.L., O.E. Adams, W.H. Rowan, and L.C. Templar (TRW Defense And Space System Group, Redondo Beach, CA).

EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE, AND CONTROL.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 151-166.

Circuit EOS/ESD failure thresholds define the minimum overstress level required to damage a semiconductor. The thresholds are calculated using conventional circuit analysis and semiconductor device damage models, which are synthesized from experimental data, and are based on the principles of semiconductor device physics. This paper examines the accuracy of calculated failure thresholds, identifies the source and magnitude of analysis errors, and suggests techniques for improving analysis accuracy.

17174

Wunsch, D.C. (The BDM Corp.).
AN OVERVIEW OF EOS EFFECTS ON PASSIVE COMPONENTS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, Rept. No. BDM/A-81-6460, pp. 167-173.

A great deal of electrical overstress testing and analysis on semiconductor devices has been performed and is presented in this paper. Passive components are generally not as vulnerable to EOS as semiconductor components and, therefore, are not usually the primary component of concern for EOS circuit failure. The emphasis on semiconductor devices has been because of the very low energy or voltage necessary to cause failure for many device types. However, there are a number of cases in which passive components are the limiting element in failures from EOS.

17175

Tasca, D.M. (General Electric Co., Space Systems Division, Philadelphia, PA).
PULSE POWER RESPONSE AND DAMAGE CHARACTERISTICS OF CAPACITORS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, Contract No. F29601-75-C-0130, pp. 174-191.

This paper presents the results of extensive experimental and theoretical investigations performed to develop quantitative response and damage models for a wide range of capacitor types under pulse electrical overstress environments. These models, with statistical variations and comparisons to manufacturers' ratings, were developed for electrostatic and electrolytic capacitors. When capacitors are subjected to high-level electrical pulse stress, their vulnerability is determined by the pulse response and damage characteristics which are peculiar to the materials and construction details of each particular capacitor type.

17176

Smith, J.S., and W.R. Littau (Lockheed Palo Alto Research Laboratories, Palo Alto, CA).
PREDICTION OF THIN-FILM RESISTOR BURNOUT.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 192-197.

A study of thin-film resistor failure when subjected to an electrostatic discharge pulse has led to the development of a predictive model for burnout. A model was developed based upon the heat flow characteristics of a thin-film resistor which permits the prediction of the voltage and current necessary to reach a critical temperature for a given square wave pulse input.

17177

Mathurin, J., R.M. Thomas, and R.H. Guay (Epitek Electronics, Inc., Canada).
BEHAVIOR OF THICK-FILM POWER RESISTORS SUBJECTED TO LARGE MOMENTARY OVERLOADS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 198-201.

This paper describes work done on the design of thick-film power resistors intended for battery-feed service in telephone exchanges and for other applications involving large momentary overloads. REA requirements governing resistance to momentary overloads must be compiled within the design of these resistors. Two major catastrophic failure modes were identified early in the work and traced to voltage breakdown and power density. Attention was focused on the problem of designing resistors which would spread the heat out sufficiently to minimize hot spots and the associated thermal gradients, since voltage breakdown effects are easy to control.

17178

Hays, R.A. (U.S. Air Force Weapons Laboratory, Kirtland Air Force Base, NM).
EOS THRESHOLD DETERMINATION OF ELECTRO-EXPLOSIVE DEVICES.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 202-207.

The threshold determination was performed to provide data in the assessment of the Minuteman Missile for Electromagnetic Pulse (EMP) studies. Four basic devices and two subassemblies were subjected to square wave and damped sine waves. Though multiple pulsing was not to be of primary interest, significant changes in breakdown characteristics were observed from the step-stress.

17179

Mykkanen, C.F. (Honeywell, Inc., Defense Systems Division, Hopkins, MN).
POTENTIAL ESD HAZARDS ASSOCIATED WITH EXPLOSIVE PRIMERS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 208-211.

Honeywell experienced an inadvertent firing of an explosive primer at their Honeywell Ordnance Proving Ground (HOPG) Facility. Experimental testing was conducted to find out what role ESD may have played in that event. Testing revealed that one of the sputtered film type primers used at the HOPG test site could be fired by high voltage-level ESD. Primers were fired by both simulated ESD discharge from a voltage calibrated VZAP tester as well as by discharges from a charged human body. Testing indicated that the firing line cable used at the test site was capable of generating triboelectrically produced static during normal usage. Even though there were other causes for this incident besides ESD, Honeywell was convinced that a potential safety problem exists if high energy level ESD is inadvertently applied to primers with low initiation energies.

17180

Clark, O.M. (General Semiconductor Industries, Inc., Tempe, AZ).
LIGHTNING PROTECTION FOR COMPUTER DATA LINES.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 212-218.

The failure rate of data terminals and computer main frames from lightning-caused transient voltages on data lines is increasing. This is directly related to a higher degree of IC miniaturization and increasing use of longer data lines. Computer systems can now be reliably protected from lightning-caused transient voltages with selected and fabricated combinations of gas surge arrestors and silicon transient suppressors. A few fundamental precautionary measures must be observed to make these protectors effective. These include short distance, low impedance paths to ground and physical separation of the protected data lines from the unprotected lines.

17181

Horgan, E.L., and T.S. Lin (TRW Defense And Space Systems Group, Redondo Beach, CA).
FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 219-224.

A procedure has been developed to determine probabilistically whether a semiconductor device failure has been caused by prescribed or anomalous EOS/ESD testing. An example is provided where a device that has received catastrophic damage during testing is analyzed by microscopic examination and detailed modeling techniques.

17182

Head, G.O. (Lear Siegler, Inc., Instrument Division, Grand Rapids, MI).
TIME-RELATED IMPROVEMENTS OF ELECTRICAL CHARACTERISTICS IN ELECTROSTATICALLY DAMAGED OPERATIONAL AMPLIFIERS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 225-228.

This paper analyzes improvements in degraded electrical characteristics occurring in 741-type operational amplifiers after they have been damaged by electrostatic discharge. Devices that have received catastrophic electrostatic discharges exhibited time-dependent parametric improvements in input offset voltage and in input bias current. 344 operational amplifiers receiving noncatastrophic discharge exhibit abnormalities and time-dependent shifts in common mode rejection.

17183

Pease, R.L., J. Barnum (Mission Research Corp., Albuquerque, NM) W.V. Vulliet, T.F. Wrobel, and V.A.J. Van Lint (Mission Research Corp., LaJolla, CA).
ELECTRICAL OVERSTRESS DAMAGE IN SILICON SOLAR CELLS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, Contract No. 62-8208, pp. 229-235.

A model has been developed to predict the electrical overstress threshold failure current in silicon solar cells as a function of pulse width. The essential features of the model are that initial failure will occur in the silicon junction under the longest finger near where the finger intersects the bus. This failure is due to heat generated in the finger being conducted into the silicon, thereby raising the silicon temperature to the instability point where the silicon resistivity starts decreasing with temperature.

17184

Chase, E.W. (Bell Laboratories, Murray Hill, NJ).
EVALUATION OF ELECTROSTATIC DISCHARGE (ESD) DAMAGE TO 16k EPROMS.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 236-241.

A study of ESD damage to 16k EPROMs manufactured both in the United States and Japan has been made. EPROMs have been evaluated using two models for ESD with both positive and negative discharges. The two models for ESD were the "Human Body Model" and the "Charged Device Model." It has been shown that EPROMs show a characteristic signature at the input protection network for either discharge model. Some EPROMs were found to be more susceptible to damage or failure from the charged device model testing than from the human body model testing. Results of experiments on some EPROMs show the three-state input/output data lines to be particularly sensitive to ESDs.

17185

Ash, M.S. (TRW Defense and Space Systems Group, Hardness and Survivability Laboratory, Redondo Beach, CA).
NON-LINEAR KINETICS OF SEMICONDUCTOR JUNCTION THERMAL FAILURE.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 242-245.

It is well known that the Wunsch-Bell semiconductor junction thermal failure description is based on a constant thermal conductivity-heat conduction model. It is equally well known that the semiconductor material thermal conductivity is a strong function of the material temperature and so is not constant. This tends to cause some apprehension with regard to the range of validity of the Wunsch-Bell model. There have been a number of studies made of damage and thermal failure mechanisms in semiconductors due to coupled electromagnetic pulses (EMP) which produce heat within the semiconductor material. This work addresses the thermal failure of the semiconductor junction due to the ultrapid generation of heat caused by the deposition of incident pulse energy.

17186

McAleer, R.E., G.H. Lucas, and A. McDonald (Texas Instruments, Inc., Abilene, TX).
A PRAGMATIC APPROACH TO ESD PROBLEM SOLVING IN THE MANUFACTURING ENVIRONMENT, A CASE HISTORY.
IITRI - EOS/ESD Symposium Proceedings, RAC Catalogue No. EOS-3, September 22-24, 1981, pp. 34-39.

This paper outlines a study conducted over a one-year period of electrostatic discharge (ESD) in the manufacturing environment. All data presented was generated from assembly line production. ESD problems are divided into three main categories for analysis: internal humidity control, assembly techniques, and operator awareness. All work done in humidity control was based on obtaining a

minimum of 50% relative humidity plant-wide. The data presented on assembly techniques includes an analysis of ESD control in the use of machinery, work surfaces, storage containers and operator grouping. An ESD program is presented to achieve active participation from assembly line personnel.

17279

Scovern, J.L. (ITT Courier Terminal Systems, Inc., Tempe, AZ).
STATIC CONTROL IMPROVES PCB QUALITY.
Quality, November 1981, pp. 46-47.

The antistatic liquid Staticide is tested to determine its effects on the quality of printed circuit boards. Solderability, corrosion rates, and printed circuit damage were checked.

17280

Siegal, B.S. (Sage Enterprises, Inc., Mountain View, CA).
ELECTRICAL THERMAL TESTING PUTS QUALITY IN GaAs FET SYSTEMS.
Microwave Systems News, Vol. 11, No. 8, August 1981, pp. 108-113.

Understanding and being able to measure the operating junction temperature of semiconductor devices is crucial to building reliable systems. This paper describes a method for electrical thermal testing of GaAs FET junctions.

17281

Stamps, D. (Fairchild).
OFFICES CATCH STATIC OVER INTERRUPTIONS.
MIS Week (Fairchild Business Newspaper), Vol. 2, No. 28, July 15, 1981.

This article gives various ESD problems encountered by companies and how these problems were solved. Special attention is given to rugs and carpeting as being static generators.

17285

Walker, R.C. and N.B. Fuqua (Reliability Analysis Center, Griffiss AFB, NY).
COPING WITH STATIC ELECTRICITY - PART XXVI, A SPECIAL REPORT FROM THE EOS/ESD SYMPOSIUM.
Evaluation Engineering, Vol. 20, No. 6, November/December 1981, pp. 104-108.

This article is a summary of the third EOS/ESD Symposium held September 21-24 at Las Vegas' Aladdin Hotel. Thirty-five papers were presented and thirty-three exhibitors displayed their products and explained their services. Professor A.D. Moore made the luncheon speech on Henry A. Rowland, the forgotten

SECTION 9
STANDARDS



Handbooks, Specifications and Standards Specifying Test Methods and Controls for Protection of Electrical and Electronic Parts, Assemblies and Equipment Against Electrostatic Discharge:

U.S. GOVERNMENT DOCUMENTS

DOD-HDBK-263	Electrostatic Discharge Control Handbook for Electrical and Electronic Parts, Assemblies and Equipment Requirement for the Electrostatic Discharge Protection of Electronic Components and Assemblies
DOD-STD-1686	Electrostatic Discharge Control Program for Electrical and Electronic Parts, Assemblies and Equipment
NAVORD OD 46363	Requirements for the Electrostatic Discharge Protection of Electronic Components and Assemblies (completely contained in DOD-HDBK-263 and DOD-STD-1686)
FED-STD-101B	Preservation, Packaging and Packing Materials, Test Procedures; Test Method 4046 Electrostatic Properties of Materials
MIL-STD-129H	Marking for Shipment and Storage
MIL-STD-758B	Packing Procedures for Submarine Repair Parts
MIL-STD-883B	Test Methods and Procedures for Microelectronics; Test Method 3015 Electrostatic Discharge Sensitivity
MS-90363G	Box, Fiberboard, with Cushioning for Special, Minimum Cube Storage and Limited Reuse Applications
MIL-B-117	Bags, Sleeves and Tubing, Interior Packaging
MIL-S-19491	Semiconductor Devices, Packaging of
MIL-M-38510	Microcircuits, General Specification for
MIL-M-55565A	Microcircuits, Packaging of
MIL-B-81705B	Barrier Materials, Flexible, Electrostatic-Free, Heat Sealable
MIL-P-81997A	Pouches, Cushioned, Flexible, Electrostatic-Free, Reclosable, Transparent

U.S. GOVERNMENT DOCUMENTS (Cont'd)

PPP-C-1842 Cushioning Material, Plastic, Open Cell
 (For Packaging Application)

NAVSUP/SPEC STD Form 36, Packaging Instructions for Electro-
Contract Requirement G-64 magnetic and Electrostatic Protection

FOREIGN GOVERNMENT DOCUMENTS

Defense STD-59-98 (U.K.) Handling Procedures for Static Sensitive
 Devices

INDUSTRY DOCUMENTS

AATCC

134-1975 Test Method for the Electrostatic
 Propensity of Carpets

ANSI

47 (Secretariat) 707-Draft Test Method for Electronic Devices
 Sensitive to Electrostatic Discharge

Z41.3 Conductive Safety-Toe Footwear: Section
 5, Conductivity

ASTM

D257-78 D-C Resistance of Conductive or Insulat-
 ing Materials

D991-75 Test Method for Rubber Property-Volume
 Resistivity of Electrically Conductive
 and Antistatic Material

D2679-78 Test Method for Electrostatic Charge

D3509-76 Test Method for Electrostatic Field
 Strength Due to Surface Charges

EIA (JEDEC)

RS-471 Attention Symbol and Label for Electro-
 static Devices

NAS

NAS-853 Field Force, Protection for

INDUSTRY DOCUMENTS (Cont'd)

NFPA

No. 56A	Inhalation Anesthetics: Section 46 Reduction in Electrostatic Hazard
No. 77	Static Electricity
<u>UL</u>	
217	Single and Multiple Station Smoke Detectors: Section 36 Static Discharge Test

U.S. GOVERNMENT DOCUMENTS

Specification Sales (3FRSBS)
Bldg. 107, Washington Navy Yard
General Services Administration
Washington, DC 20407

FED-STD-101B
PPP-C-1842

Commanding Officer
Naval Publications and Form Center
5801 Tabor Avenue
Philadelphia, PA 19120

DOD-HDBK-263
NAVORD OD-46363
DOD-STD-1686
MIL-STD-129H
MIL-STD-758B
MIL-STD-883B
MS-90363G

MIL-B-117
MIL-S-19491
MIL-M-55565A
MIL-B-81705B
MIL-P-81997A
NAVSUP/SPEC STD Form 36
Contract Requirement G-64

DOD-HDBK-263: Electrostatic Discharge Control Handbook for Electrical and Electronic Parts, Assemblies and Equipment

This handbook provides guidelines for the establishment of an Electrostatic Discharge (ESD) Control Program in accordance with DOD-STD-1686. This document is applicable to the protection of electrical and electronic parts from damage due to ESD.

DOD-STD-1686: Electrostatic Discharge Control Program for Electrical and Electronic Parts, Assemblies and Equipment

This standard provides direction for the establishment and implementation of an Electrostatic Discharge (ESD) Control Program for any activity that designs, tests, inspects, services, manufactures, processes, assembles, installs, packages, labels, stores or stows or otherwise handles electrical or electronic parts susceptible to damage caused by static electricity.

NAVORD OD 46363: Requirements for the Electrostatic Discharge Protection of Electronic Components and Assemblies

This ordinance document covers the general and detail requirements for the electrostatic discharge protection of electronic components and assemblies. This document has been incorporated in its entirety into DOD-HDBK-263 and DOD-STD-1686.

FED-STD-101B: Preservation, Packaging and Packing Materials Test Procedures; Test Method 4046: Electrostatic Properties of Materials

The test method in this standard describes the procedures to use for testing the electrostatic properties of various materials.

MIL-STD-129H: Marking for Shipment and Storage

Paragraph 5.4.38 of this standard specifies the marking requirements of unit, intermediate and exterior packs of sensitive electronic (ESDS) items.

MIL-STD-758B: Packing Procedures for Submarine Repair Parts

Appendix C of this standard covers protection for sensitive electronic items such as, but not limited to, diodes, transistors, integrated circuits, and equipments incorporating such items which are susceptible to damage from electrostatic, electromagnetic, or both field forces.

MIL-STD-883B: Test Methods and Procedures for Microelectronics; Test Method 3015.1: Electrostatic Discharge Sensitivity

This test method establishes the means for determining the electrostatic discharge sensitivity classification for all microcircuits, and is used to determine the handling, marking, and packaging for shipment requirements for each device type.

MS-90363G: Box, Fiberboard, with Cushioning for Special, Minimum Cube Storage and Limited Reuse Applications

Dash Nos. 6, 7, and 8 of this standard specify the packaging and marking requirements of electrostatic sensitive devices.

MIL-B-117: Bags, Sleeves and Tubing, Interior Packing

This specification covers bags, sleeves and tubing, and interior packing for the preservation-packaging, field force protection (shielding), packing and container marking of electrical and electronic devices.

MIL-S-19491: Semiconductor Devices, Packaging of

This specification covers the requirements for the preservation-packaging, field force protection (shielding), packing and container marking of all types of discrete semiconductor devices (such as diodes and transistors).

MIL-M-38510: Microcircuits, General Specification For

This specification (revision E) requires all those devices covered by the specification to be tested for ESD sensitivity during initial qualification and any subsequent product redesign in accordance with MIL-STD-883 Method 3015.1 or the applicable detail (slash sheet) specification. Those devices determined to be sensitive to ESD (category A 2000 volts or less) or untested devices shall be marked accordingly either a) with the MIL-STD-129 symbol, b) an equilateral triangle, or c) utilizing a bright orange marking ink.

Slash sheets covered under this specification contain VZAP requirements for CMOS and MOS integrated circuits.

MIL-M-55565A: Microcircuits, Packaging Of

This specification covers the requirements for the preservation-packaging, field force protection (shielding), packing and container marking of all types of microcircuits.

MIL-B-81705B: Barrier Materials, Flexible, Electrostatic-Free, Heat Sealable

This specification covers opaque and transparent heat sealable, electrostatic-free, flexible, barrier materials for the packaging of missiles, explosive powered and electro-sensitive devices, microcircuits, semiconductors and thin film resistors.

MIL-P-81997A: Pouches, Cushioned, Flexible, Electrostatic-Free, Reclosable, Transparent

This specification covers the requirements for flexible electrostatic-free reclosable transparent pouches designed for shielding, packaging and storage of static-sensitive electronic devices.

PPP-C-1842: Cushioning Material, Plastic, Open Cell (For Packaging Applications)

This specification covers the requirements for Plastic Open Cell Cushioning Material designed for shielding, packaging and storage of static-sensitive devices.

NAVSUP/SPCC Form 36, Contract Requirement G-64: Packaging Instructions For Electromagnetic and Electrostatic Protection

This contract clause specifies the packaging instructions for the protection of field forces sensitive items.

FOREIGN GOVERNMENT DOCUMENTS

Ministry of Defense
Directorate of Standardization
First Avenue House
High Holborn
London WC1V 6HE

Defense Standard 59-98; Handling Procedures for Static Sensitive Devices

This standard provides guidance relating to the handling, identification and packaging of static sensitive devices.

British Standards Institute
2 Park Street
London W1A 2BS

BS5783: 1979; Code of Practice for Handling of Electrostatic Sensitive Devices

This code of practice recommends the precautions for the storage transportation, handling and testing of all kinds of electrostatic sensitive devices (ESDS), circuits, and assemblies.

INDUSTRY DOCUMENTS

American Society for Textile Chemists and Colorists
AATCC Technical Center, P.O. Box 12215
Research Triangle Park, NC 27709

AATCC Test Method 134-1975: Electrostatic Propensity of Carpets

This test method is designed to assess the static propensity of carpets by controlled laboratory simulation of conditions which may be met in practice, and more particularly, with respect to those conditions which are known from experience to be strongly contributory to excessive accumulation of static charges.

American National Standards Institute
1430 Broadway
New York, NY 10018

ANSI Test Method 47 (Secretariat) 707 (Proposed): Electronic Devices Sensitive to Electrostatic Discharges

This test method is designed to determine which electronic devices are sensitive to electrostatic discharge to the degree that they require special handling precautions.

ANSI Standard 241.3-1976; Conductive Safety-Toe Footwear

This standard provides the requirements for the design of conductive safety-toe footwear which protect against the hazards of the buildup of static electricity.

American Society of Testing and Materials
1916 Race Street
Philadelphia, PA 19103

ASTM Test Method D257-78: D-C Resistance or Conductance of Insulating Materials

This test method covers direct-current procedures for the determination of d-c insulation resistance, volume resistance, volume resistivity, surface resistance and surface resistivity of electrical insulating materials or the corresponding conductances or conductivities.

ASTM Test Method D991-75: Rubber Property-Volume Resistivity of Electrically Conductive and Antistatic Products

This test method covers the determination of volume resistivity of rubbers used in electrically conductive and antistatic products.

ASTM Test Method D2679-78: Electrostatic Charge

This test method covers the determination of the amount of electrostatic charge present on or in a specimen or of the electrostatic charge transferred between two material objects upon contact.

ASTM Test Method D3509-76: Electrostatic Strength Due to Surface Charges

This test method covers the determination of the value of electrical field strength at and near a variety of objects such as metal surfaces at high voltages and insulating bodies with electrostatic charge.

Electronic Industries Association
2001 Eye Street
N.W. Washington, DC 20006

EIA Standard RS-471: Attention Symbol and Label for Electrostatic Sensitive Devices

This standard provides a distinctive caution symbol and label to be used to identify those electronic devices that require special handling to prevent damage due to electrostatic discharge.

National Standards Association
1321 Fourteenth Street N.W.
Washington, DC 20005

NAS 853: Field Force, Protection For

This standard provides for the protection of items, components and assemblies which may be damaged by field forces (electrostatic, electromagnetic, magnetic or radioactive) encountered in nonoperating environment.

National Fire Protection Association
470 Atlantic Ave
Boston, MA 02210

NFPA Standard 56A: Inhalation Anesthetics; Section 46: Reduction in Electrostatic Hazard

Section 46 of this standard provides the requirements to reduce the possibility of electrostatic spark discharges, with consequent ignition of flammable gases in anesthetizing locations.

NFPA Standard 77: Static Electricity

This standard provides recommended practices that assist in reducing the fire hazard of static electricity by presenting a discussion of the nature and origin of static charges, the general methods of mitigation and recommendations in certain specific operations for its dissipation.

Underwriter's Laboratory
383 Pfingsten Road
Northbrook, IL 60062

UL Code 217: Single and Multiple Station Smoke Detectors; Section 36: Static Discharge Test

Section 36 of this code provides a test to determine if smoke detector units are sensitive to electrostatic discharges.

APPENDIX
ADDITIONAL RAC SERVICES

ADDITIONAL RAC SERVICES

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() MDR-16 Linear/Interface Data Complete Set: \$310	Feb. 1981	60.00	70.00**
() MDR-17 Digital Failure Rate Data (\$360 non-U.S.)	Aug. 1981	60.00	70.00**
() MDR-18 Memory/LSI Data	Feb. 1982	60.00	70.00**
() DSR-3 Transistor/Diode Data	Jan. 1980	60.00	70.00**
() NPRD-2 Nonelectronic Parts Reliability Data	Aug. 1981	60.00	70.00*

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() EERD-1 Electronic Equipment Reliability Data	Oct. 1980	60.00	70.00**
() EEMD-1 Electronic Equipment Maintainability Data	Oct. 1980	60.00	70.00*

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() RDH-376 Reliability Design Handbook	Mar. 1976	36.00	46.00**
() MFAT-1 Microelectronics Failure Analysis Techniques Procedural Guide	July 1981	125.00	135.00***

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